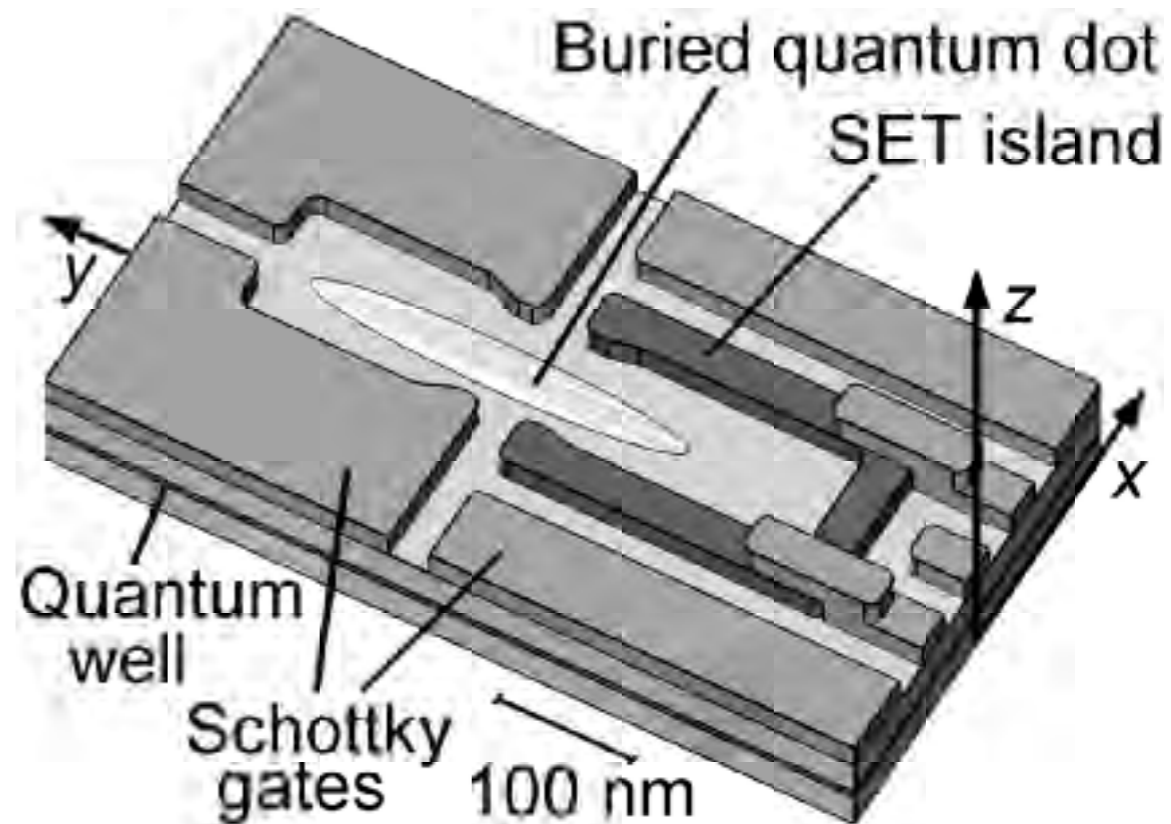
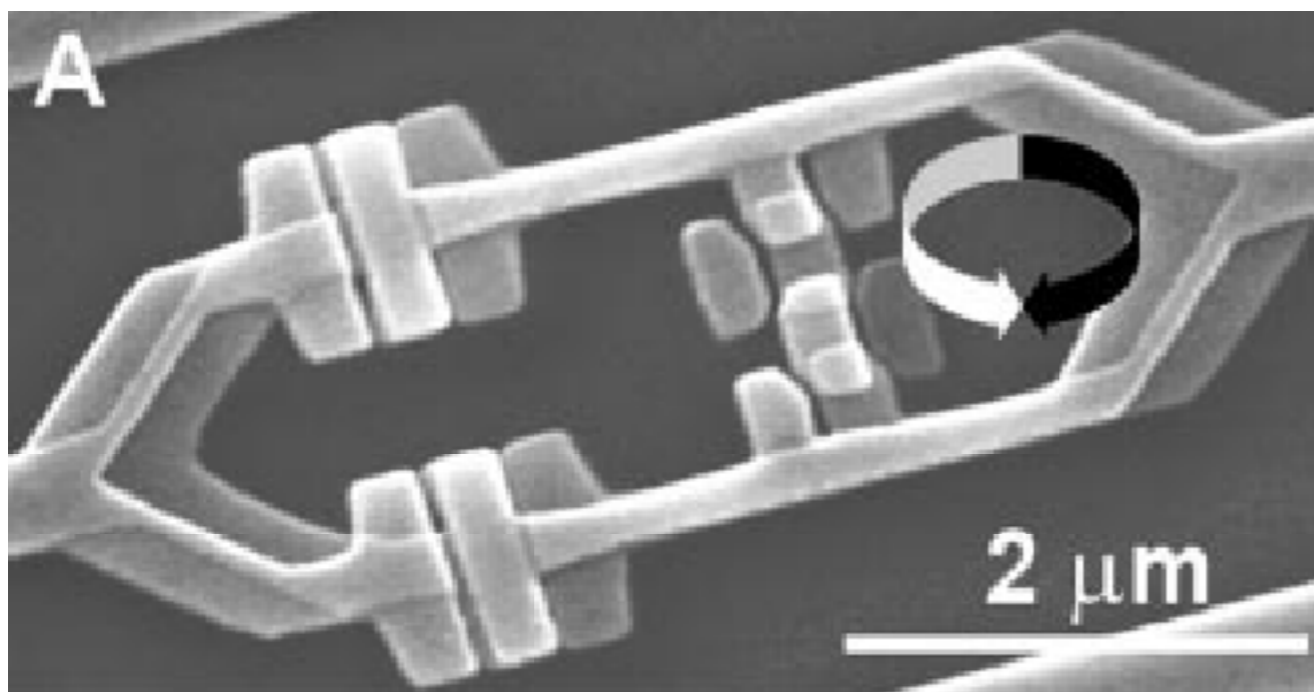
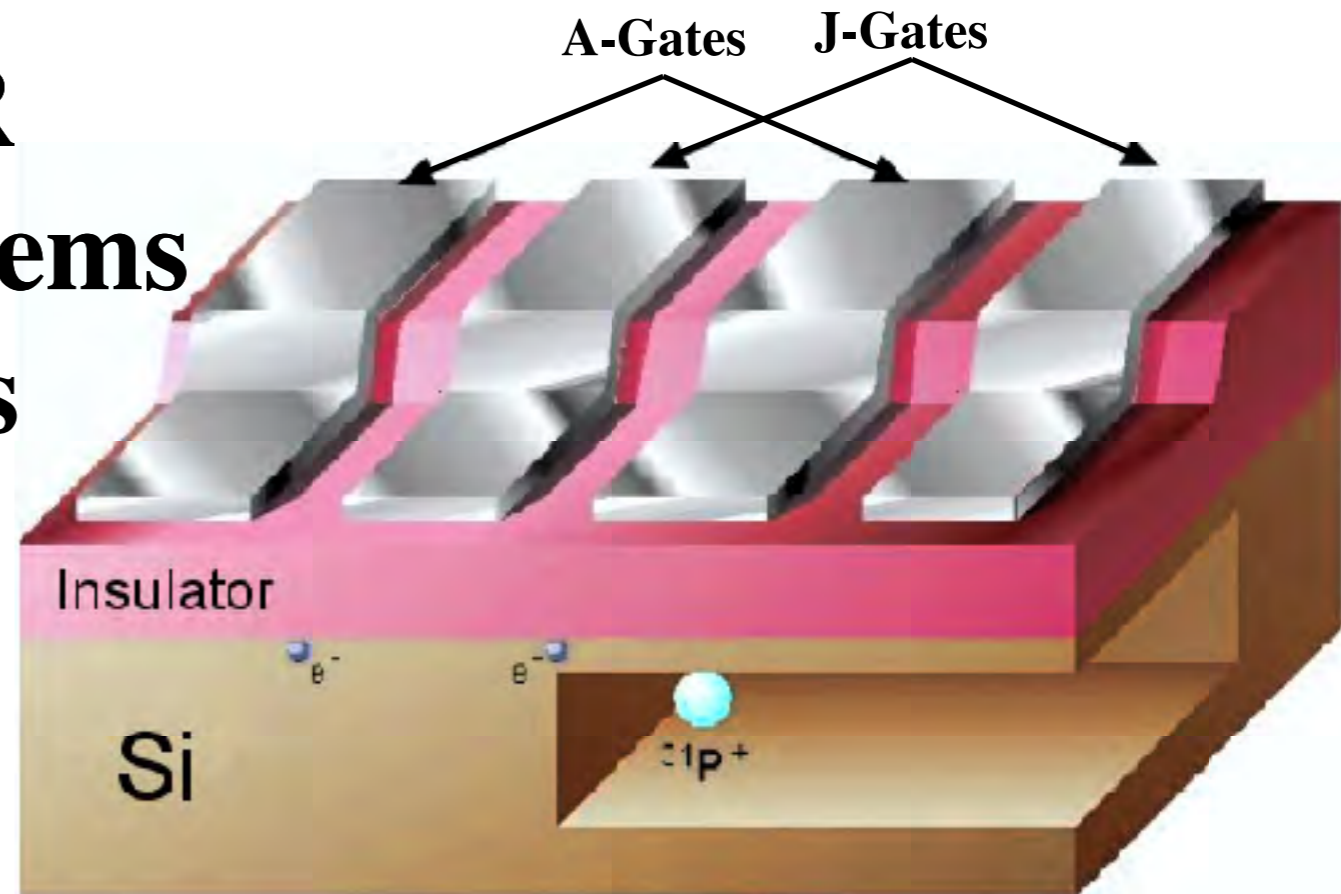


12) Solid-State Systems

12.1 Solid state NMR/EPR

12.2 Superconducting systems

12.3 Semiconductor qubits



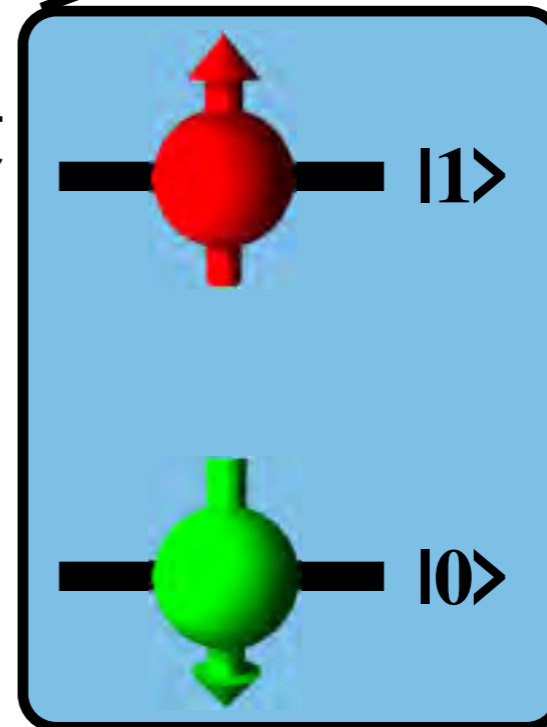
12.1.1 Scaling behavior of NMR quantum information processors

12.1.2 ^{31}P in silicon

12.1.3 N@C60

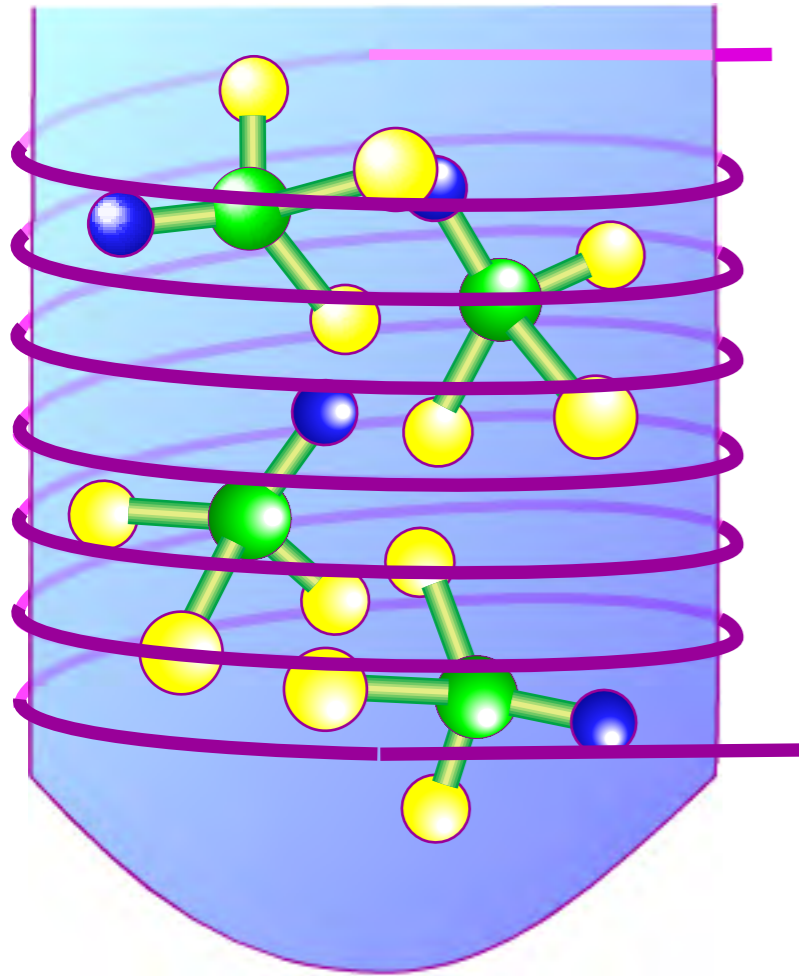
12.1.4 Other proposals

12.1.5 Single-spin readout



Spins in solids

Why Solids ?



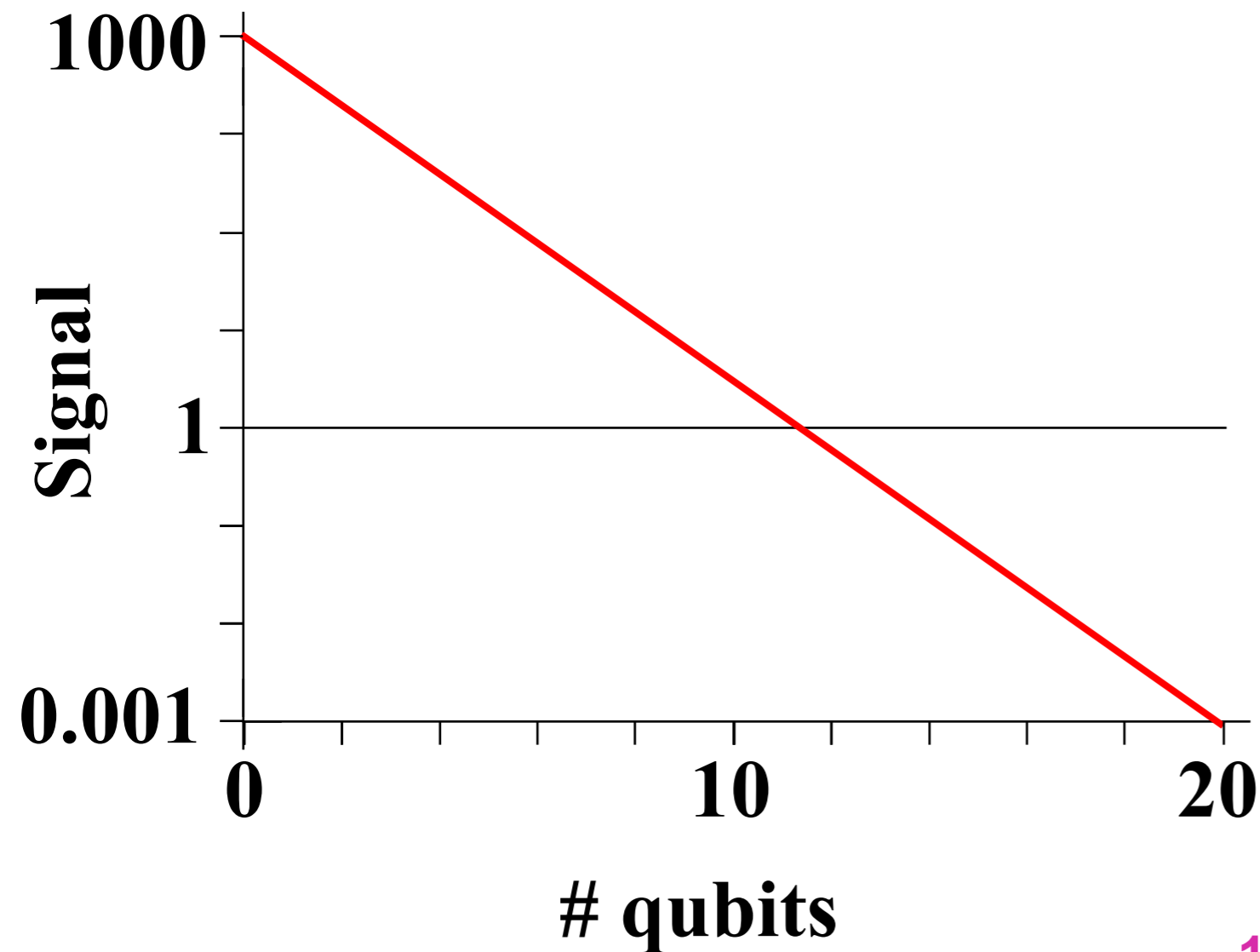
- **Liquid state NMR is an excellent system for small quantum registers.**
- **For > 10 qubits, problems arise:**
 - **addressability**
 - **decoherence**

- **Solids provide possible solutions:**
 - **many qubits**
 - **local addressing**
 - **low temperature**

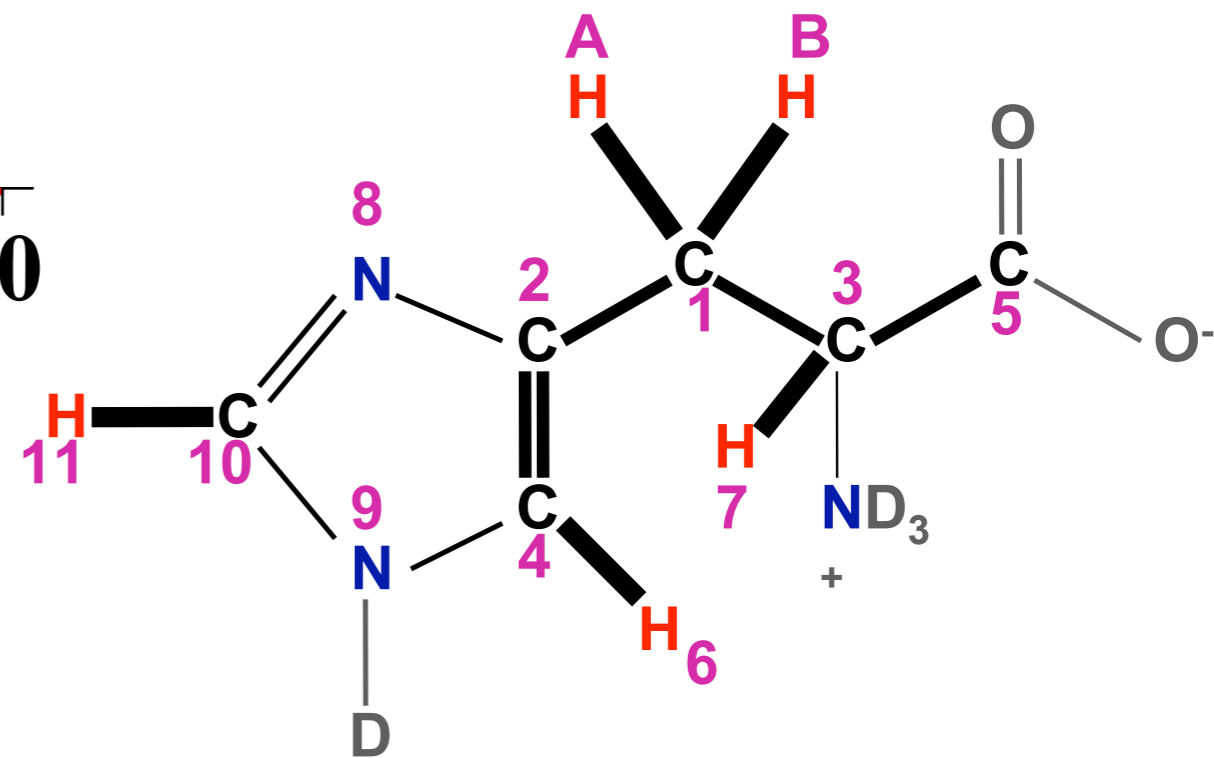


Scaling Behavior

Signal loss for pps preparation



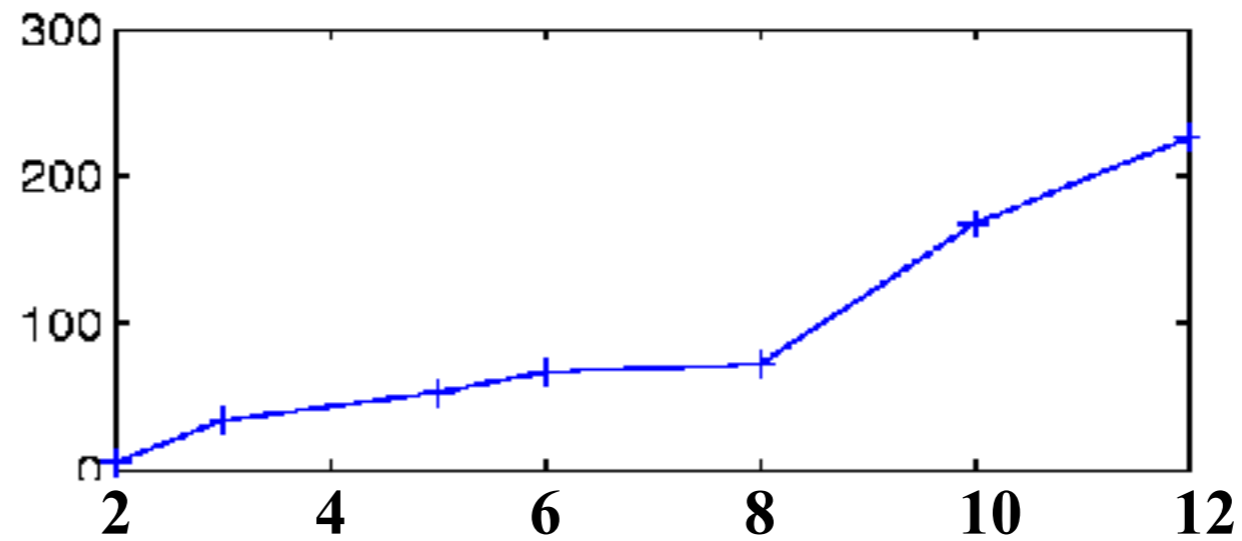
12-qubit system: (Mahesh)



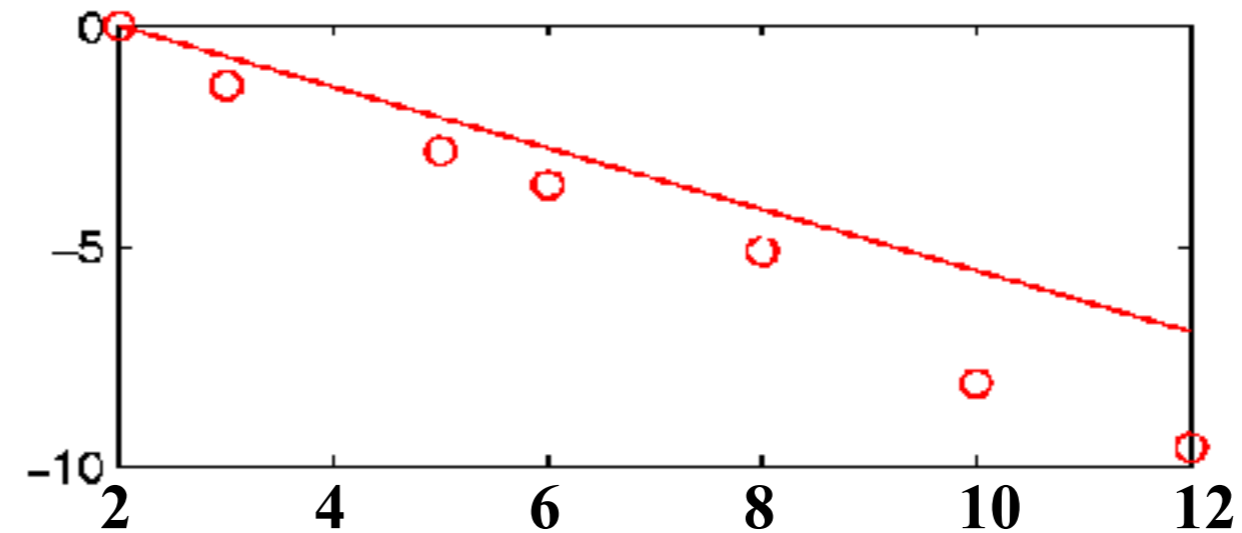
L-Histidine

Scaling Behavior

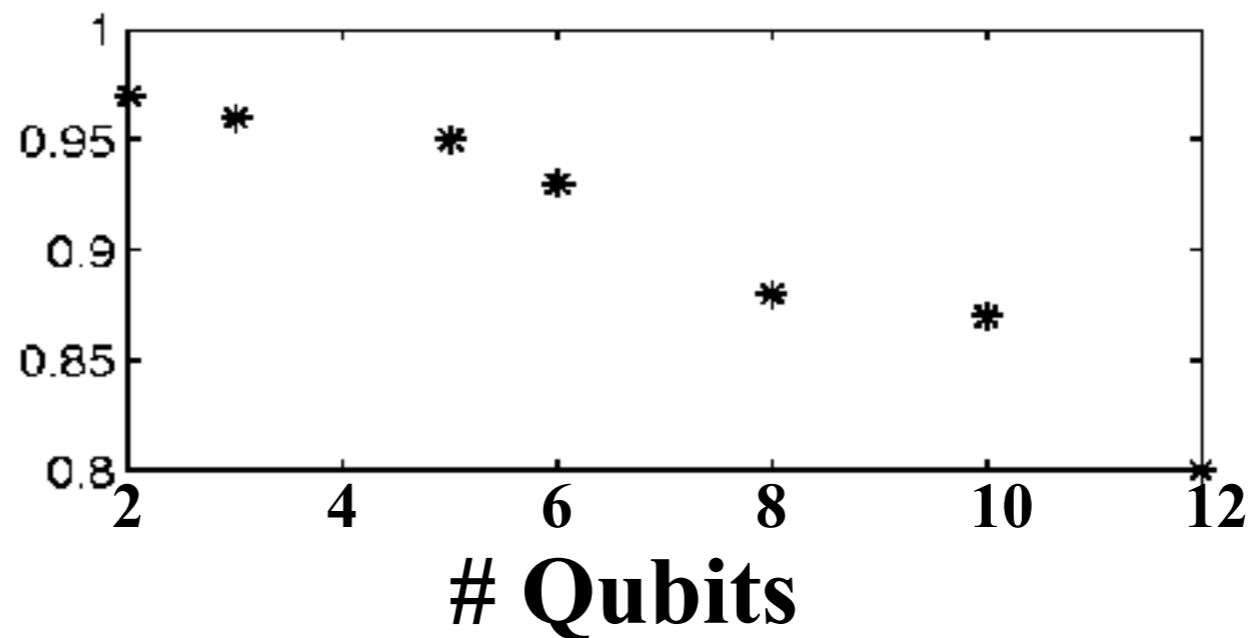
Execution time / ms



ln (signal)



Fidelity (simulated)

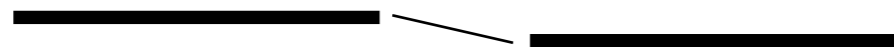


Solid-State NMR

H. Kampermann, and W.S. Veeman, 'Quantum Computing Using Quadrupolar Spins in Solid State NMR', Quantum Information Processing 1, 327 (2002).

^{23}Na : $I = 3/2 = 2$ qubit

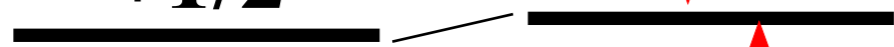
$m_z = -3/2$



$-1/2$



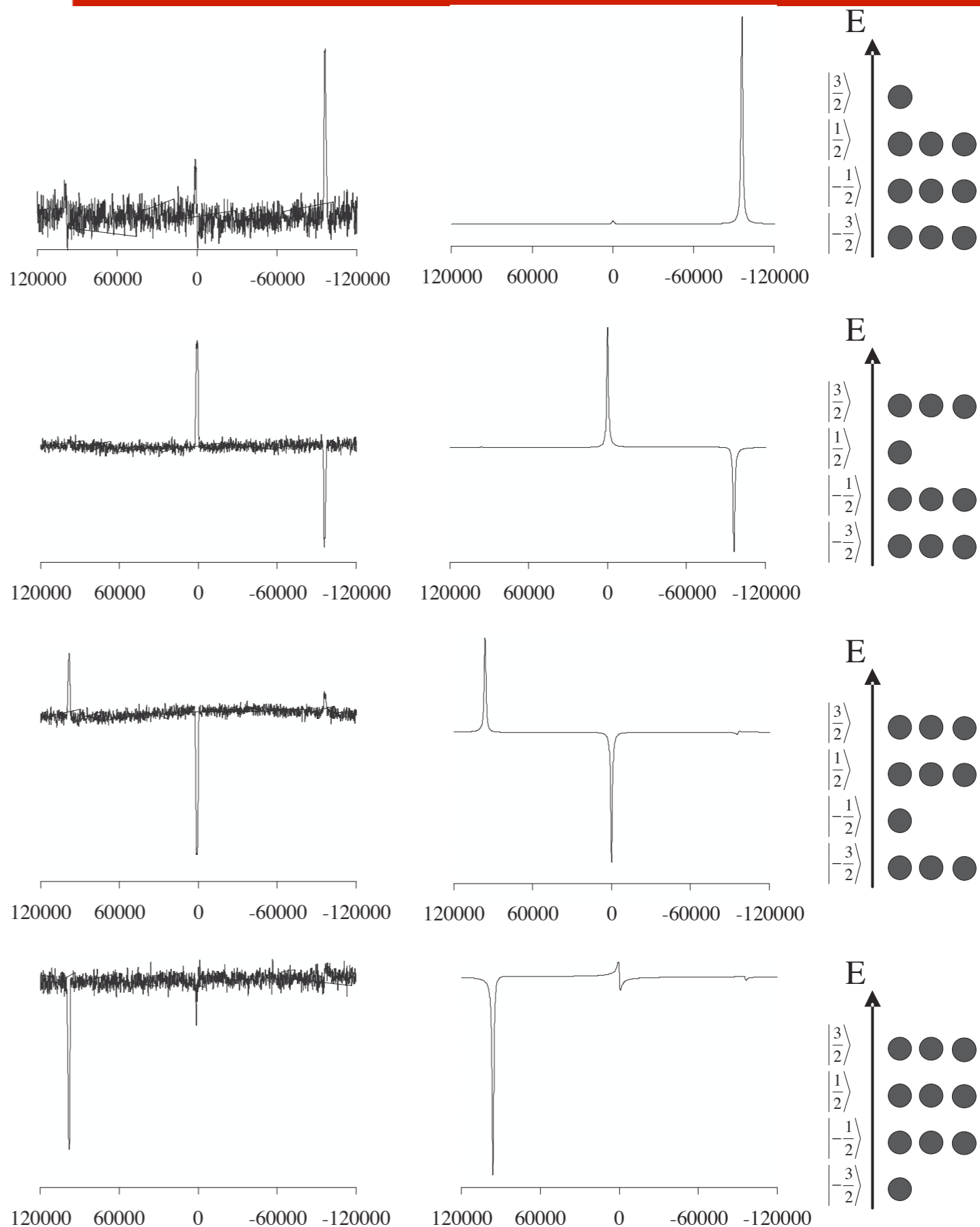
$+1/2$



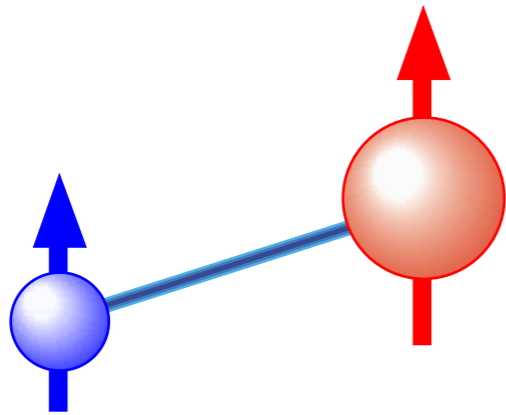
$+3/2$



H_Q



Electron-Nucleus Systems

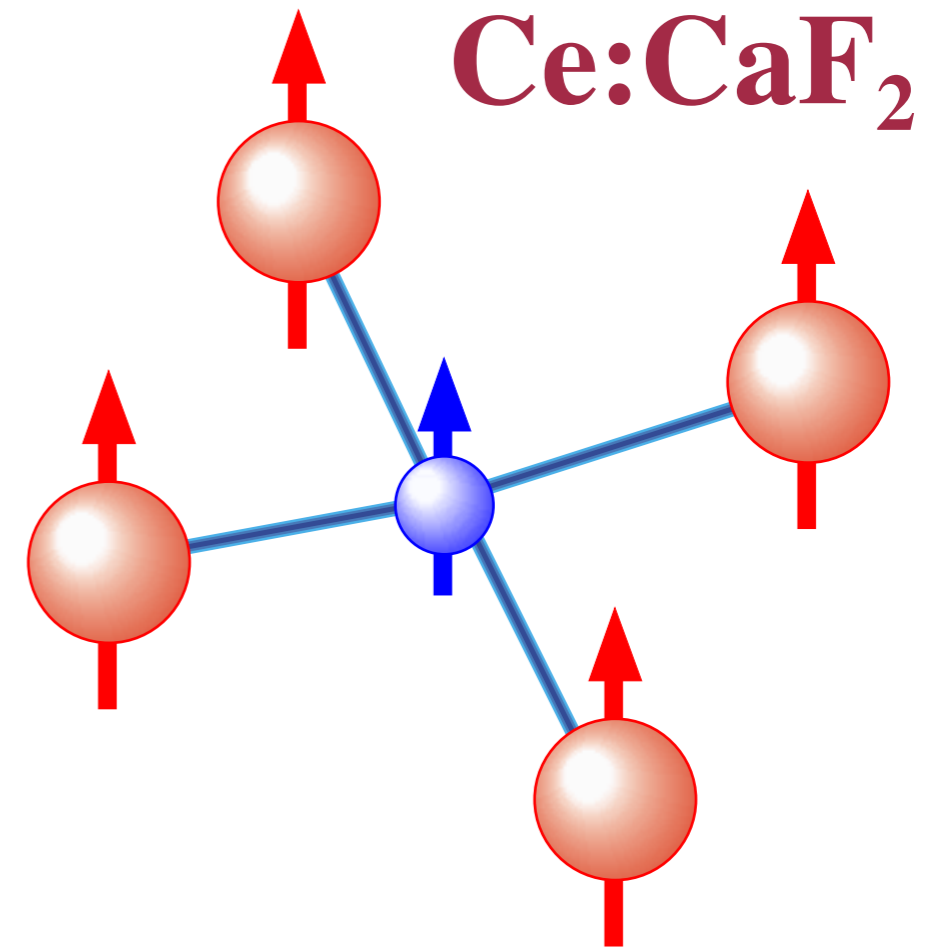


Electron-nucleus entangling in solid malonic acid radical

M. Mehring, J. Mende, and W. Scherer, Phys. Rev. Lett. **90**, 153001 (2003).

Pseudopure state preparation

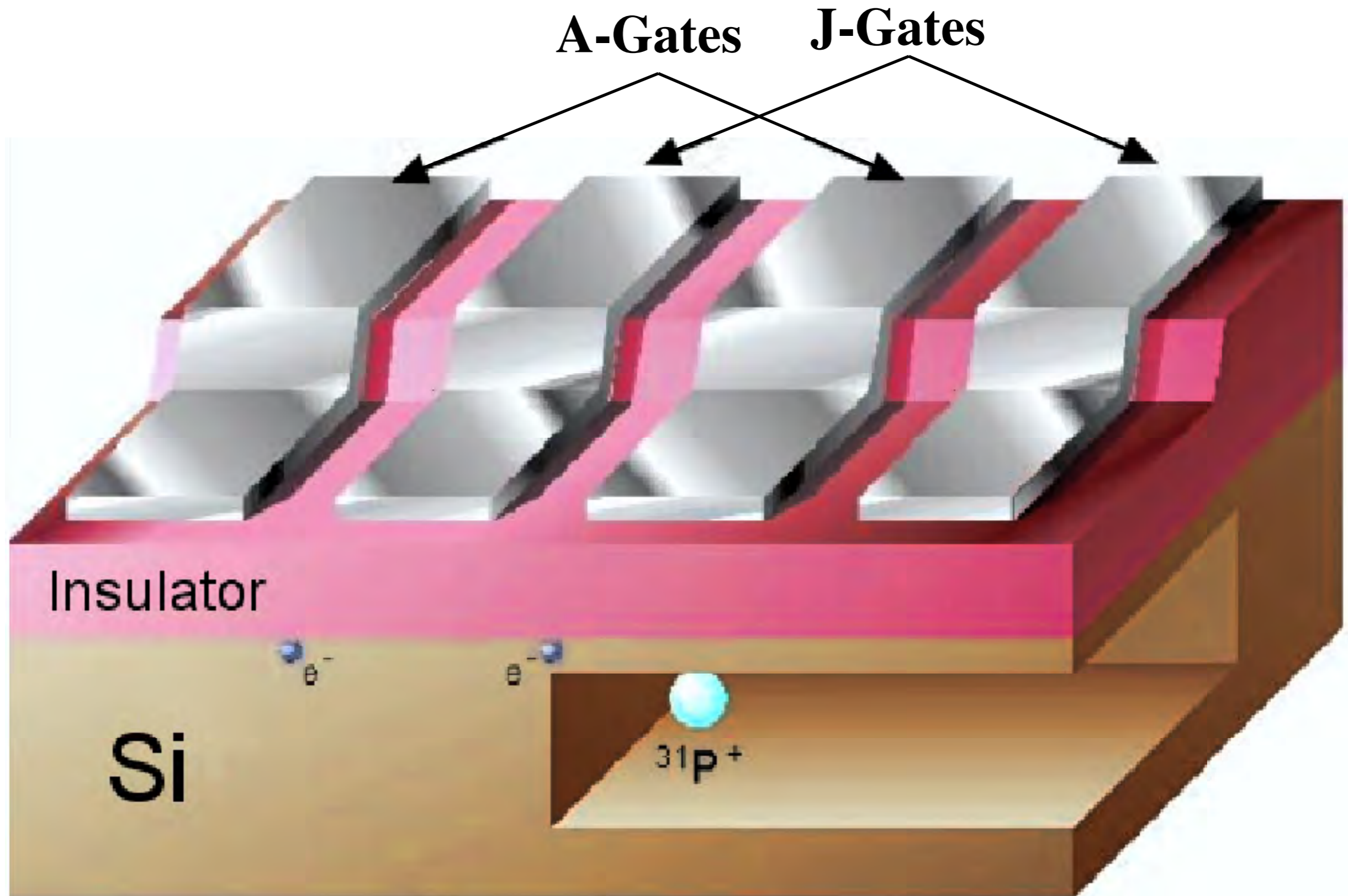
$$\rho_{10} = \begin{pmatrix} 0.01 & 0 & 0 & 0 \\ 0 & -0.06 & 0 & 0 \\ 0 & 0 & 1.02 & 0 \\ 0 & 0 & 0 & 0.03 \end{pmatrix}$$



“S-Bus”

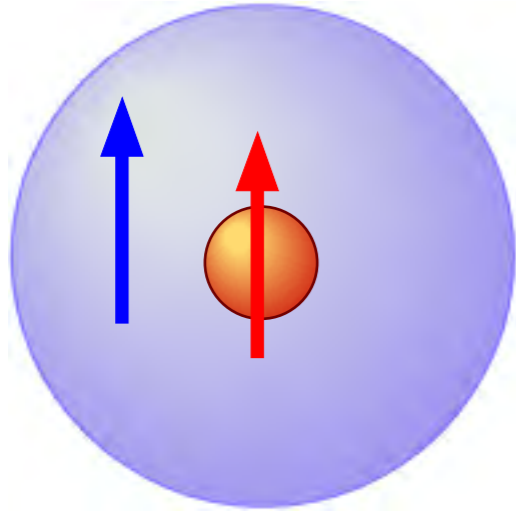
Electron spin mediates nucleus-nucleus couplings

^{31}P in Silicon



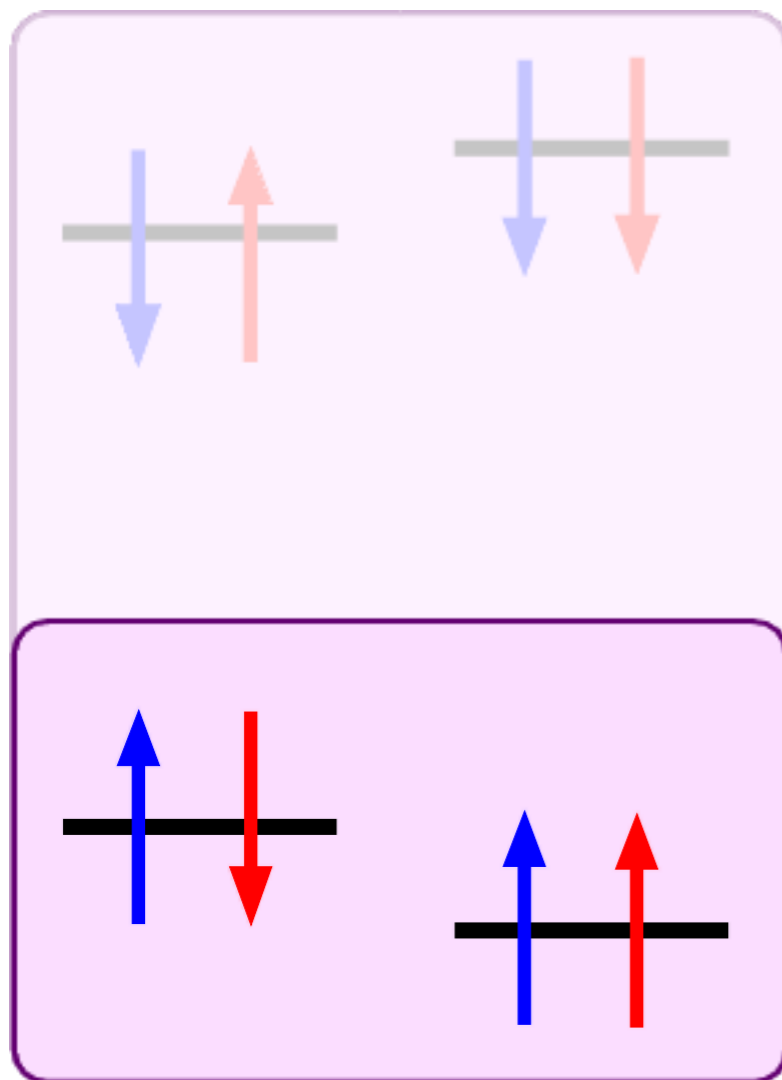
The Qubits

^{31}P = shallow donor



nuclear spin = qubit
electron spin = control

Relevant Interactions



$$\mathcal{H} = \underbrace{-\omega_I I_z}_{\text{nuclear Zeeman}} - \underbrace{\omega_S S_z}_{\text{electron Zeeman}} - \underbrace{a \vec{I} \cdot \vec{S}}_{\text{hyperfine}}$$

Qubit

Control

$|1\rangle$
 $|0\rangle$

Transition frequency $\omega_0 = \omega_I + a/2$
(high field approximation)

Why ^{31}P in Si ?



Long decoherence times:

Electron spin $T_2 \sim 60$ ms in ^{28}Si @ 7K

Nuclear spin $T_1 > 10$ h



Excellent technology base



^{28}Si has nuclear spin 0

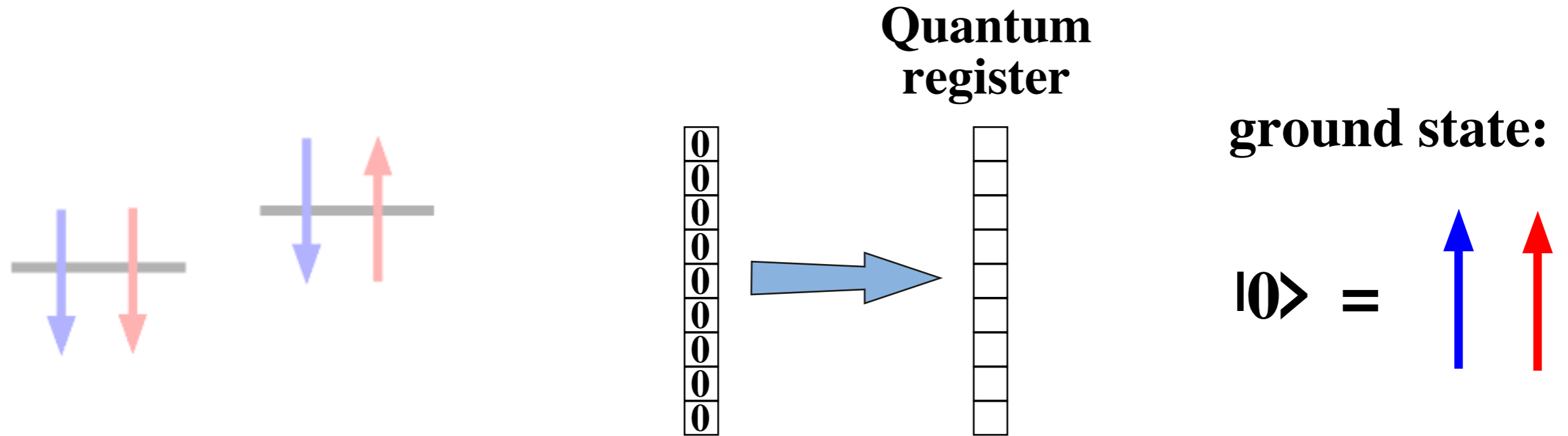
Natural abundance: 4.6% ^{29}Si



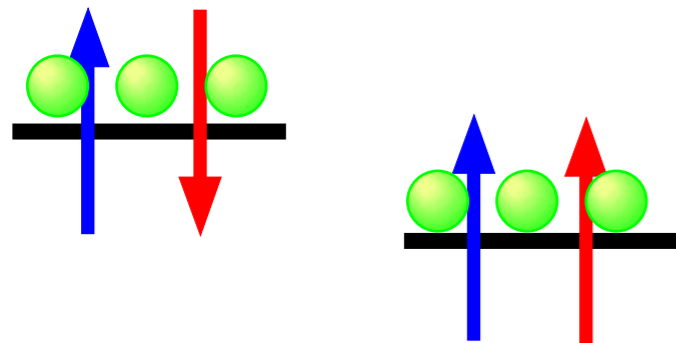
Spin-orbit coupling small

Initialization

**DiVincenzo's rule 2:
Initialization into a well defined state.**



Boltzmann factor @ 100 mK, 2T:

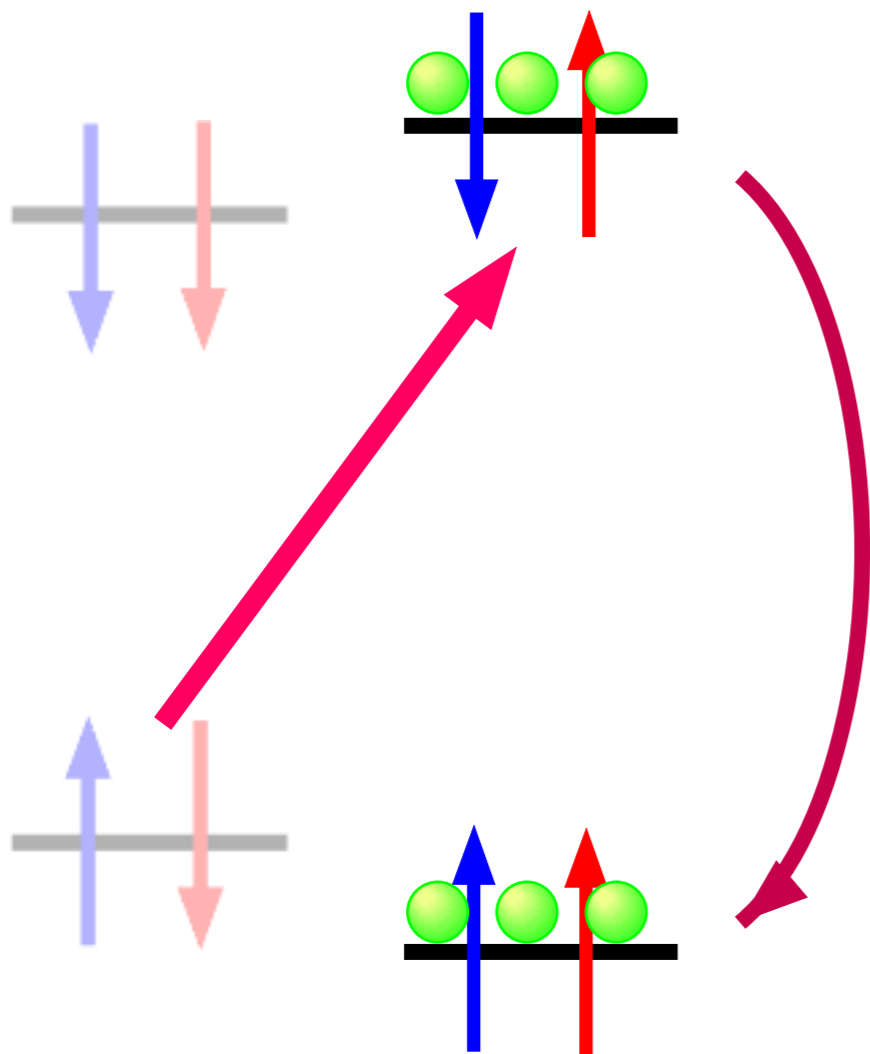


electrons: $\frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}} \approx 1$

nuclei: $\frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}} \approx 5 \cdot 10^{-3}$

Initialization

**Initialize nuclear spin qubit
by microwave pulse**



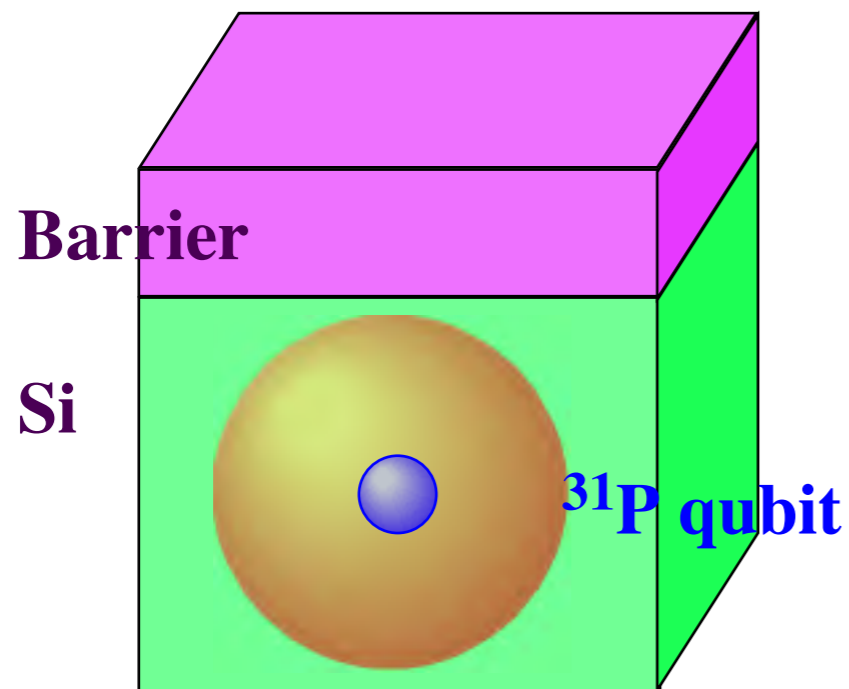
**Relaxation
Dissipation required**

Alternatives:

- **Optical spin injection through SiGe superlattices or quantum dots**
- **Electrical spin injection**
- **Readout**

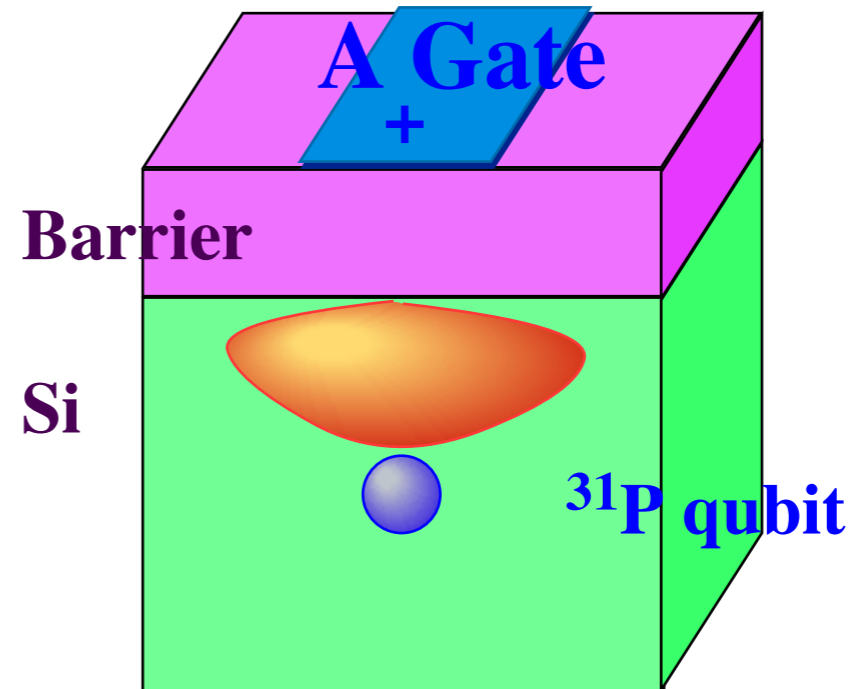
Modify Frequency : A-Gates

$$\mathcal{H} = -\omega_I I_z - \omega_S S_z - a \vec{I} \cdot \vec{S} \quad a \sim |\Psi_{\text{el}}(\vec{r}_n)|^2$$



$|\Psi_{\text{el}}(\vec{r}_n)|$ large

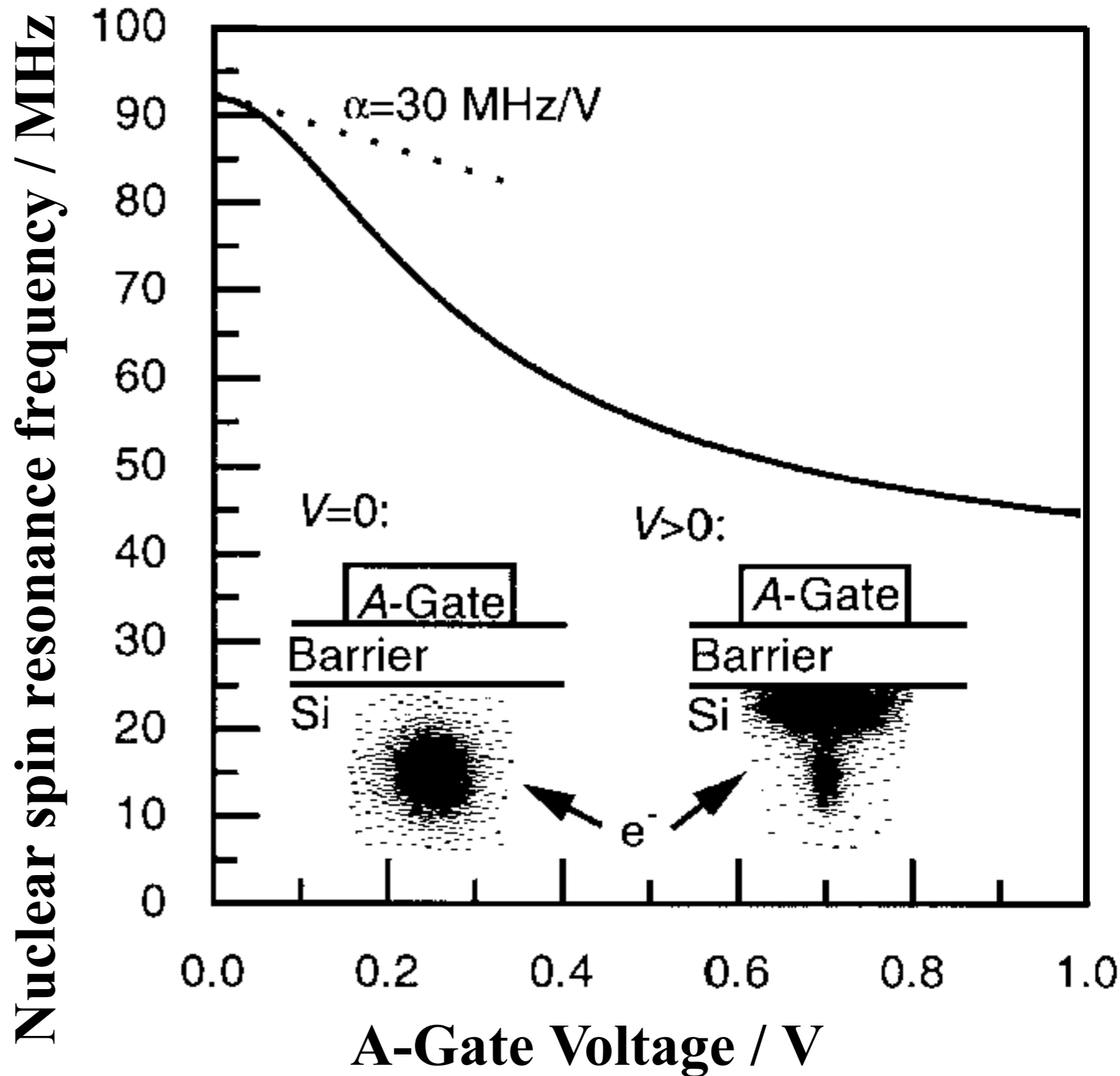
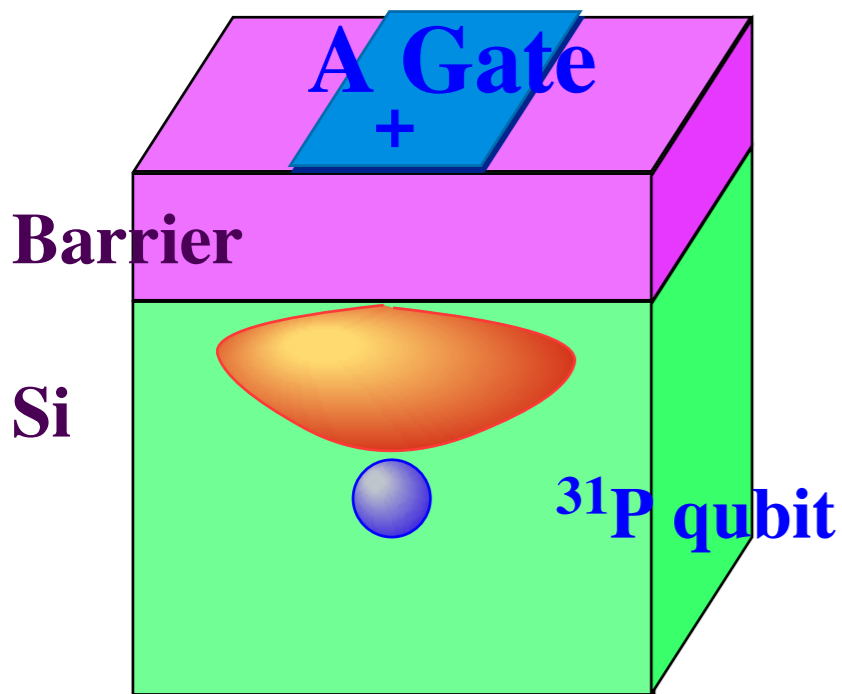
$$\nu_0 \sim 90 \text{ MHz}$$



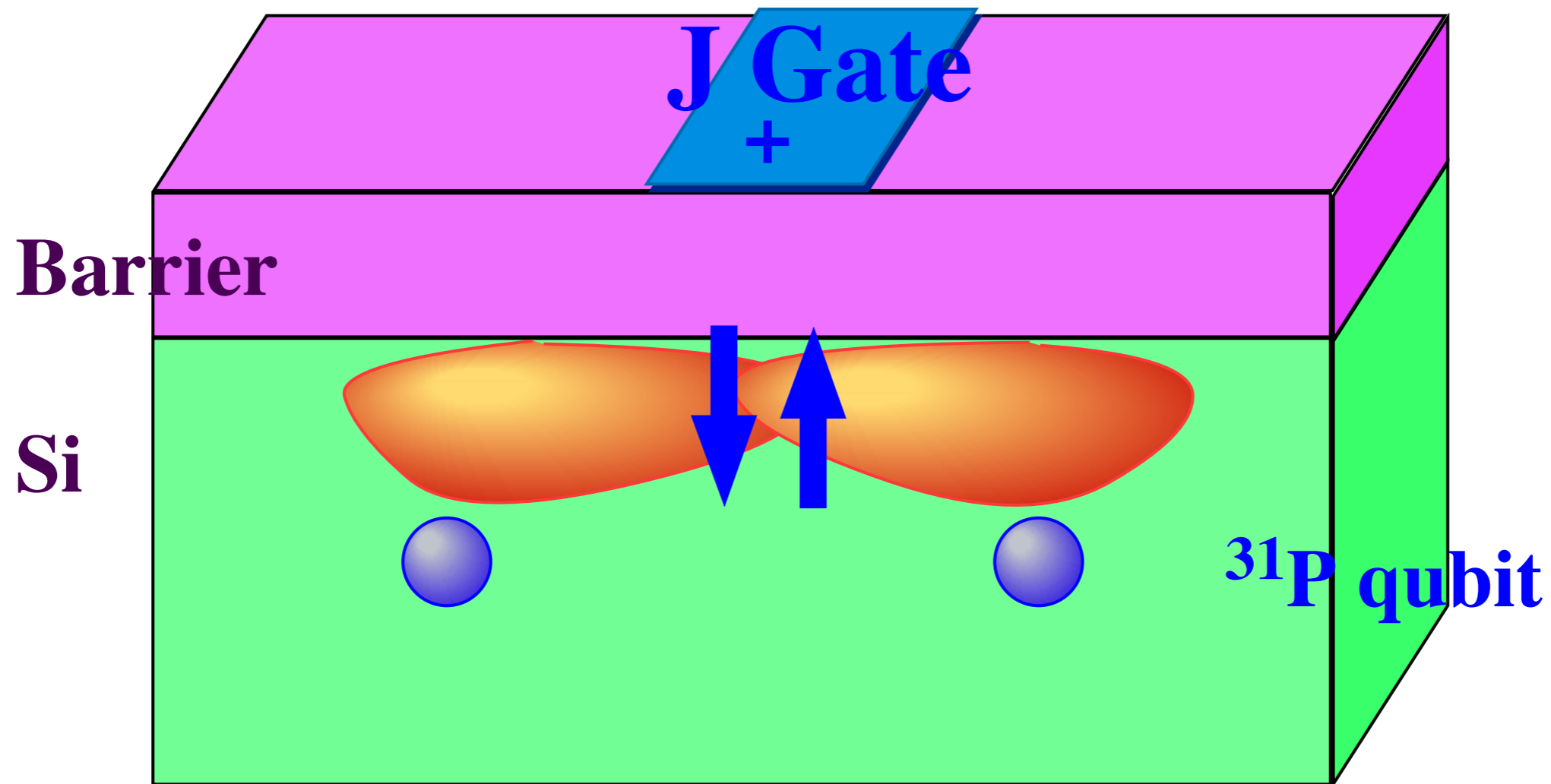
$|\Psi_{\text{el}}(\vec{r}_n)|$ small

$$\nu_0 \sim 50 \text{ MHz (for } U \sim 0.7 \text{ V)}$$

Electronic Frequency Tuning



Modify Couplings : J-Gates

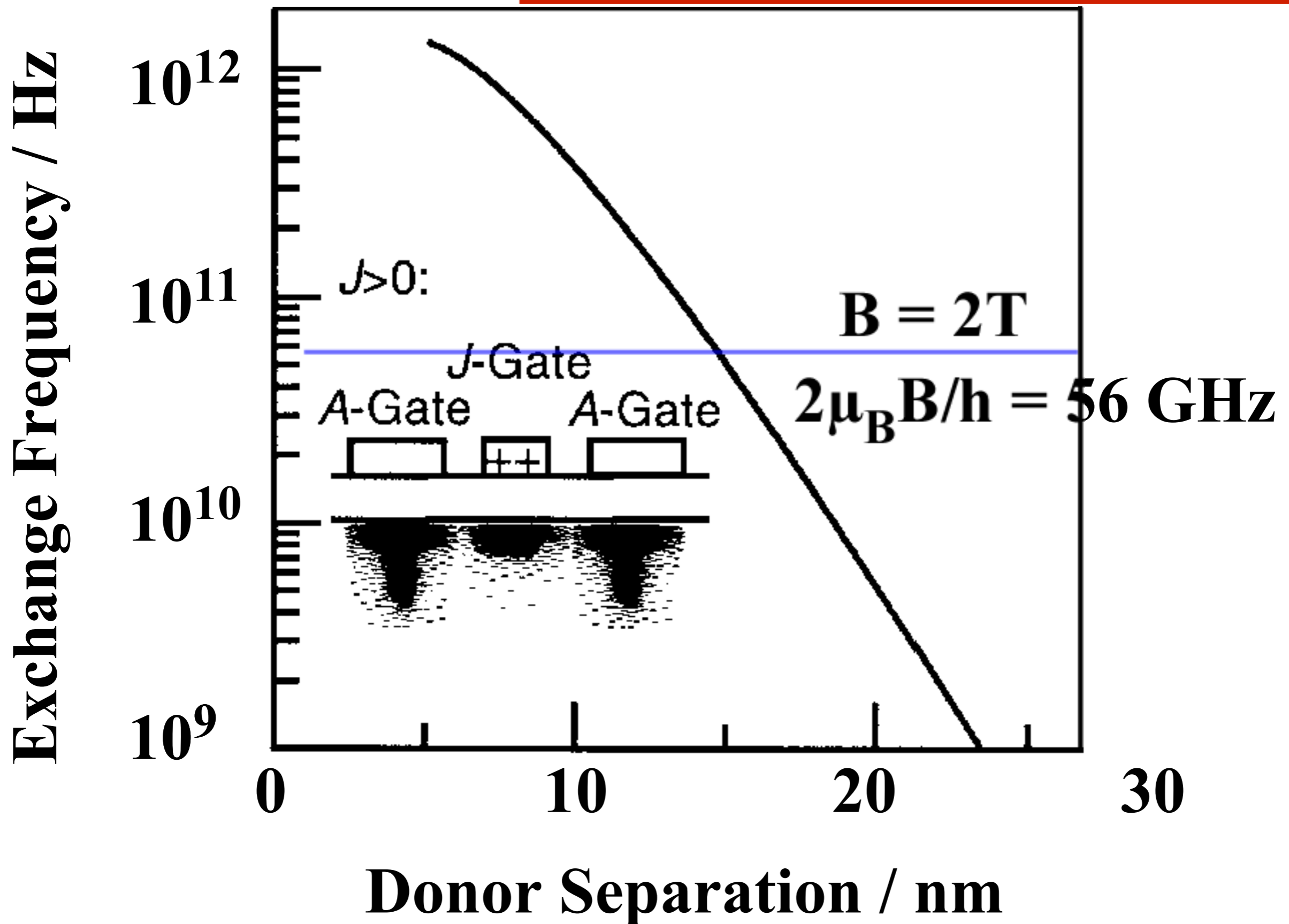


J gate draws electrons into overlap region

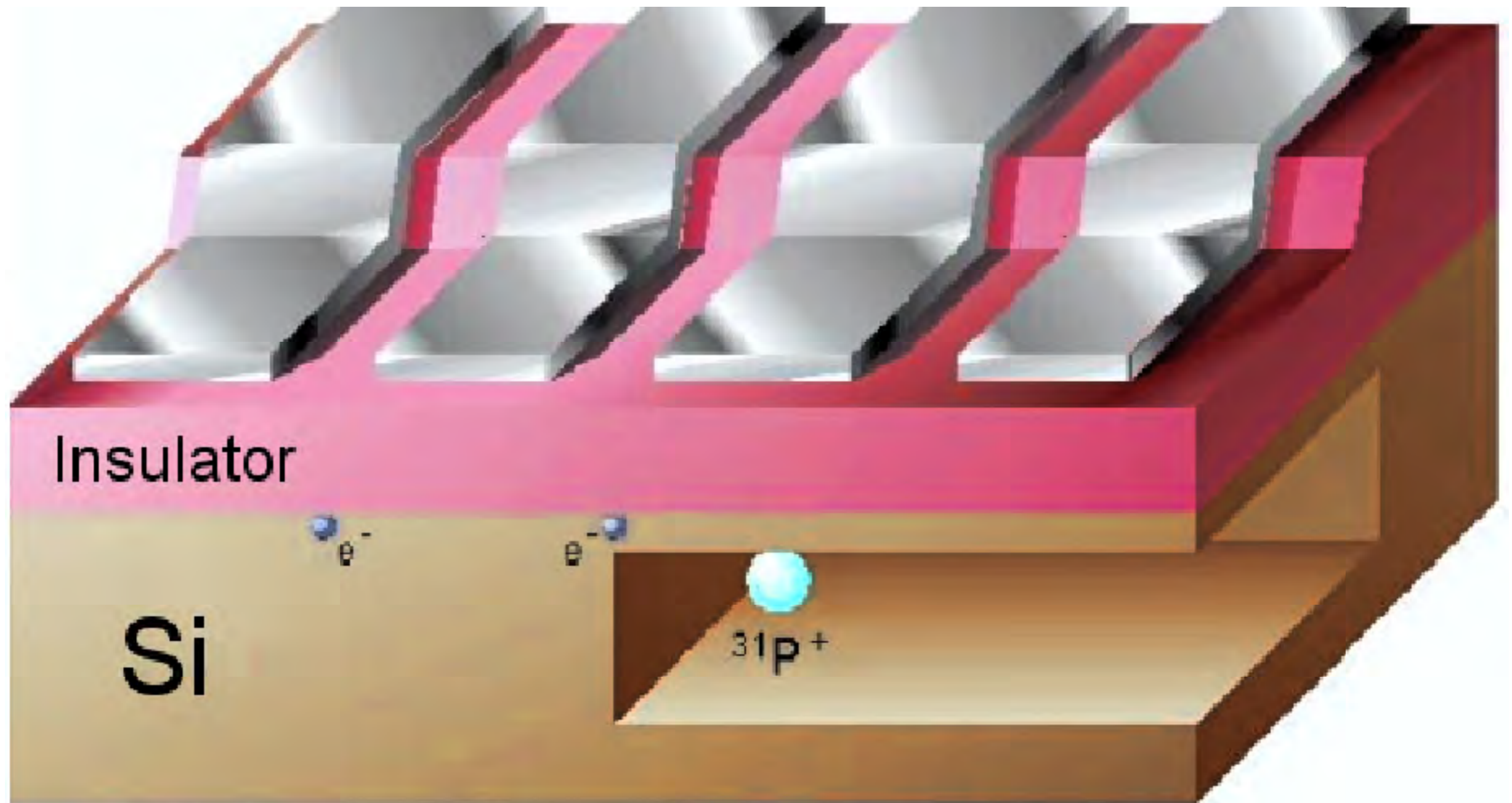
coupling operator: $\mathcal{H}_J = J \vec{I}_1 \cdot \vec{I}_2$

effective qubit-coupling: 75 kHz depends on B-field, gates

Tuning of Couplings



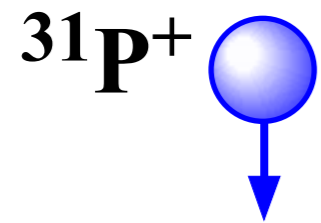
Donor Placement



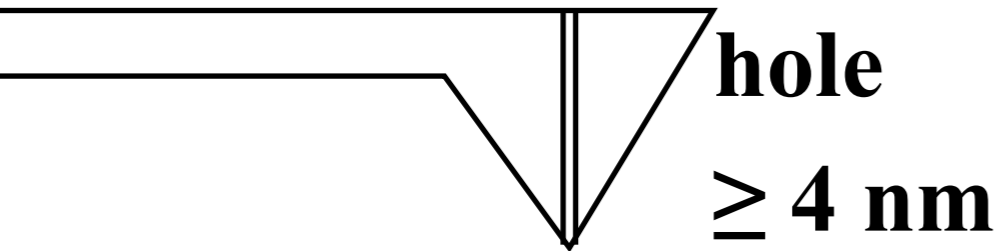
How to put exactly one atom at the right position ?

^{31}P Implantation

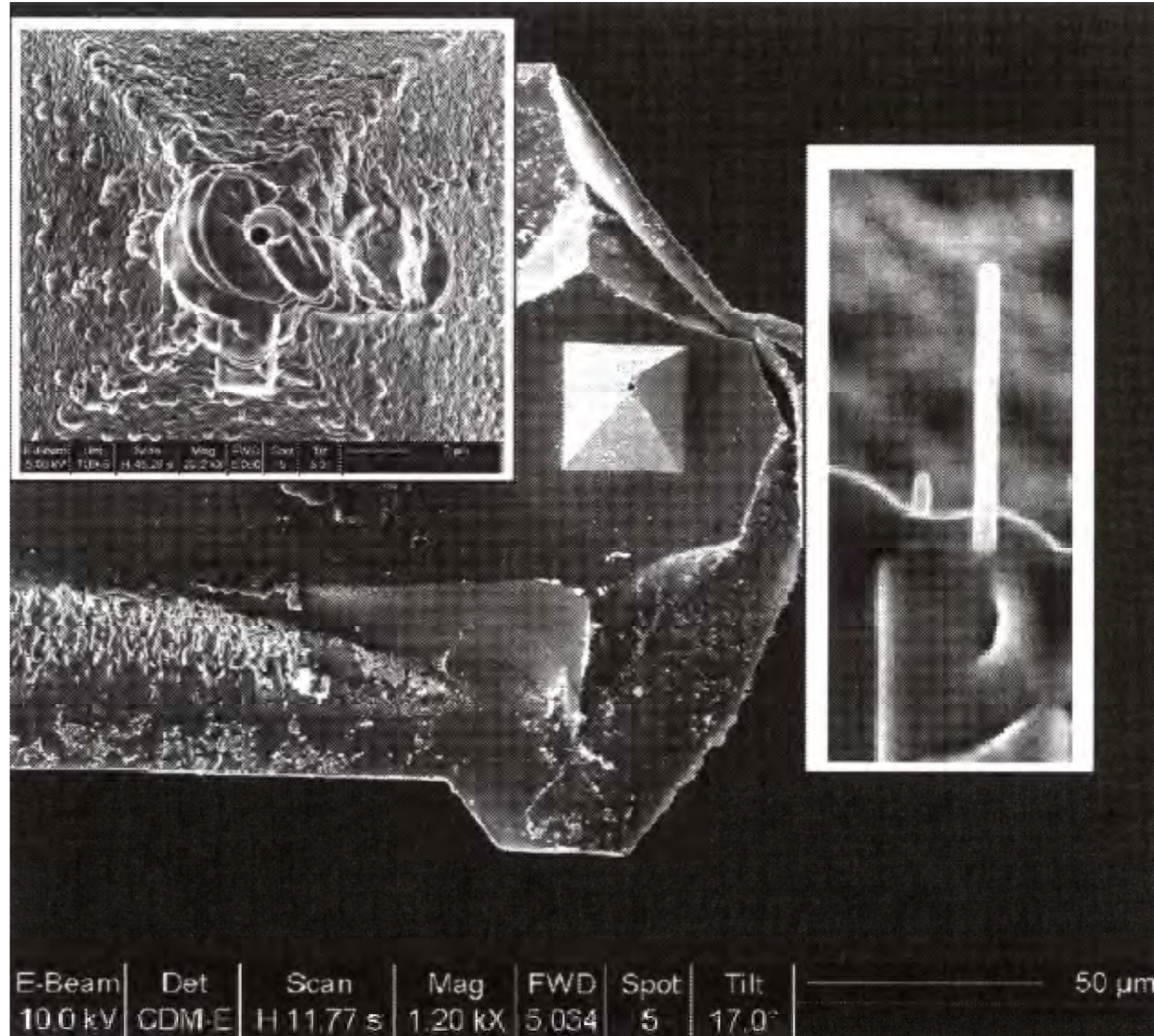
Focused ion beam



AFM Tip



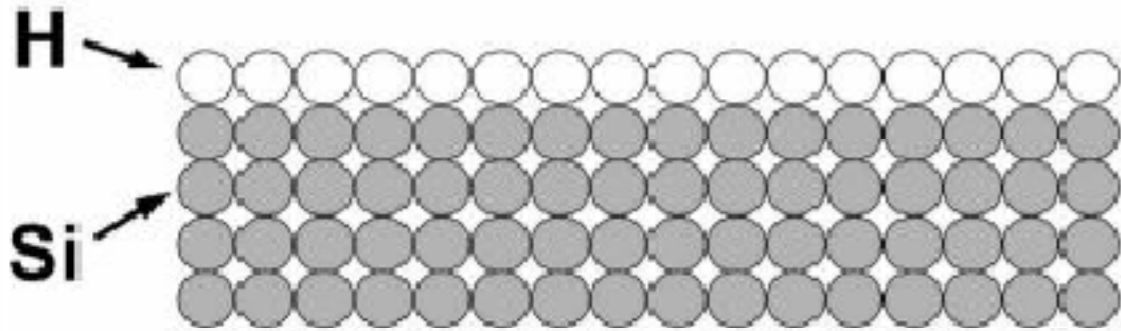
Si substrate



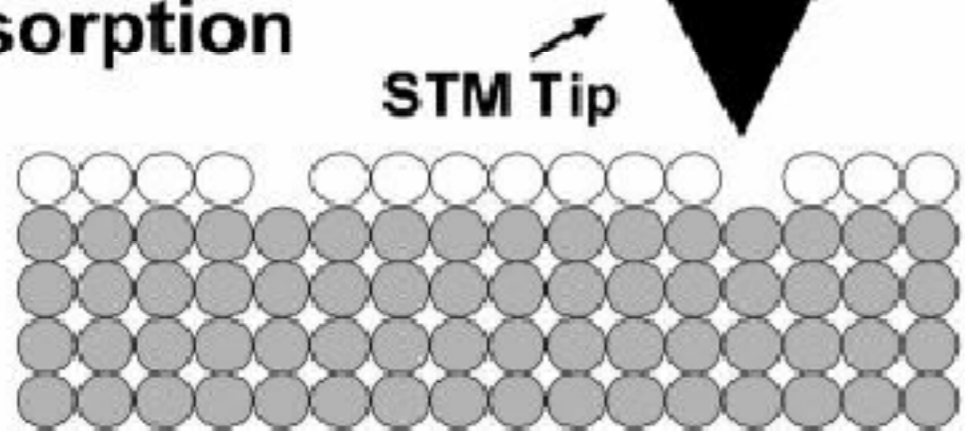
Depositing ^{31}P

Phys. Rev. B, 64:161401 (2001).

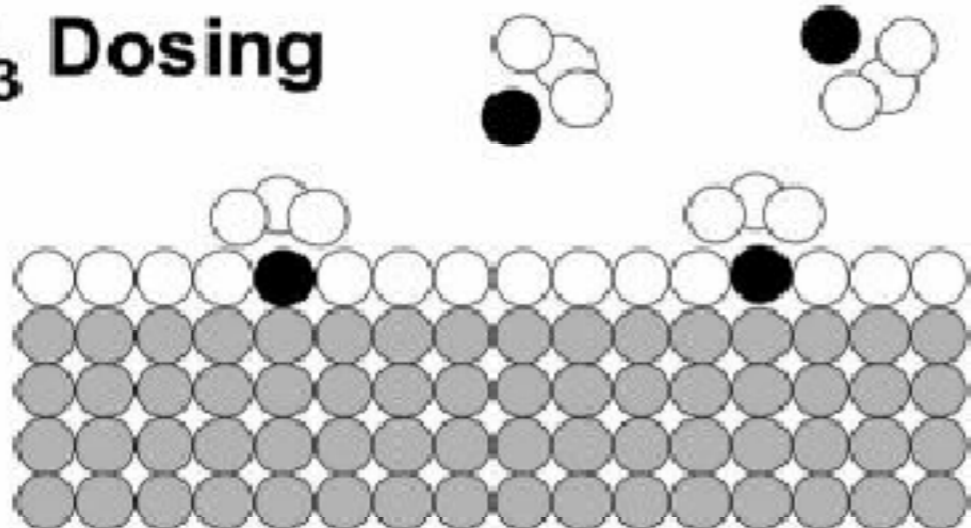
Mono-hydride Deposition



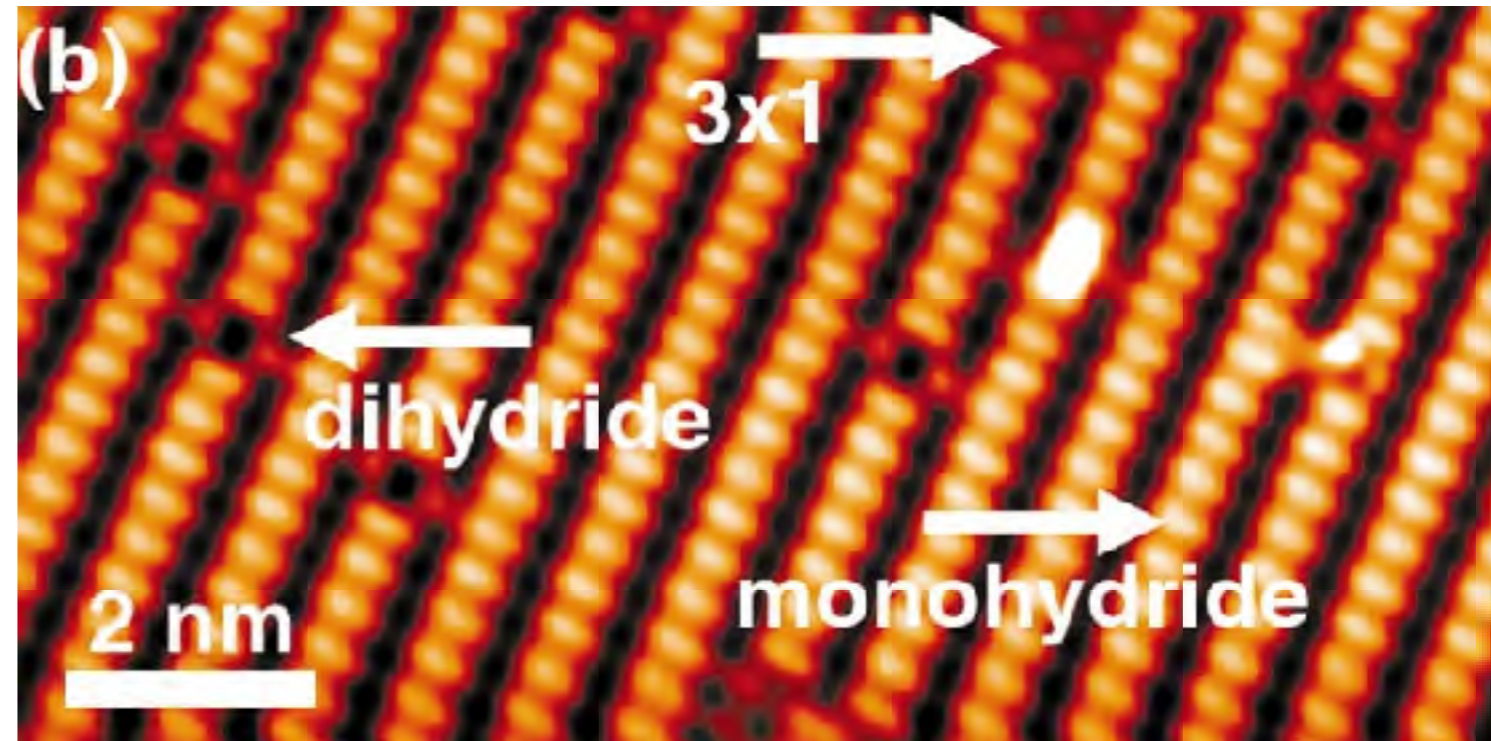
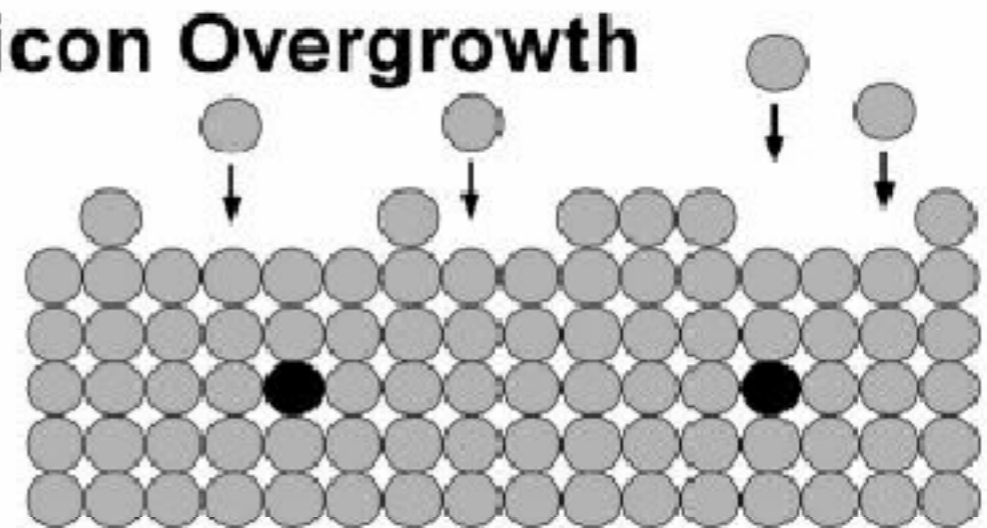
Hydrogen Desorption



PH_3 Dosing



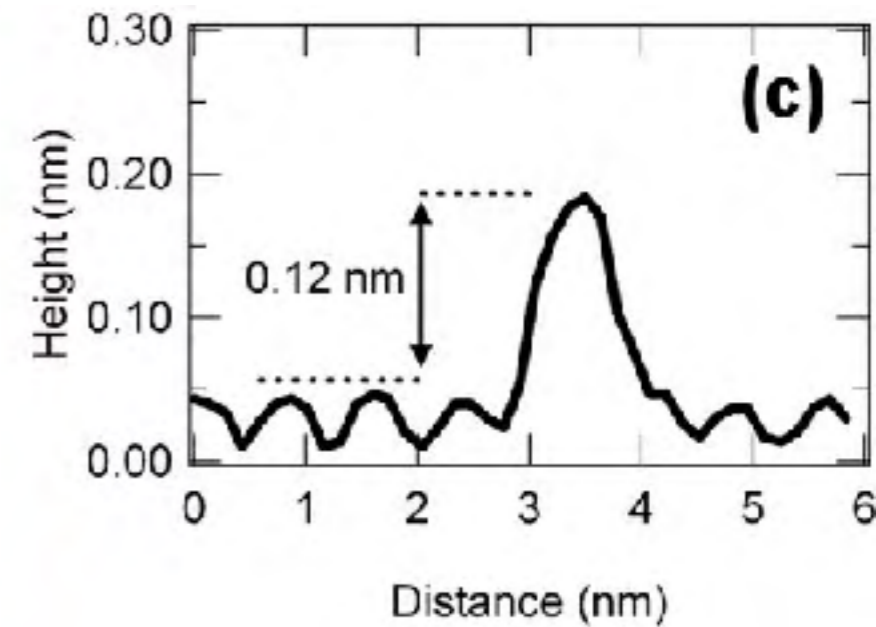
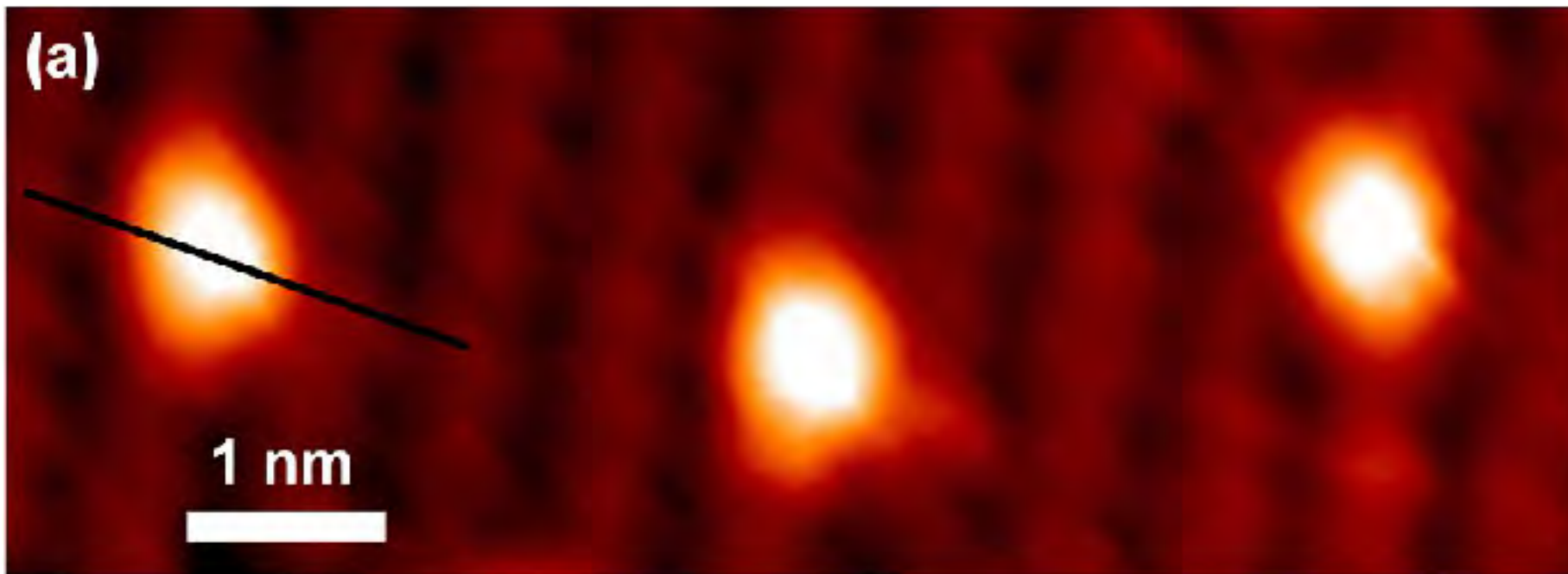
Silicon Overgrowth



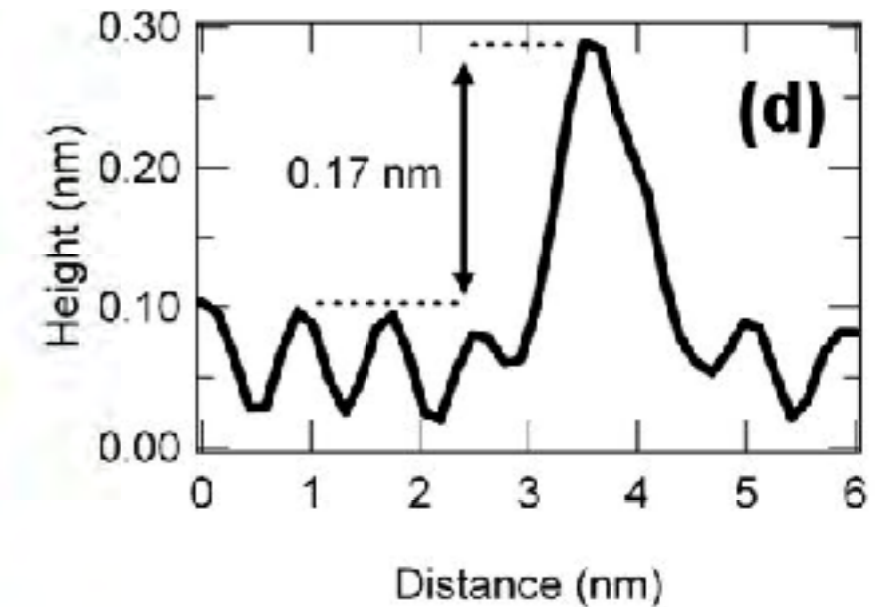
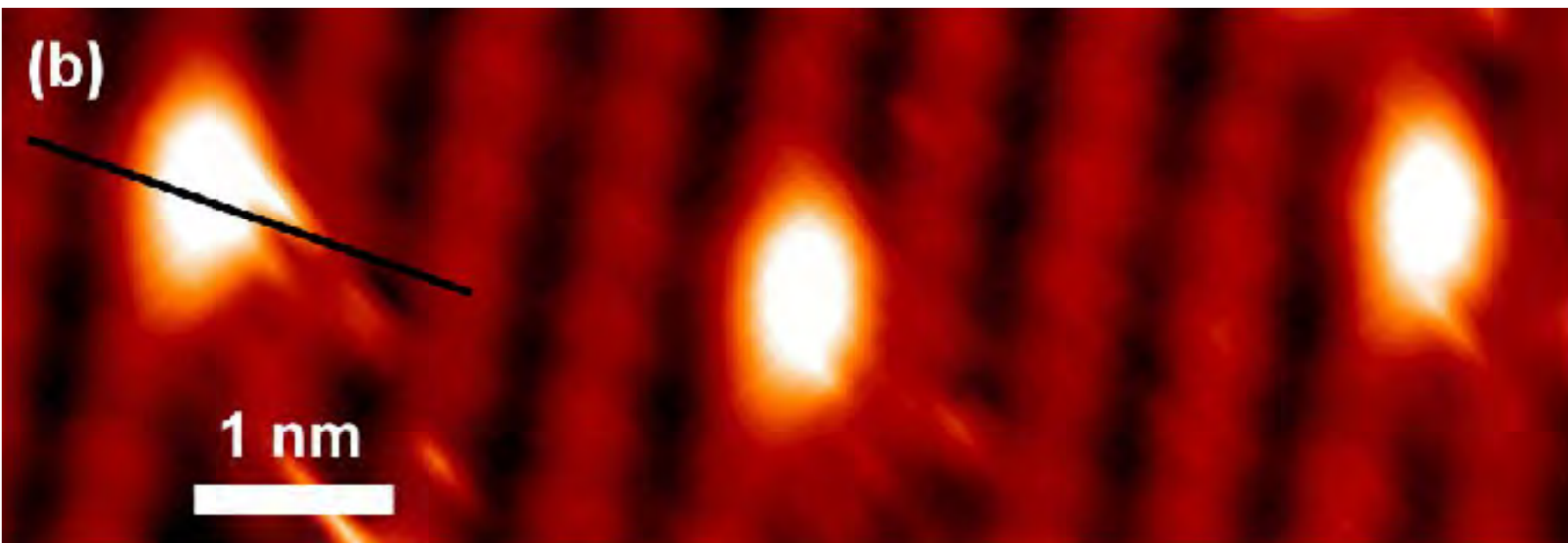
STM of H-terminated Si surface

Chemisorbed ^{31}P

Hydrogen desorbed



After PH_3 dosing



Phys. Rev. B, 64:161401 (2001).

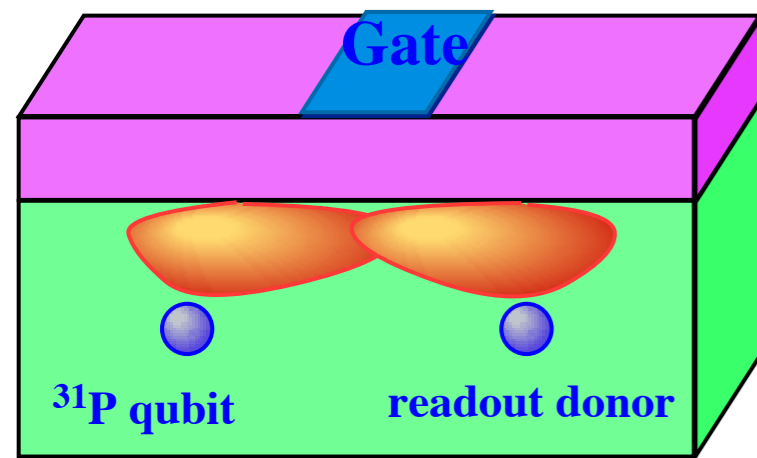
Qubit Readout

DiVincenzo's rule 5: Qubit-selective readout.

1) Transfer qubit to electron spin

2) Transfer to readout donor

3) Detection of singlet state



Scan converts $|0\rangle$ to electron singlet state

electron spins

$|\downarrow\downarrow\rangle$

$|\uparrow\downarrow+\downarrow\uparrow\rangle$

Energy

nuclear spin

$|1\rangle = \downarrow$

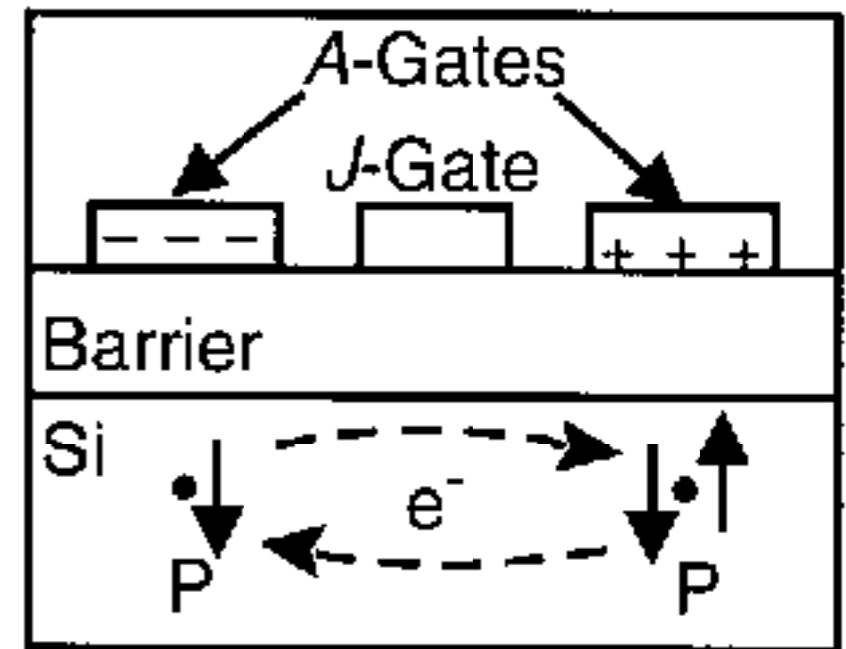
$|0\rangle = \uparrow$

$|\uparrow\downarrow-\downarrow\uparrow\rangle$

singlet pair can form D^-

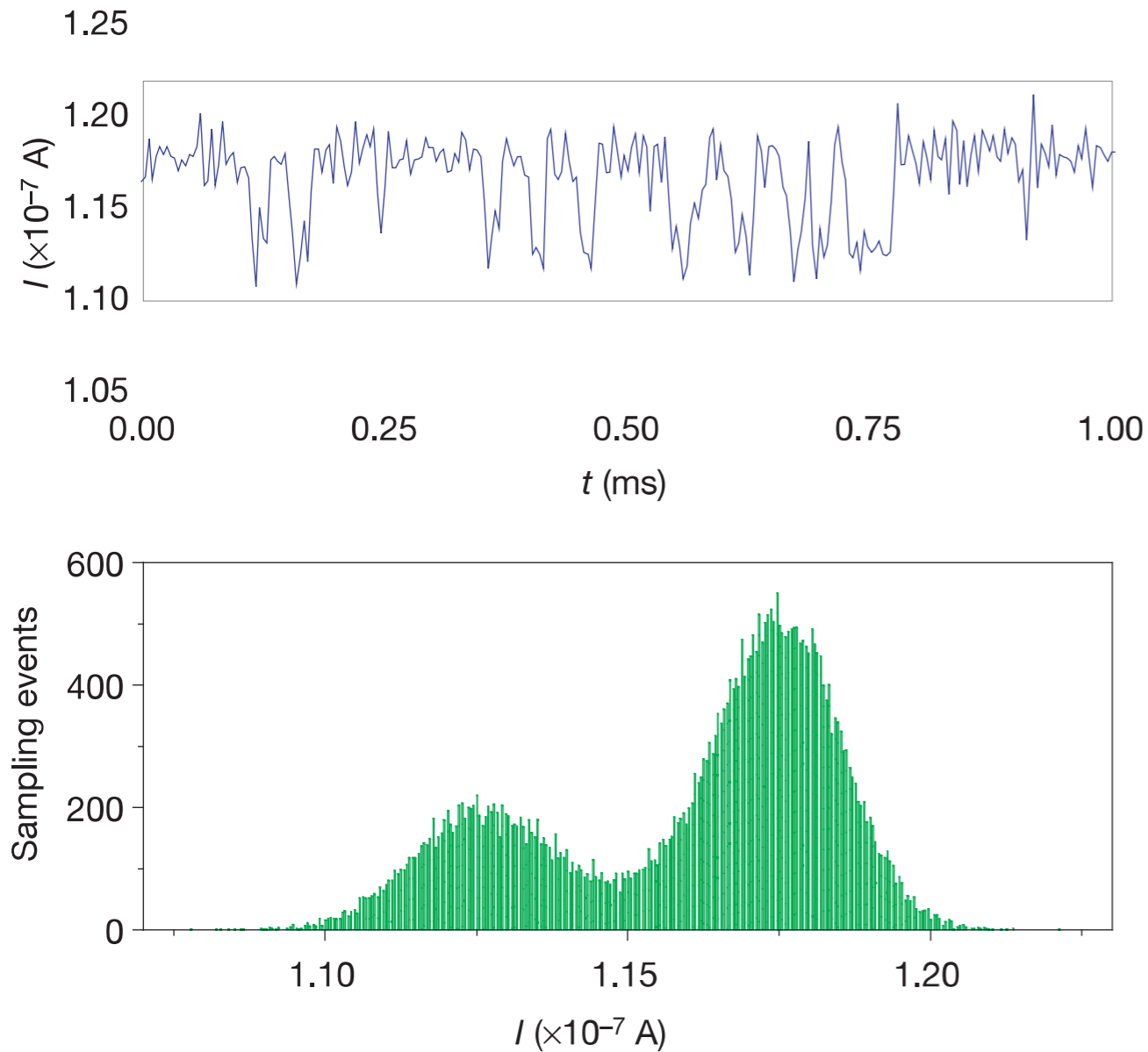
electrostatic detection of D^-

Coupling J



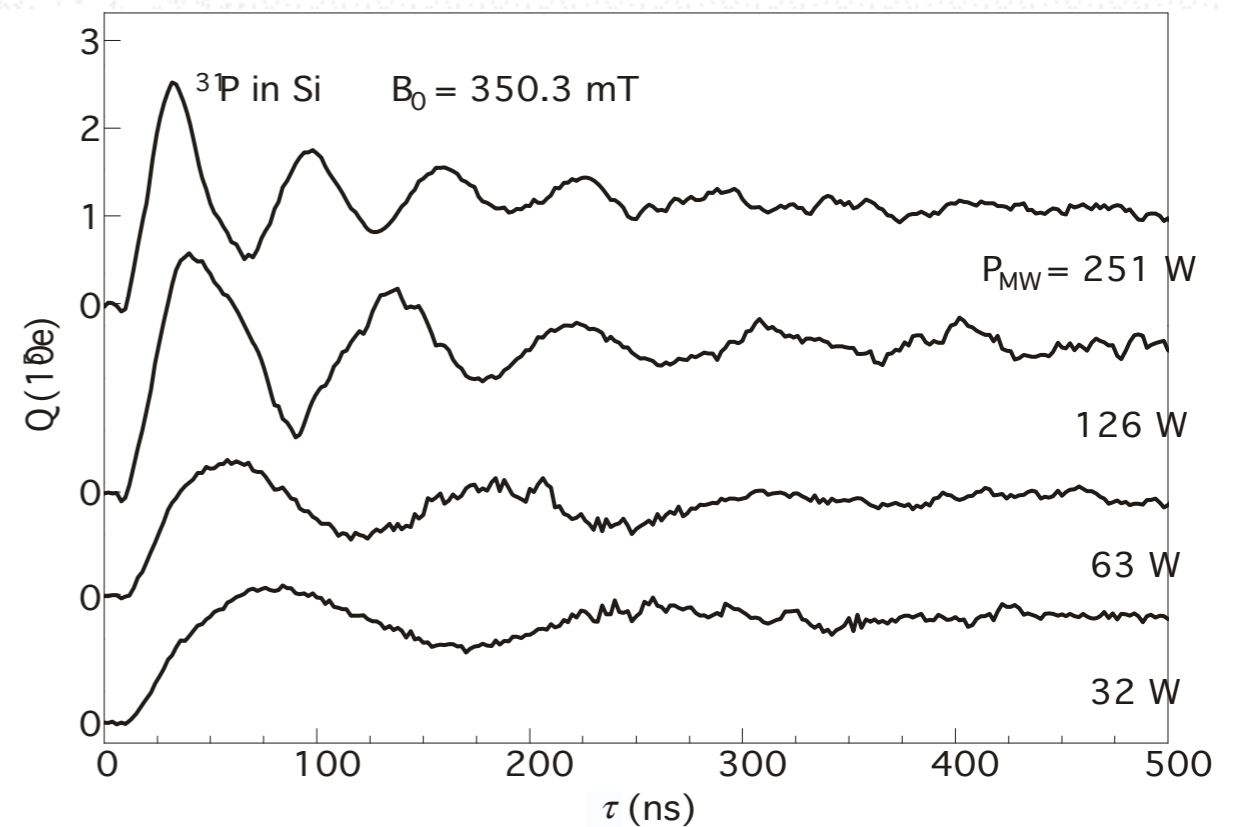
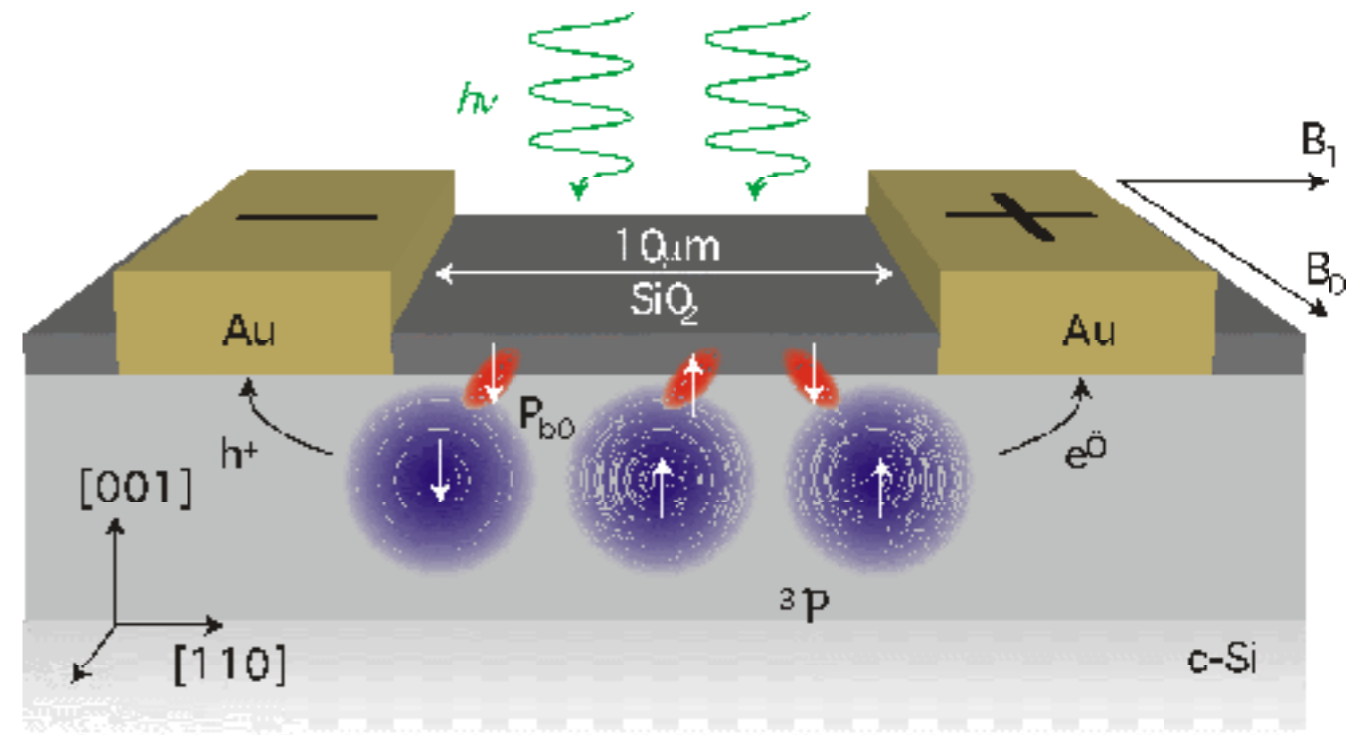
Current State

Single spin ESR



Xiao et al., Nature, 430, 435 (2004).

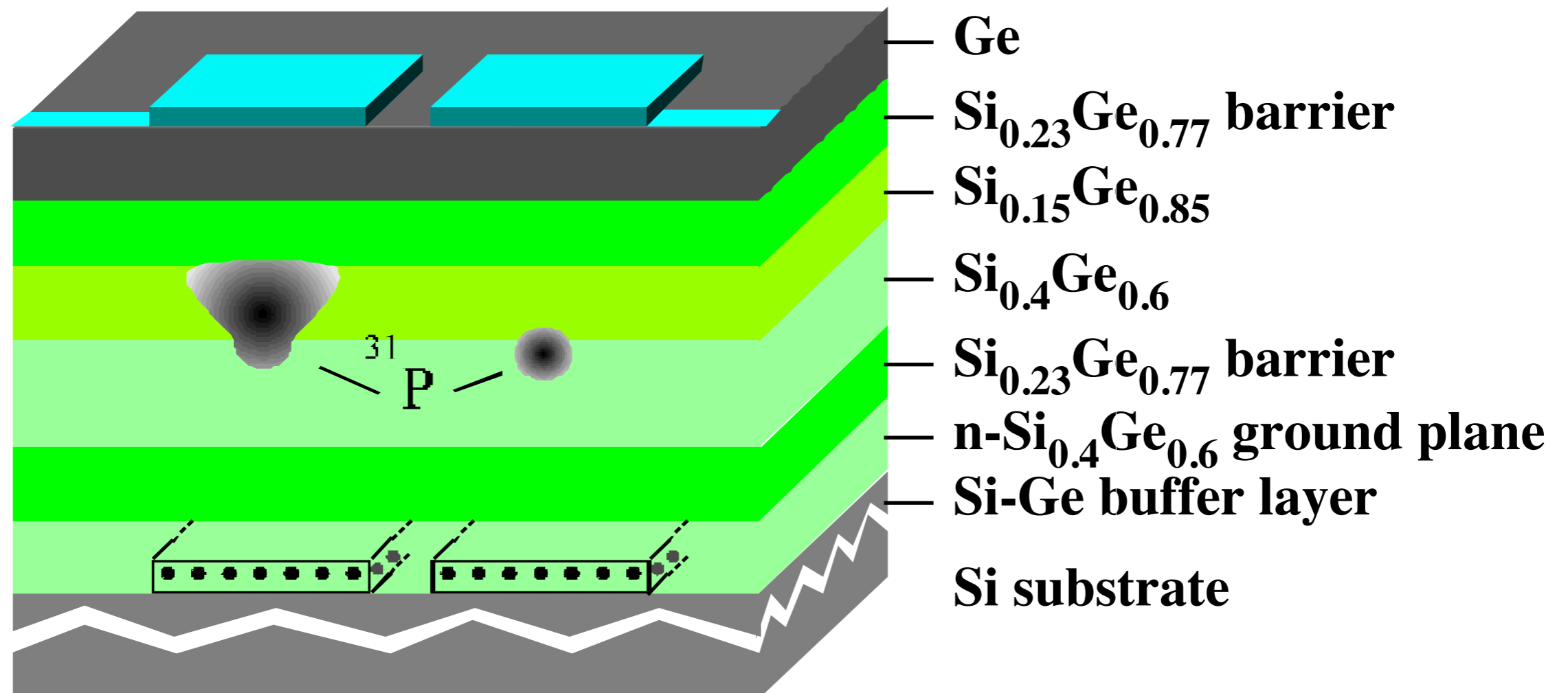
Coherent excitation



Stegner et al., Nature Physics 2, 835–838 (2006).

SiGe Spin-Transistor

R. Vrijen et al, Phys. Rev. A 62, 012306 (2000)



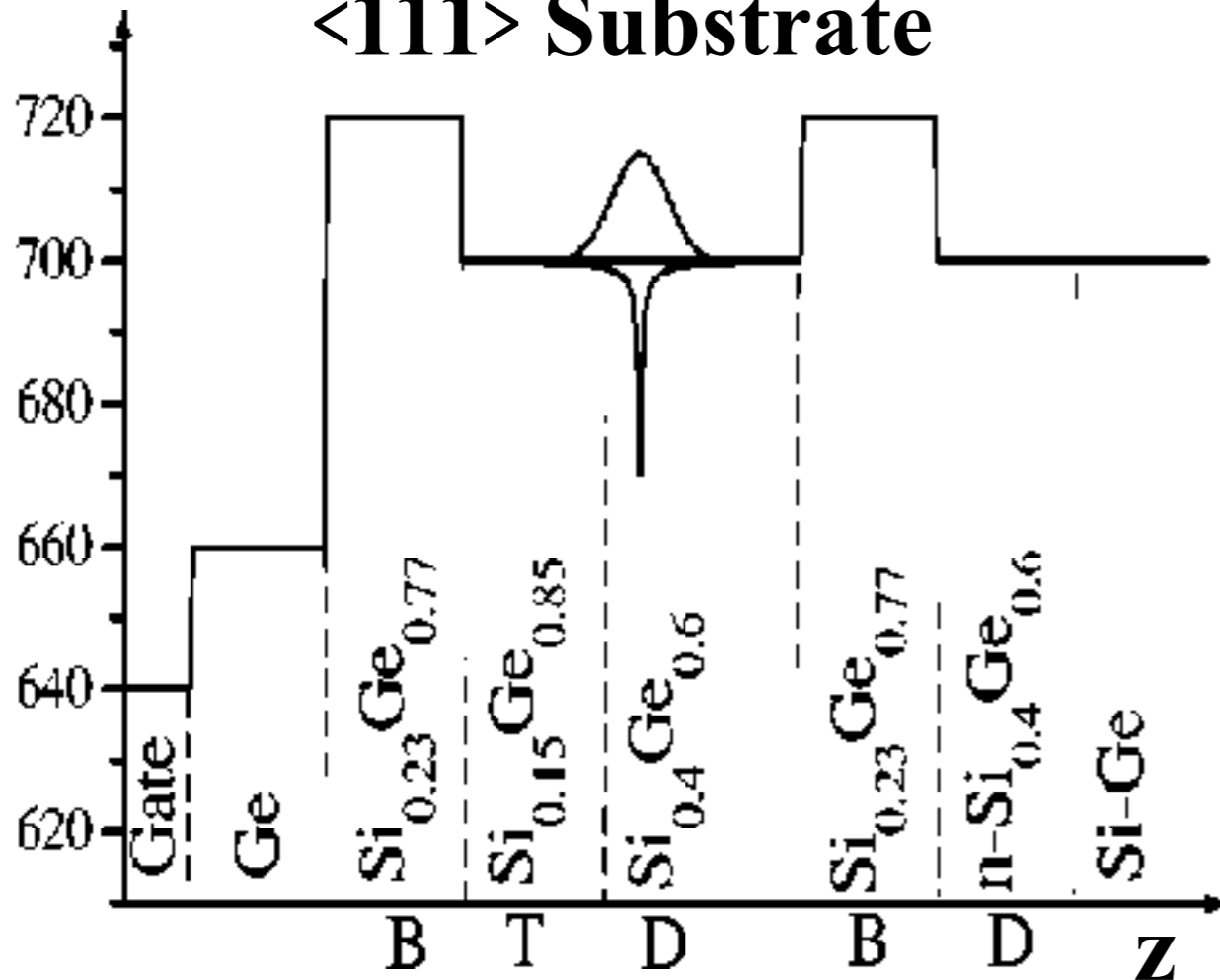
Modification of Kane proposal:

- Use SiGe heterostructure
- Use electron spin instead of nuclear
- Only one type of gates needed

g-factor Tuning

gate off

$\langle 111 \rangle$ Substrate

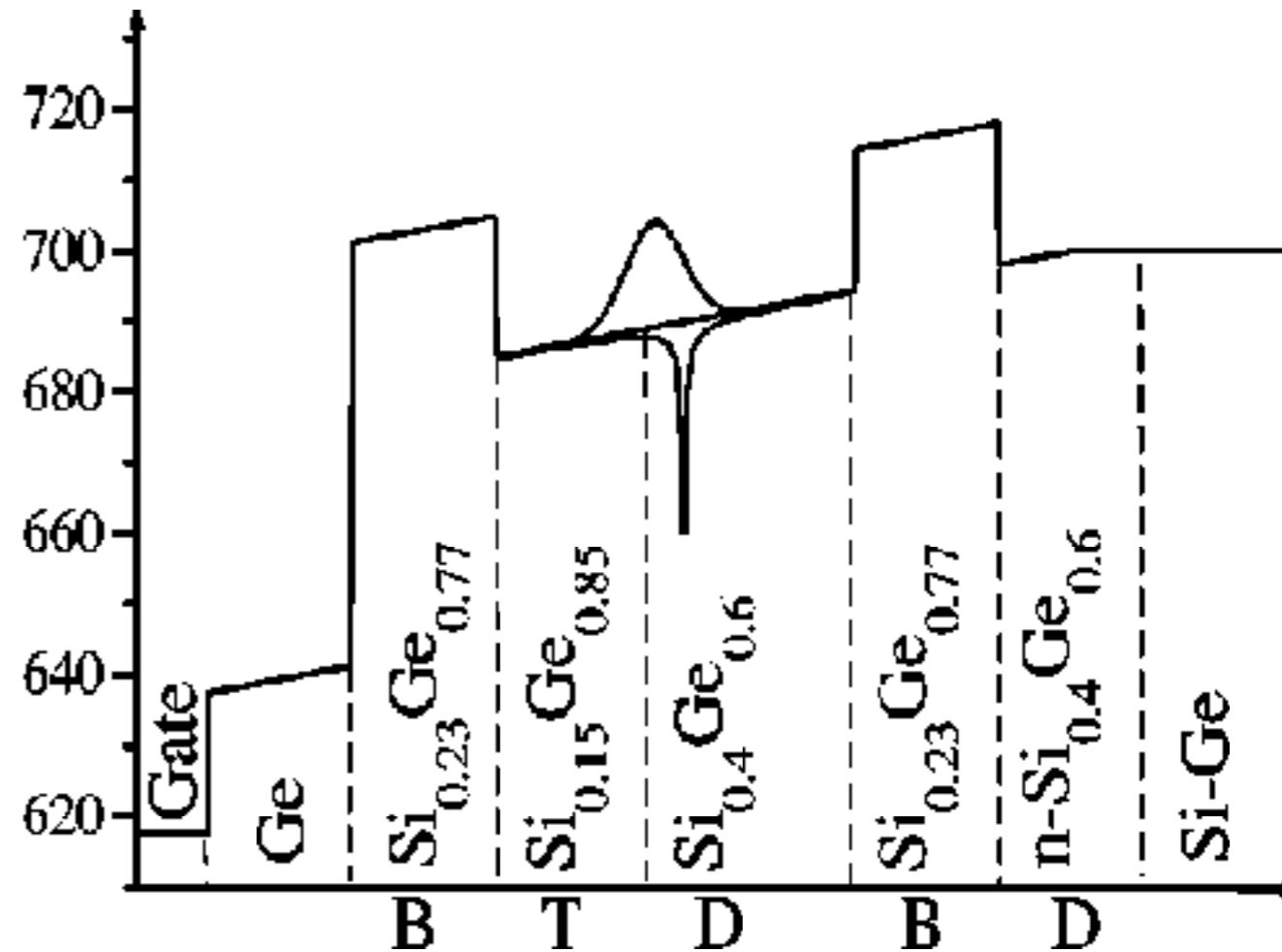


$$g_T = 0.82$$

$$g_D = 2.00$$

$$g_{av} = 2.00$$

biased gate



$$g_{av} \sim 1.5$$

➔ 1-qubit gates

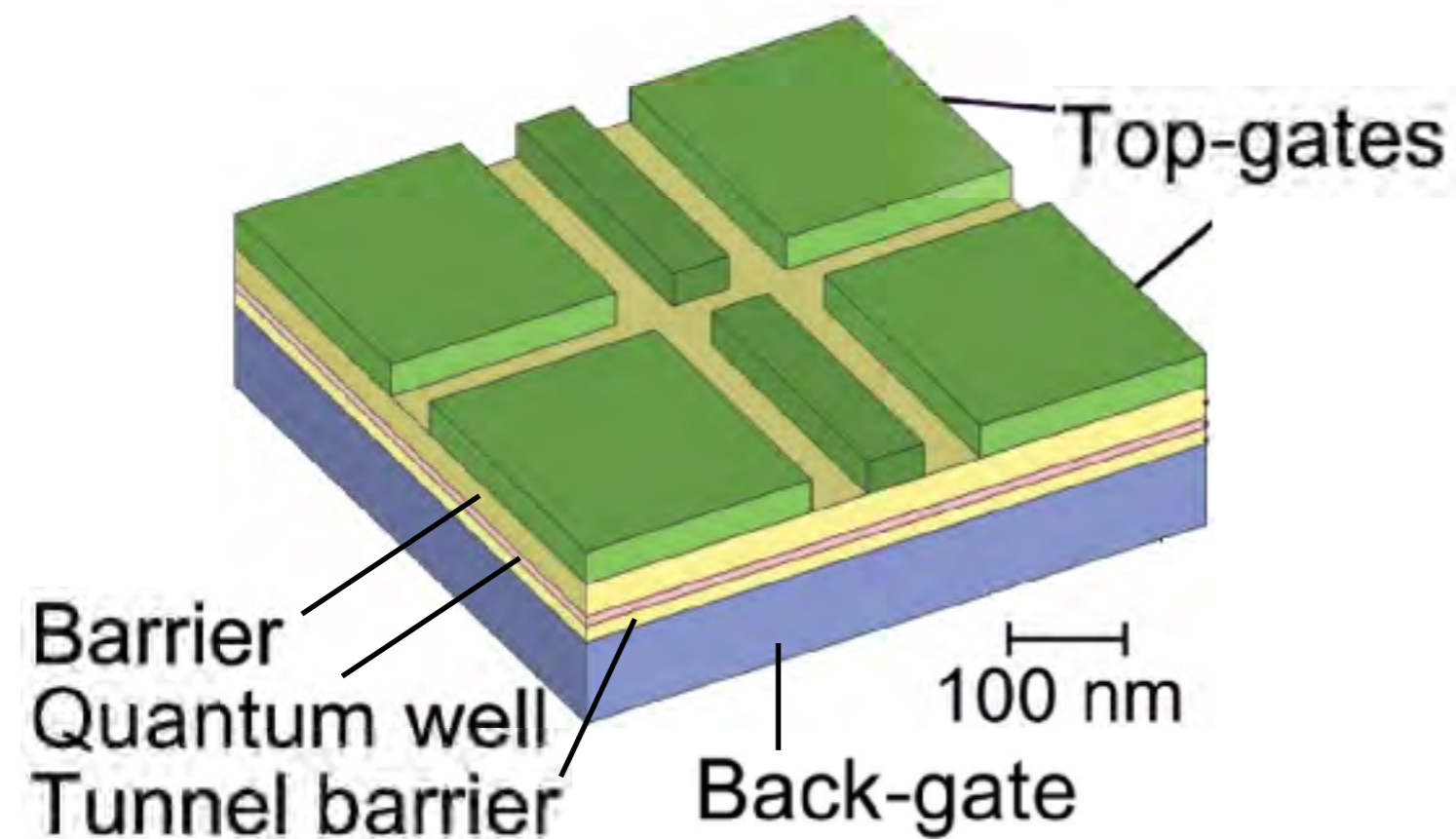
➔ also changes Bohr radius
can be used for 2-qubit gates

Quantum-Dot Qubits

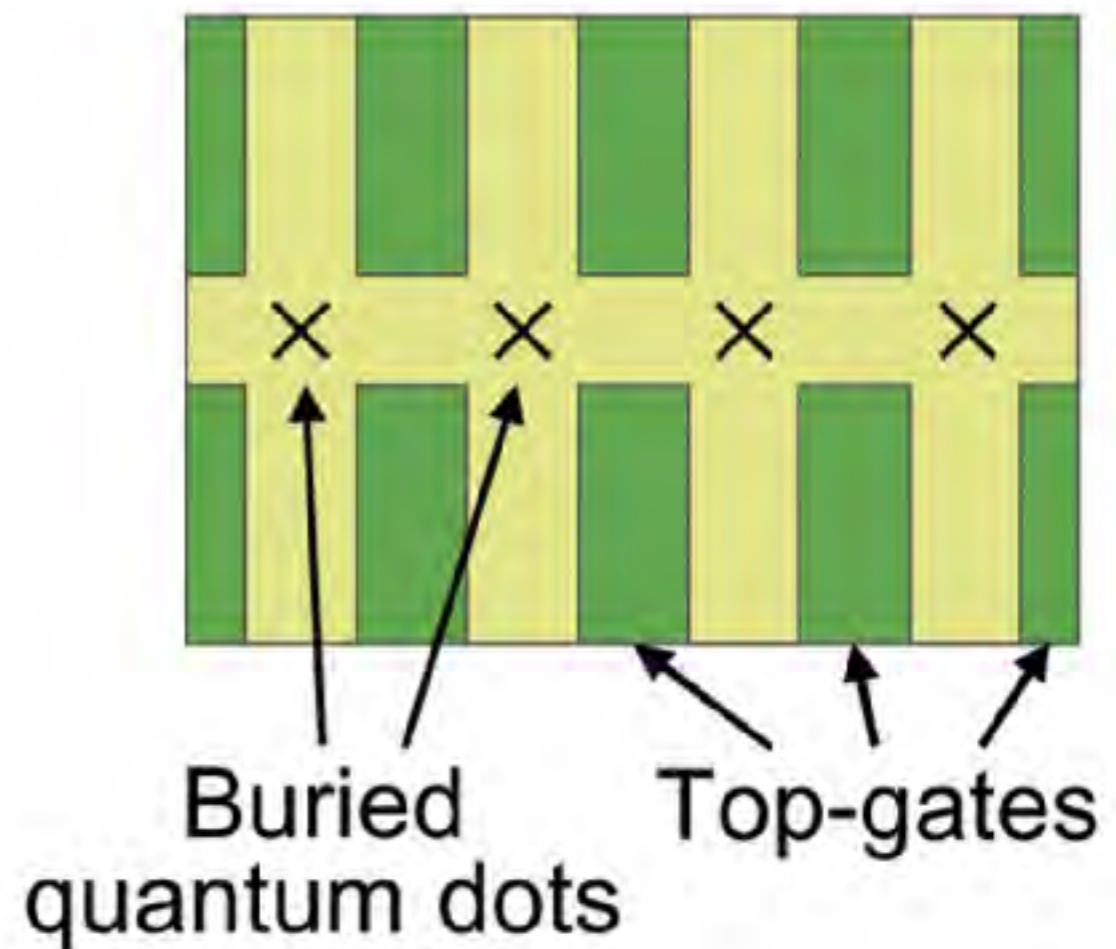
M. Friesen et al., PRB 67, 121301 (2003).

Electrostatically confined
quantum dots in Si - SiGe QW

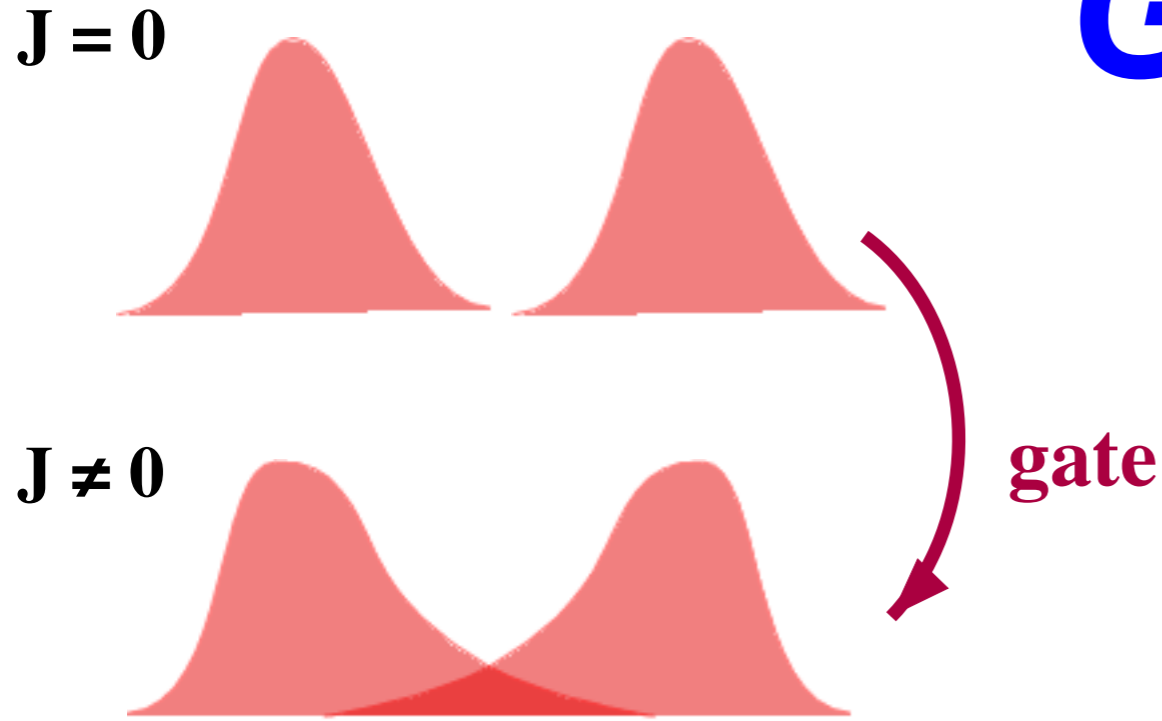
2 qubits



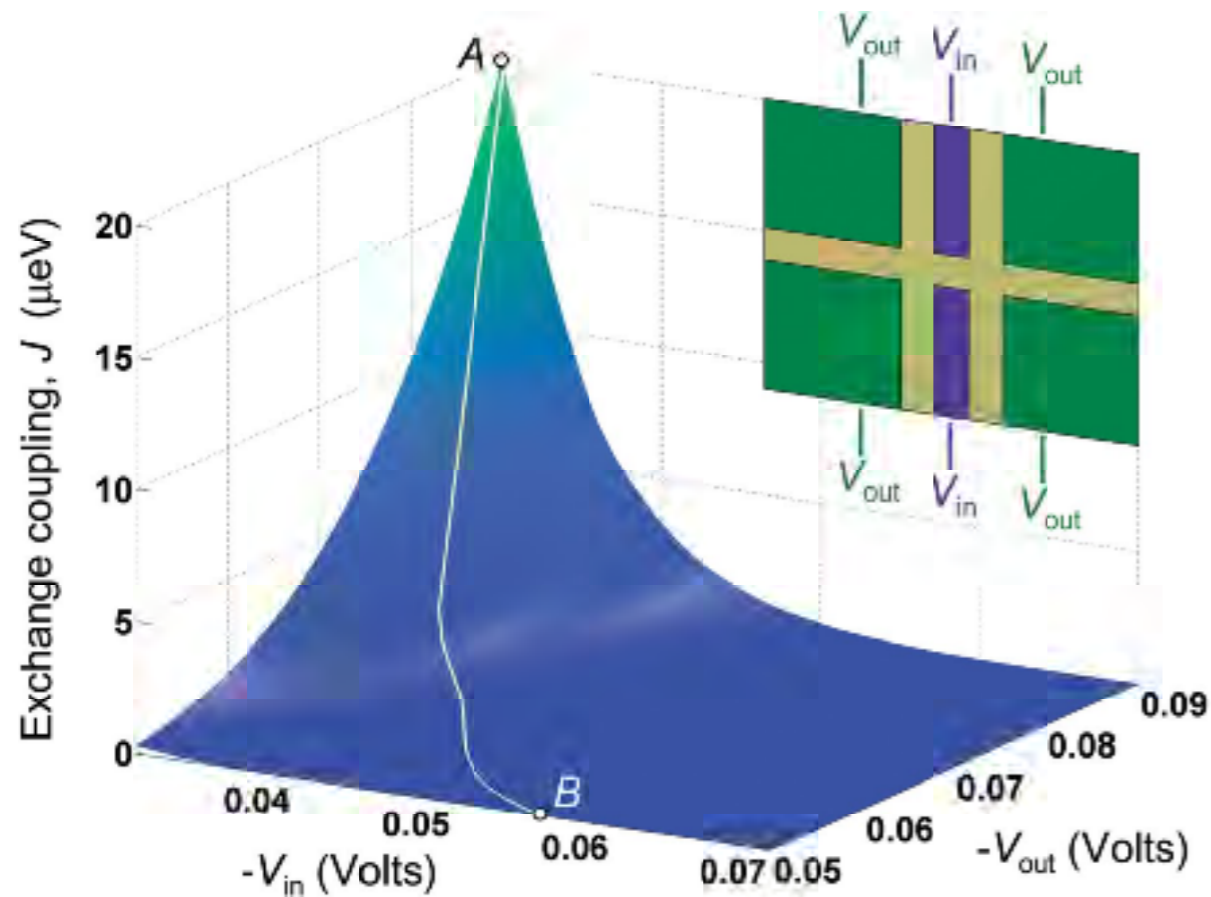
4 qubits



Gated Exchange



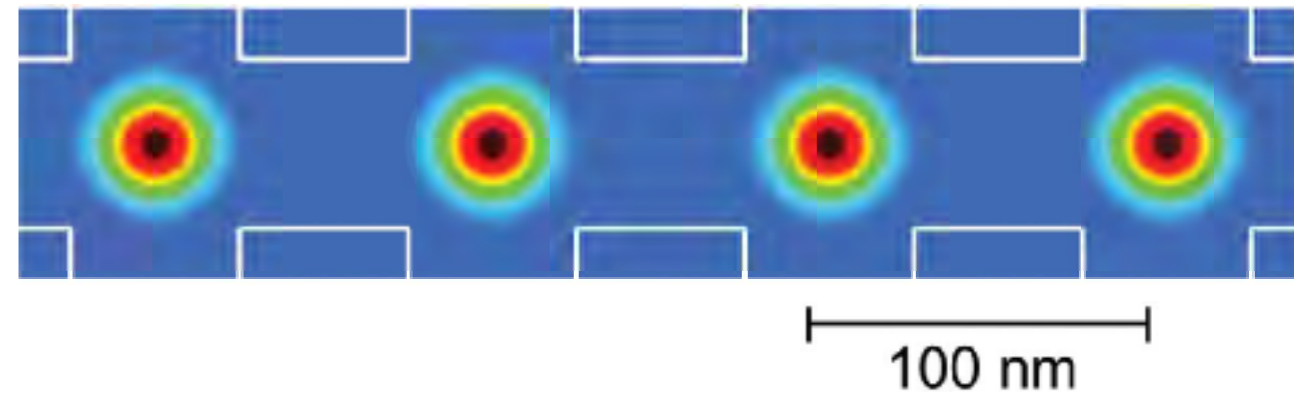
Tuning of exchange in 2-qubit system



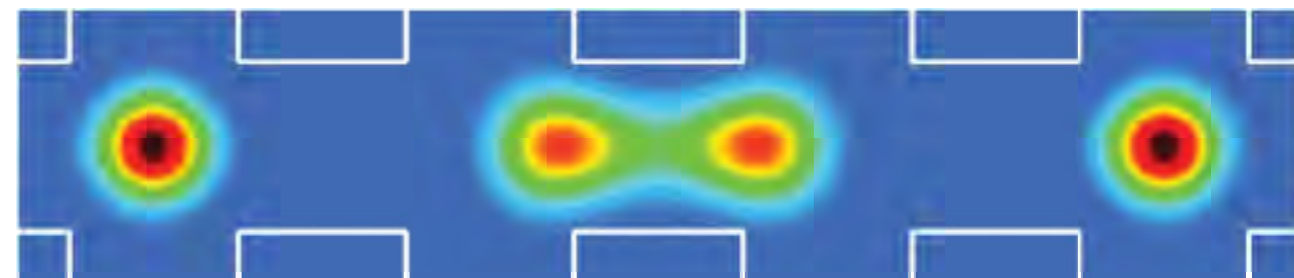
$$\mathcal{H}_J = J \vec{S}_1 \cdot \vec{S}_2$$

4-qubit system

$J = 0$

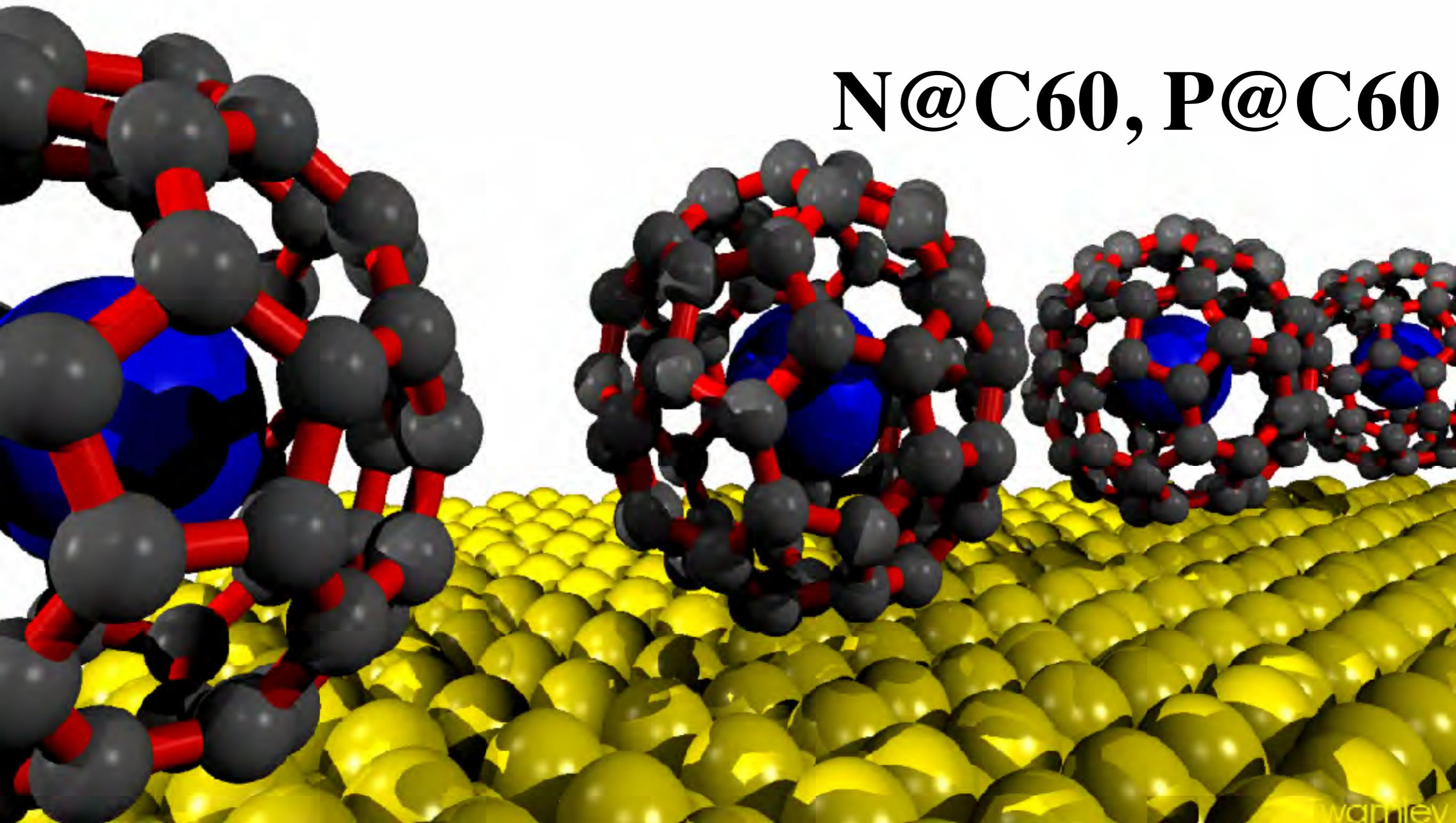


$J_{23} = 100 \text{ MHz}$



Endohedral Fullerenes

N@C60, P@C60

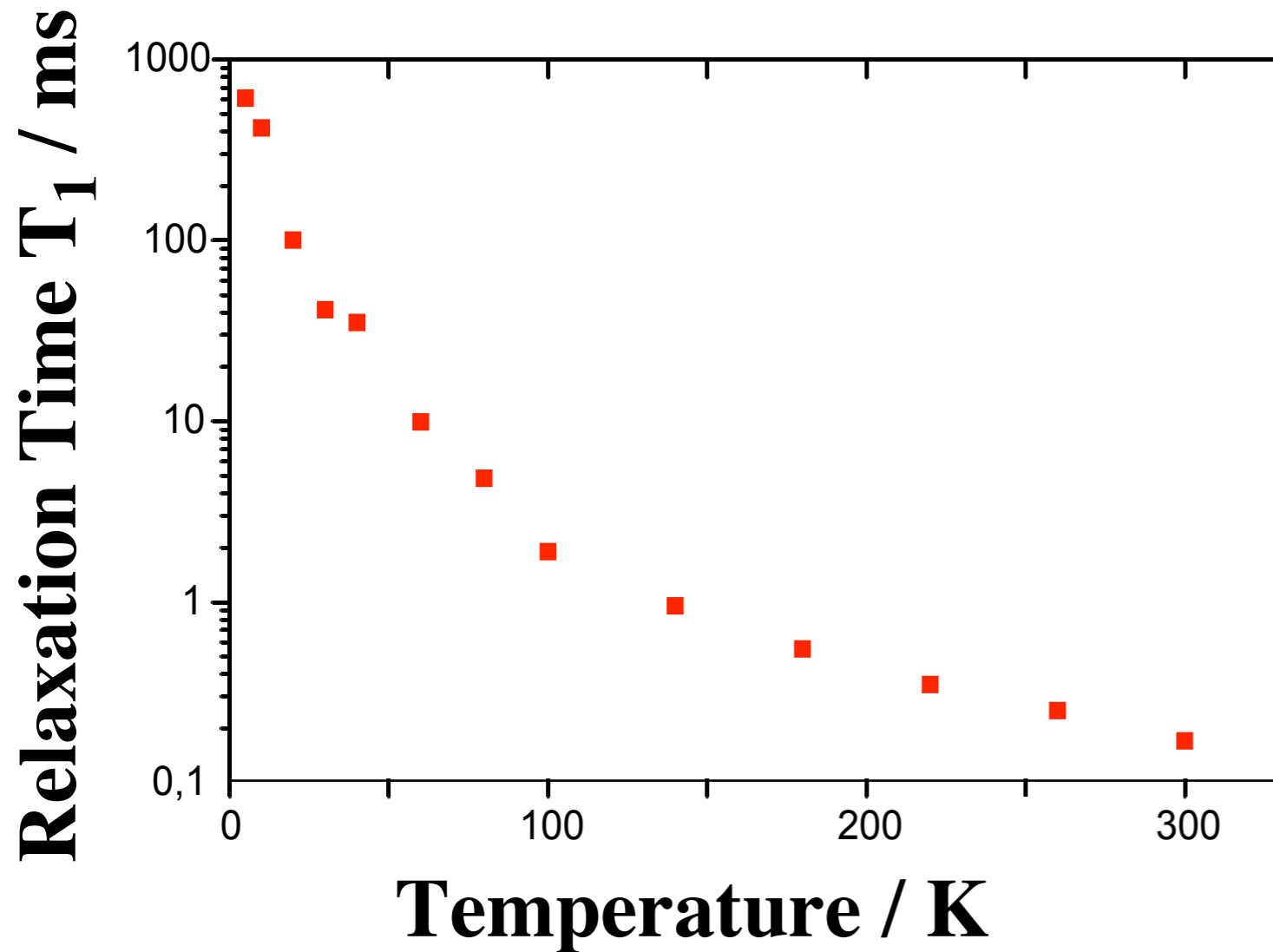


Why $N@C_{60}$?

Decoherence Time

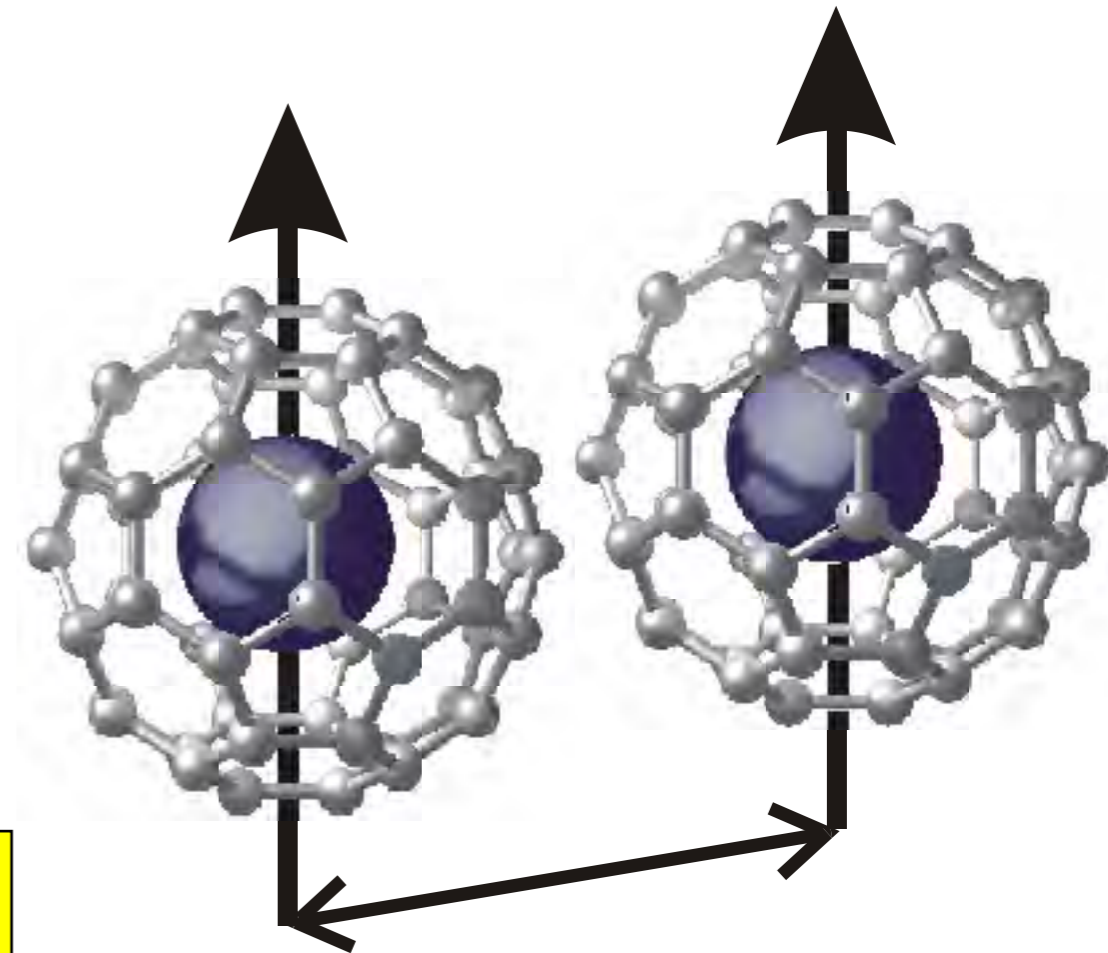
vs.

Switching Time



may be ~ 10 ns

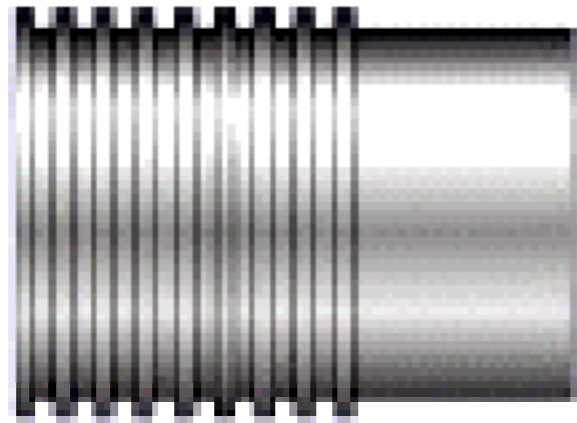
based on dipole-dipole
coupling @ 1 nm



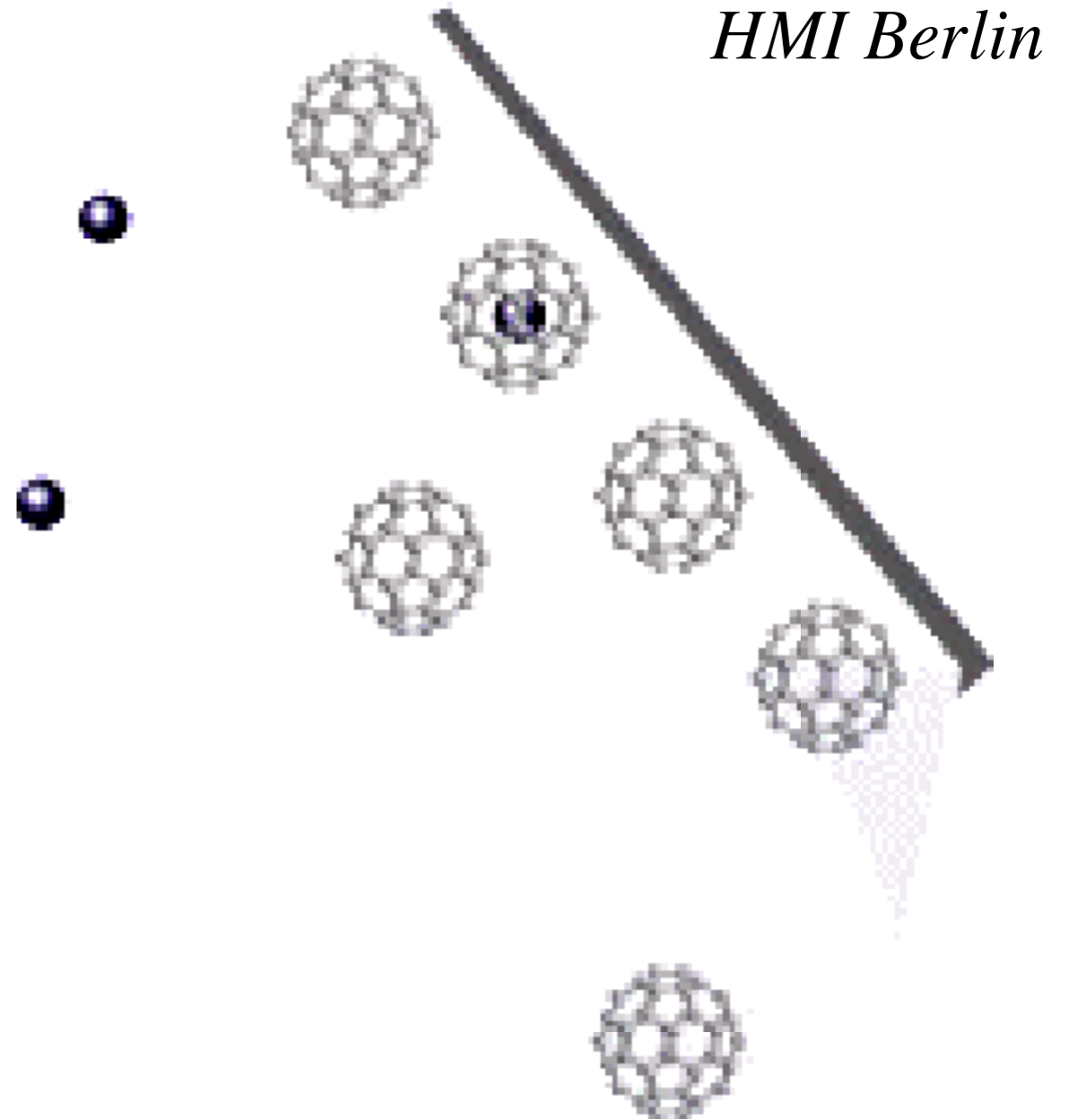
 # gates $\sim 10^8$

Production

Implantation into empty cages



ion source



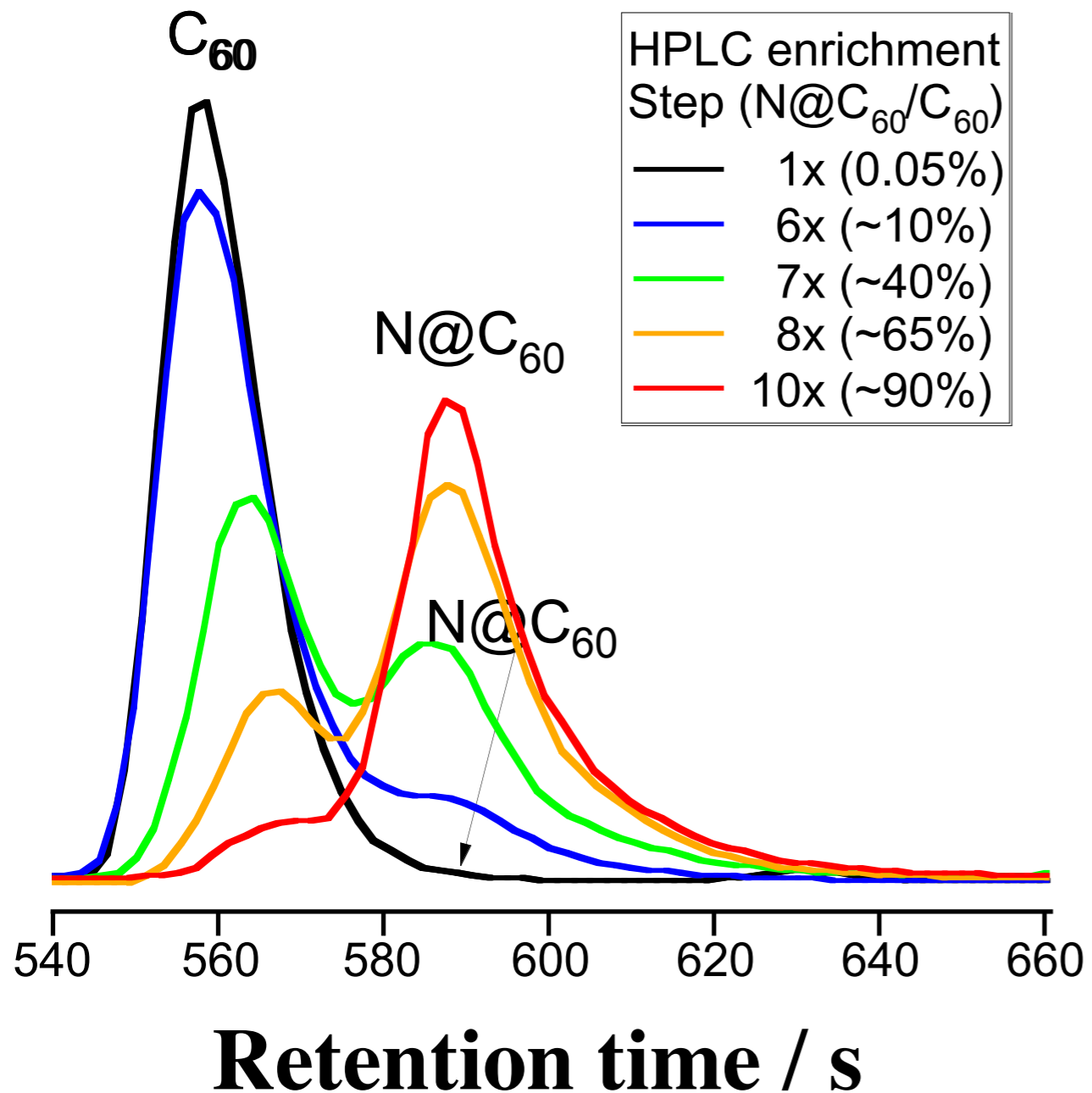
HMI Berlin

effusion cell

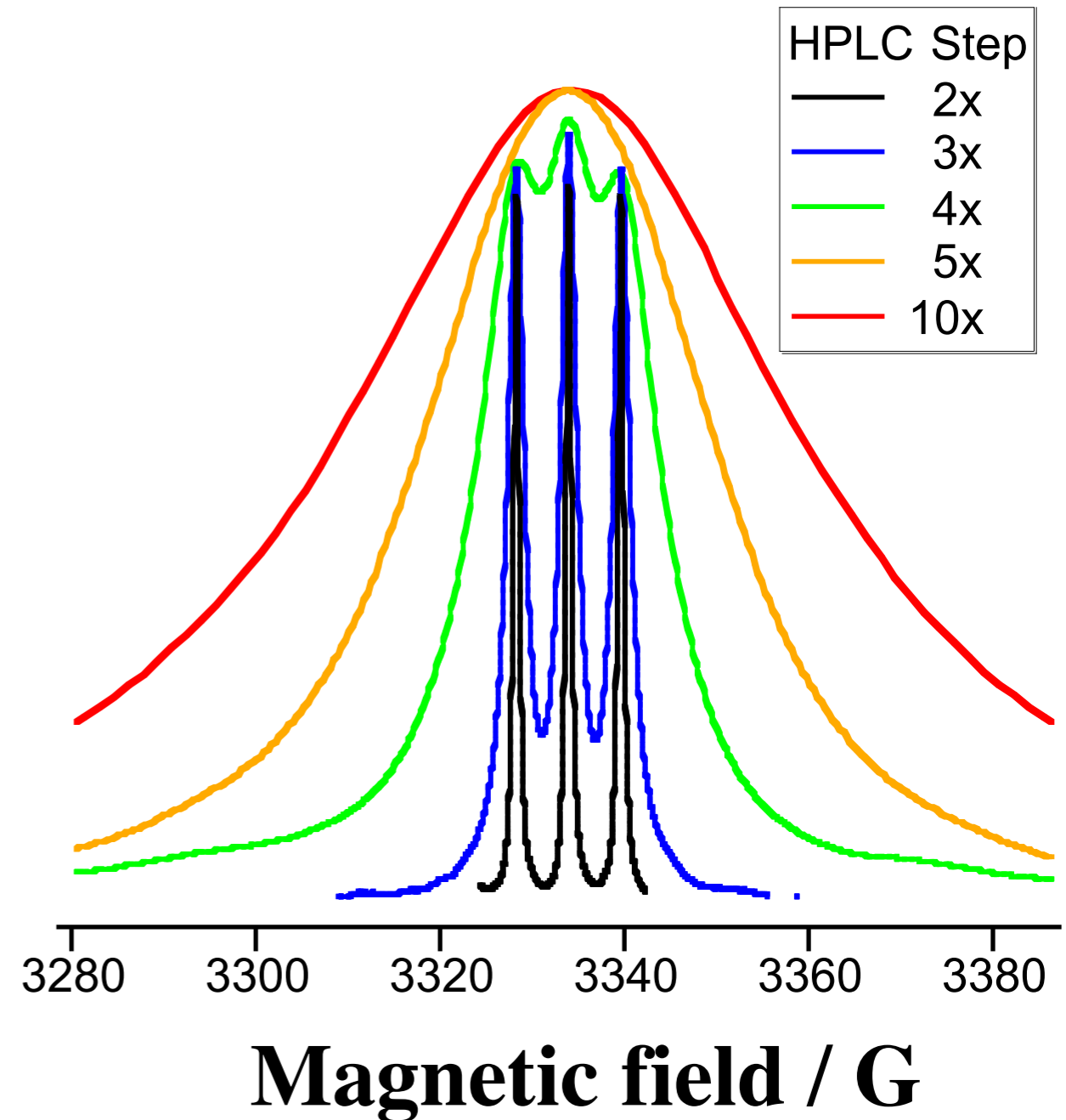


Purification by HPLC

HPLC Chromatograms



EPR Spectra



C₅₉N on Si

Nano-Positioning

University of Nottingham

before

after

3.8nm

4.6nm

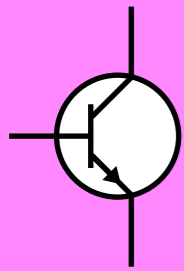
4.6nm

 Accuracy of positioning determined by surface lattice constant.

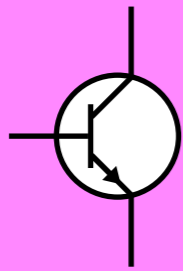
 Manipulation process does not induce additional defects on underlying surface

Addressing Qubits

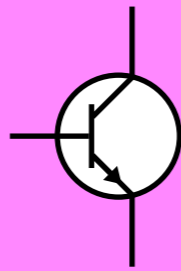
Solid-State Computer



bit 1



bit 2



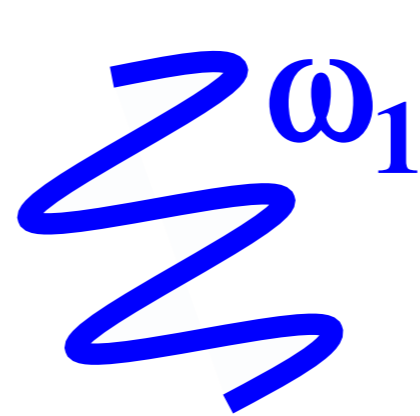
bit 3

separate leads



space

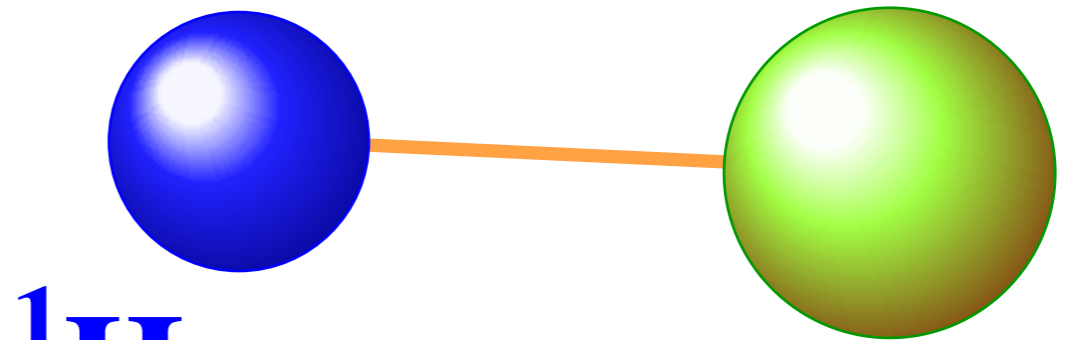
NMR in Liquids



ω_1



ω_2



^1H

qbit 1

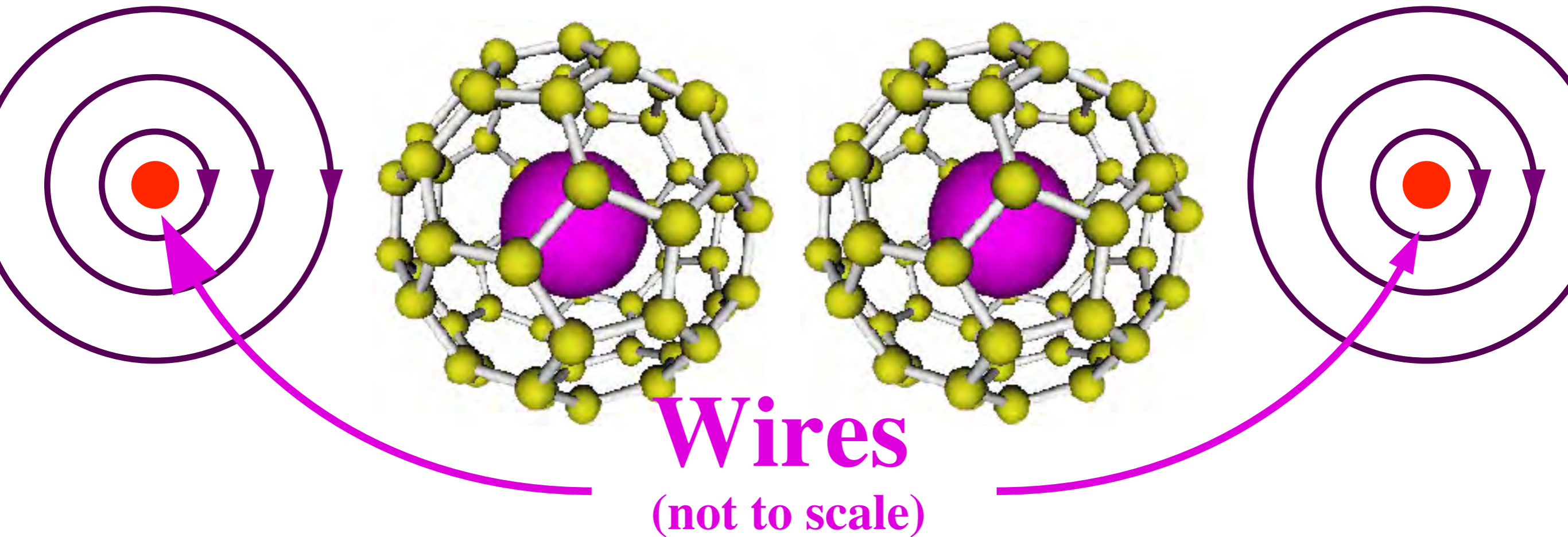
^{13}C

qbit 2

monochromatic radiation
affects only one type of spins

Addressing N@C60

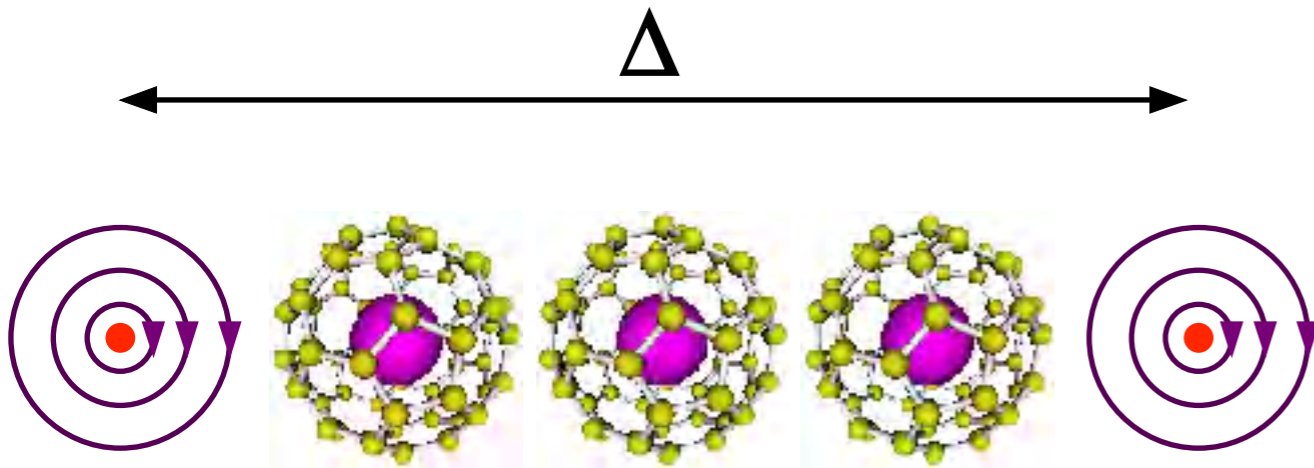
Phys. Rev. A **65**, 052309 (2002).



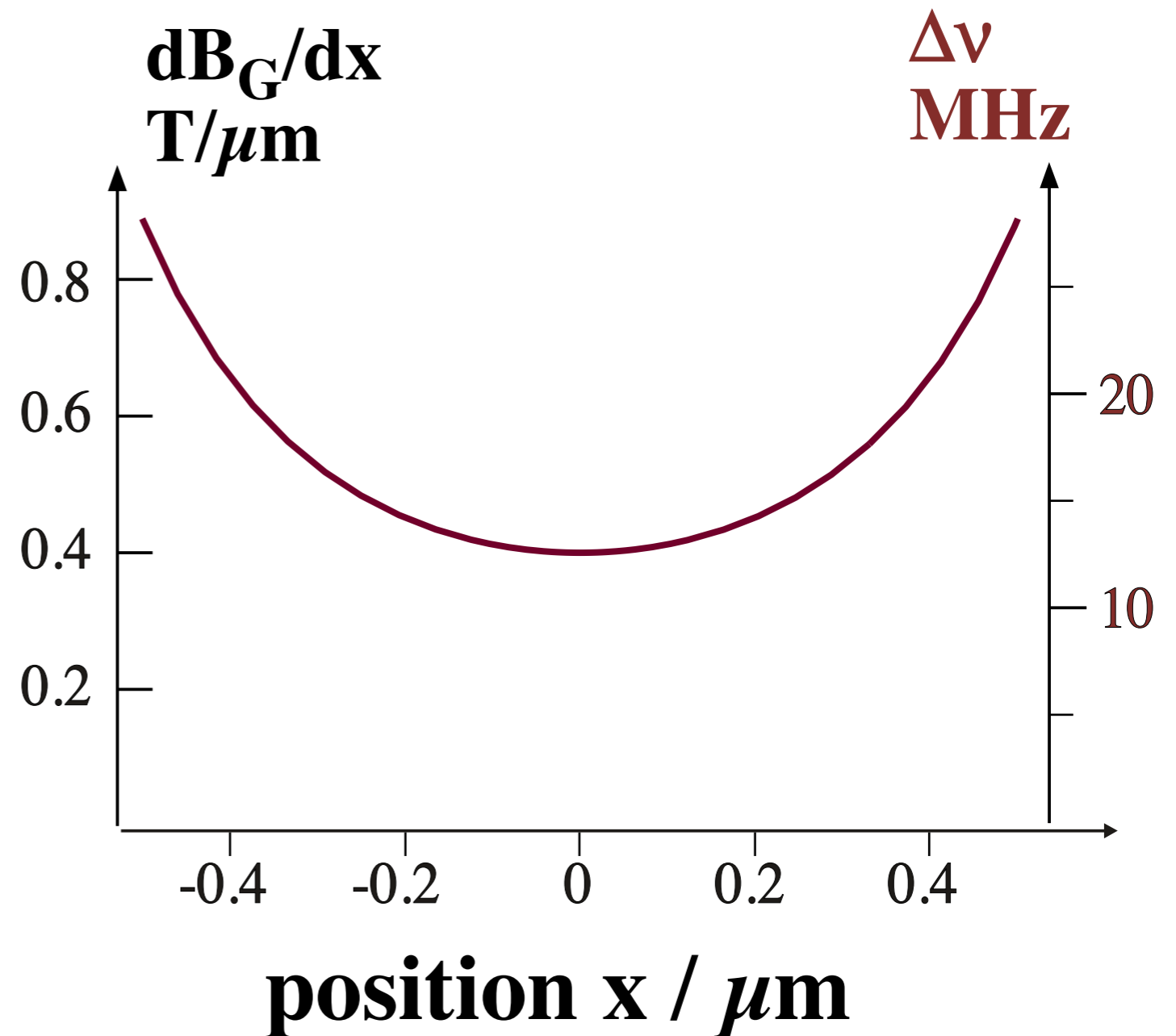
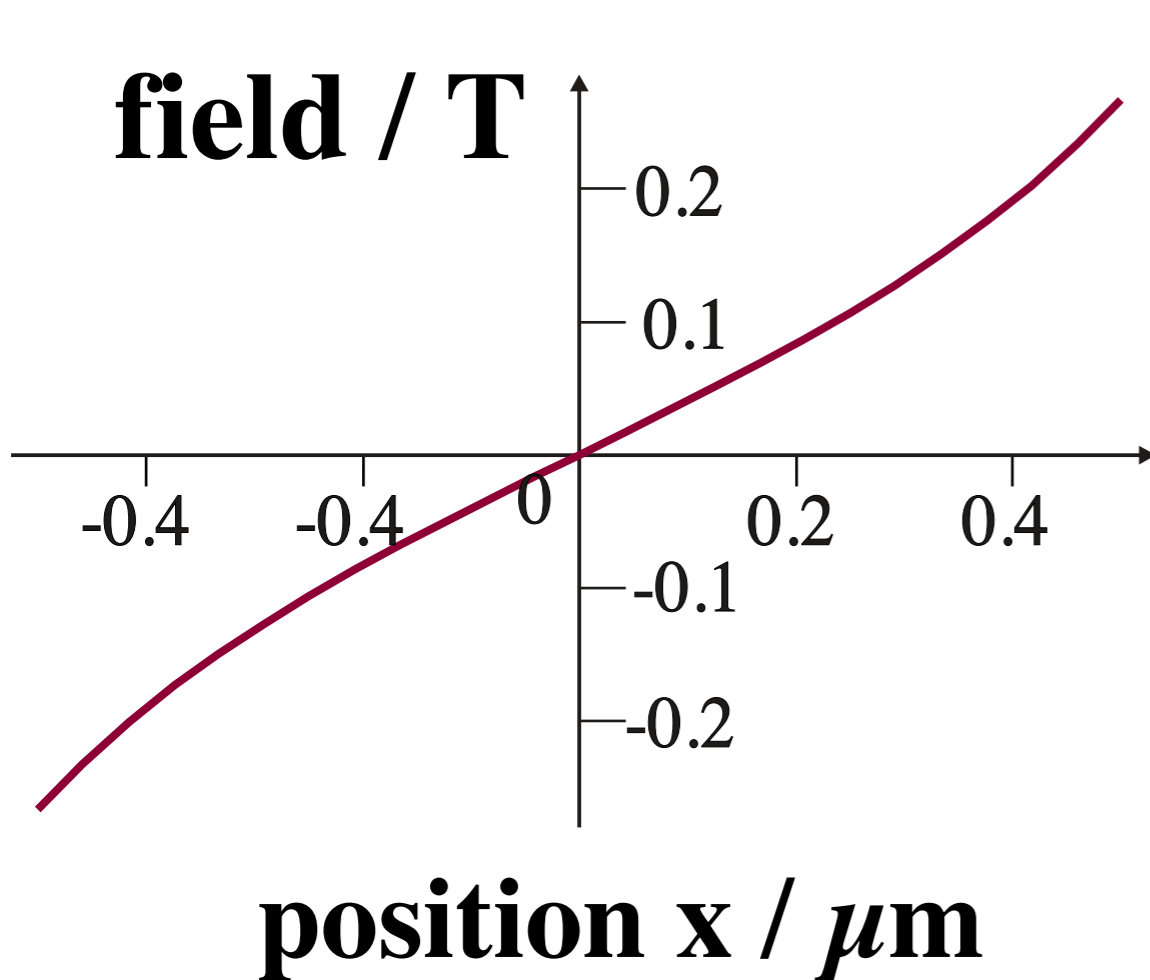
**Current pulses through μm -scale wires
could shift frequencies by multi-MHz**

Magnetic Field

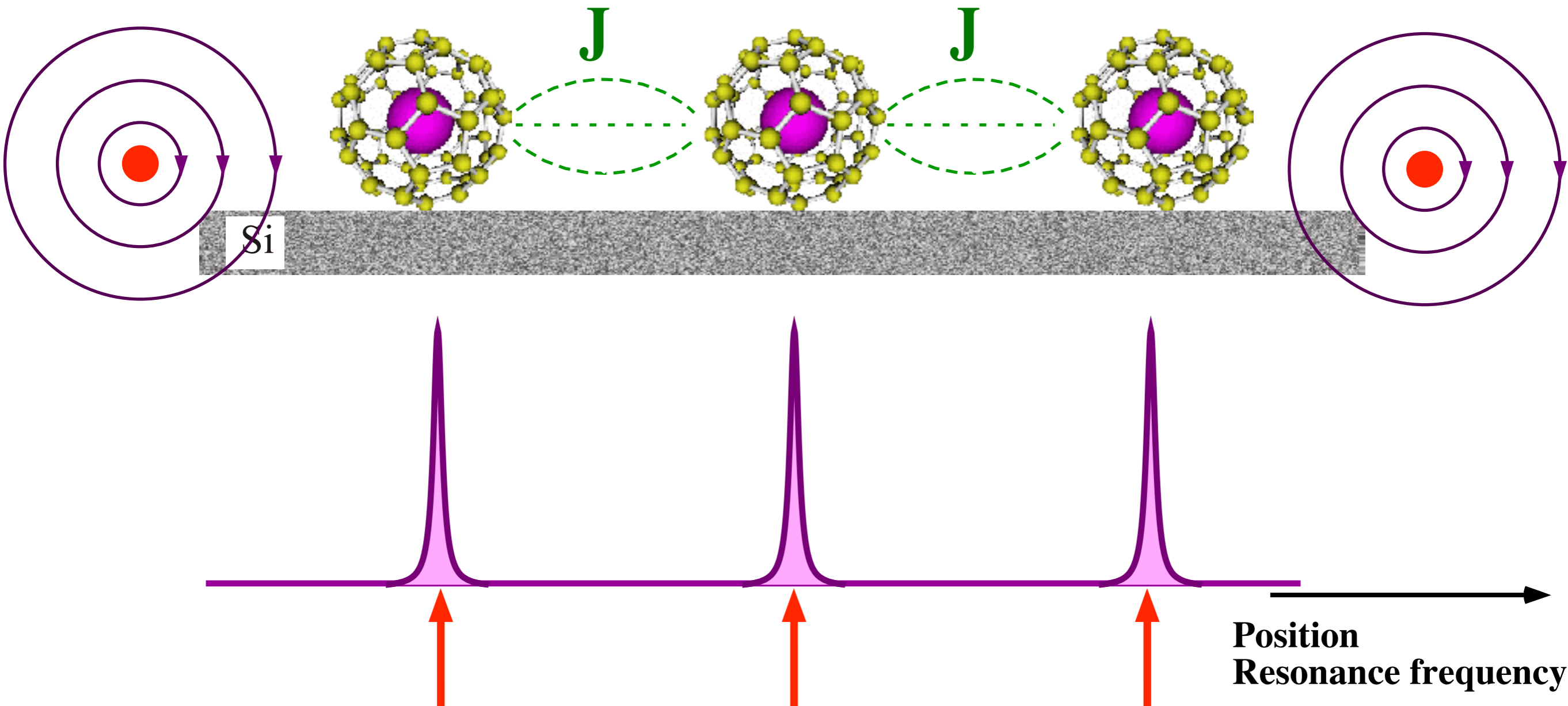
for $I = 1\text{A}$, $\Delta = 1\ \mu\text{m}$



Nearest neighbour
frequency difference



Frequency Selection



Implement 1-qubit gates by frequency- or field switching

What about 2-qubit gates?

2-Qubit Gates

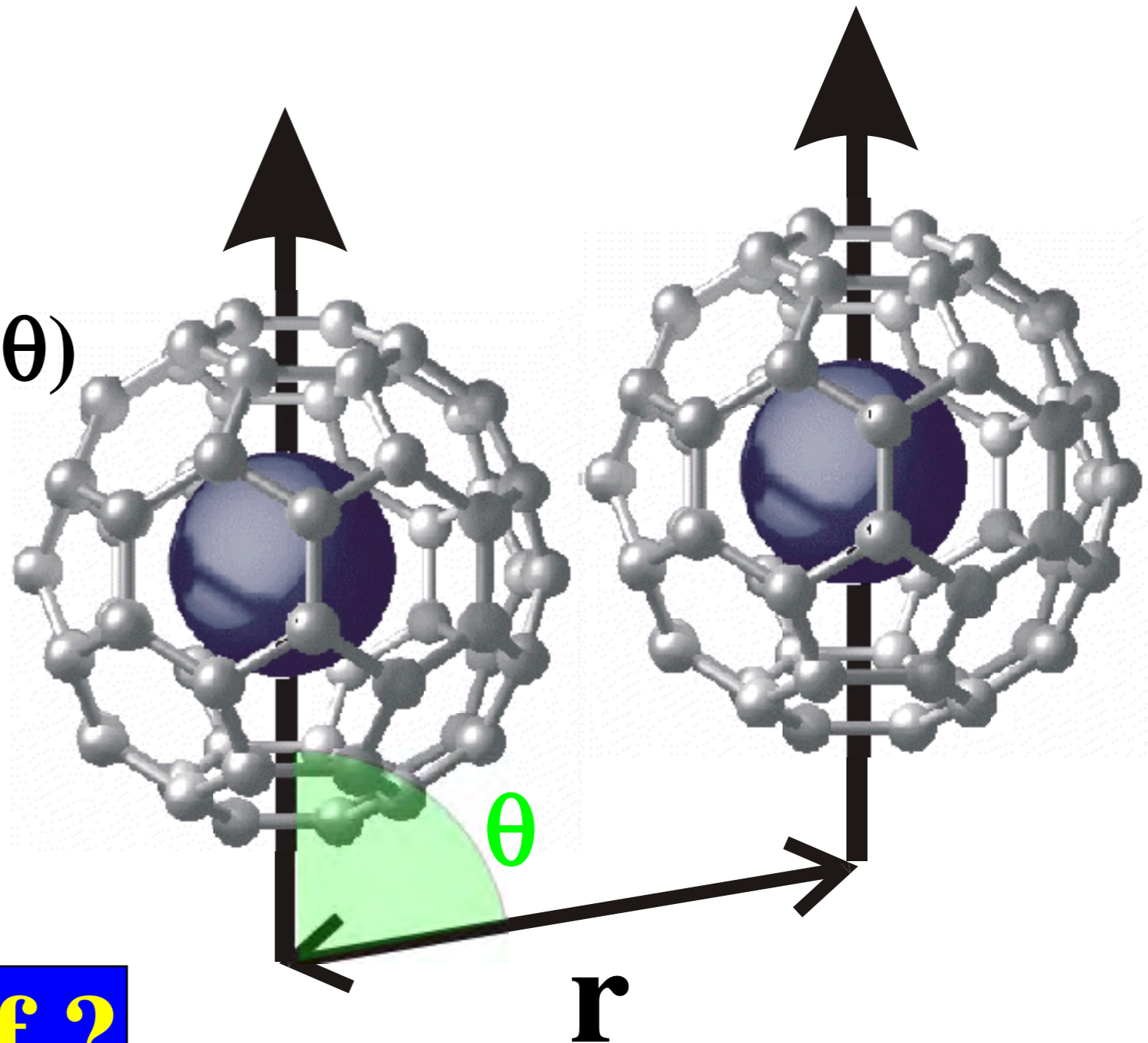
Required: Interaction

Dipole-dipole coupling

$$E_{\text{dd}} = \frac{\mu_0}{4\pi} \frac{\gamma_1 \gamma_2}{r^3} (1 - 3\cos^2\theta)$$

N@C₆₀, 1.1 nm distance

$$\frac{E_{\text{dd}}}{h} \sim 50 \text{ MHz}$$



Switch on / off ?

Switchable Coupling

activate:
SWAP QuInfo

electron spin

$|i\rangle$



$|i+1\rangle$

coupling on

hyperfine
coupling

^{15}N : 22 MHz
SWAP
 ^{31}P : 138 MHz

nuclear spin:
 ^{15}N , ^{31}P

$|i\rangle$

$|i+1\rangle$

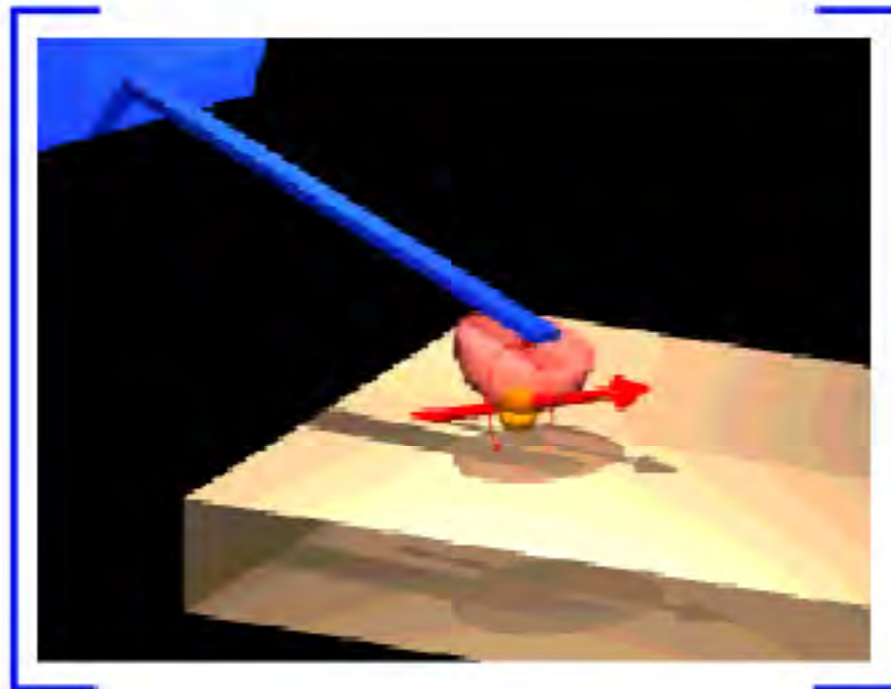
coupling off

$$\frac{E_{dd}(\text{nuclei})}{E_{dd}(\text{electrons})} \sim 10^{-8}$$

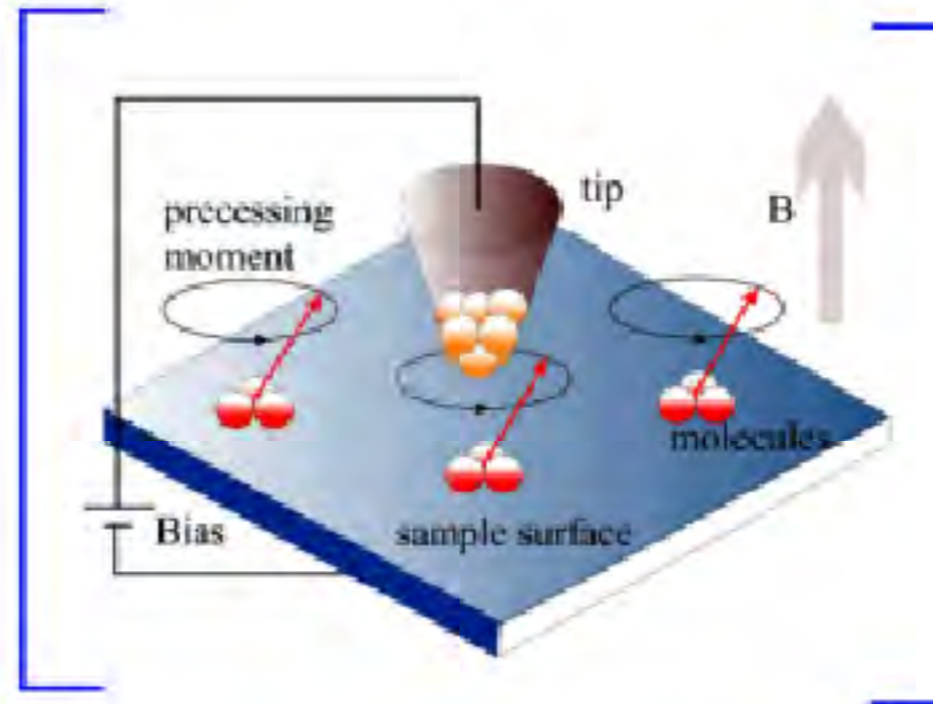
+ (Nuclei) : long decoherence times
no coupling

+ (Electrons) : fast gates
strong coupling

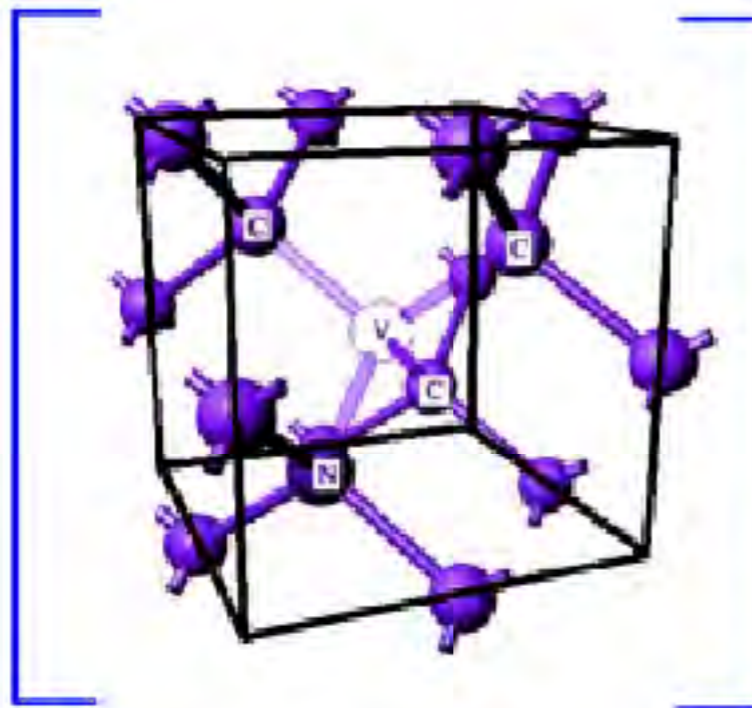
Single-Spin Readout



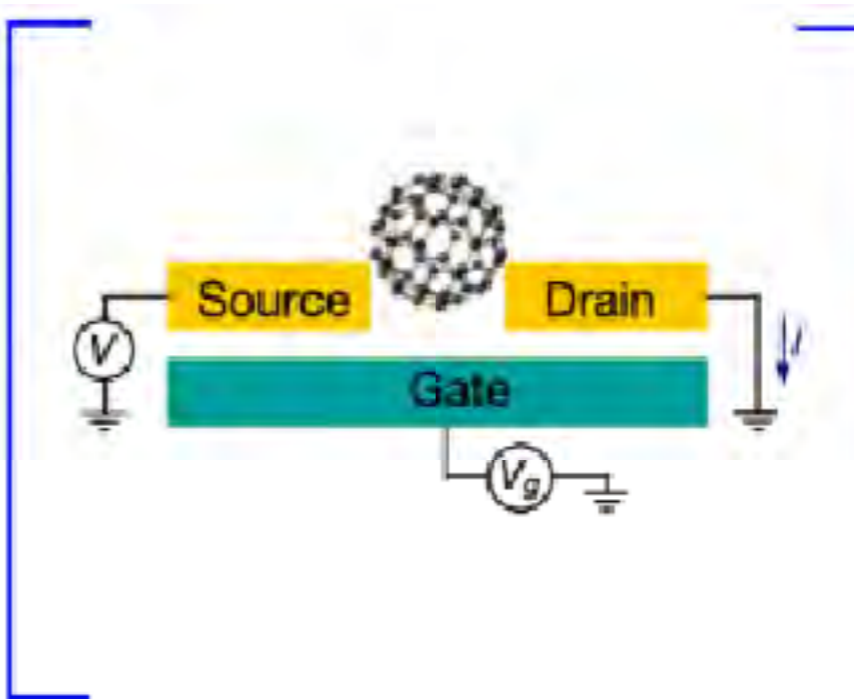
- Magnetic Resonance Force Microscope



- Scanning Tunneling Microscope Electron Spin Resonance

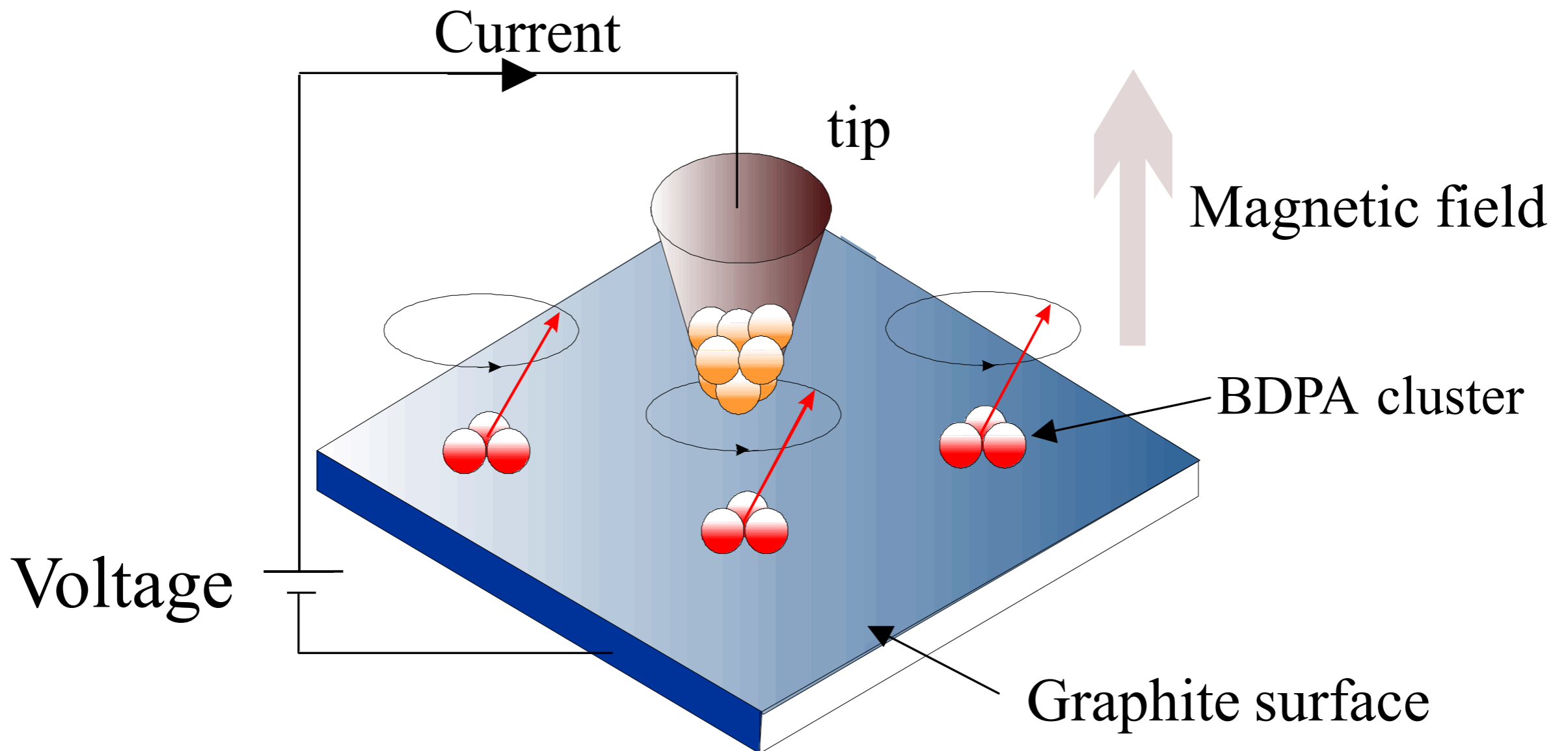


- Optical Detection via Diamond N/V center



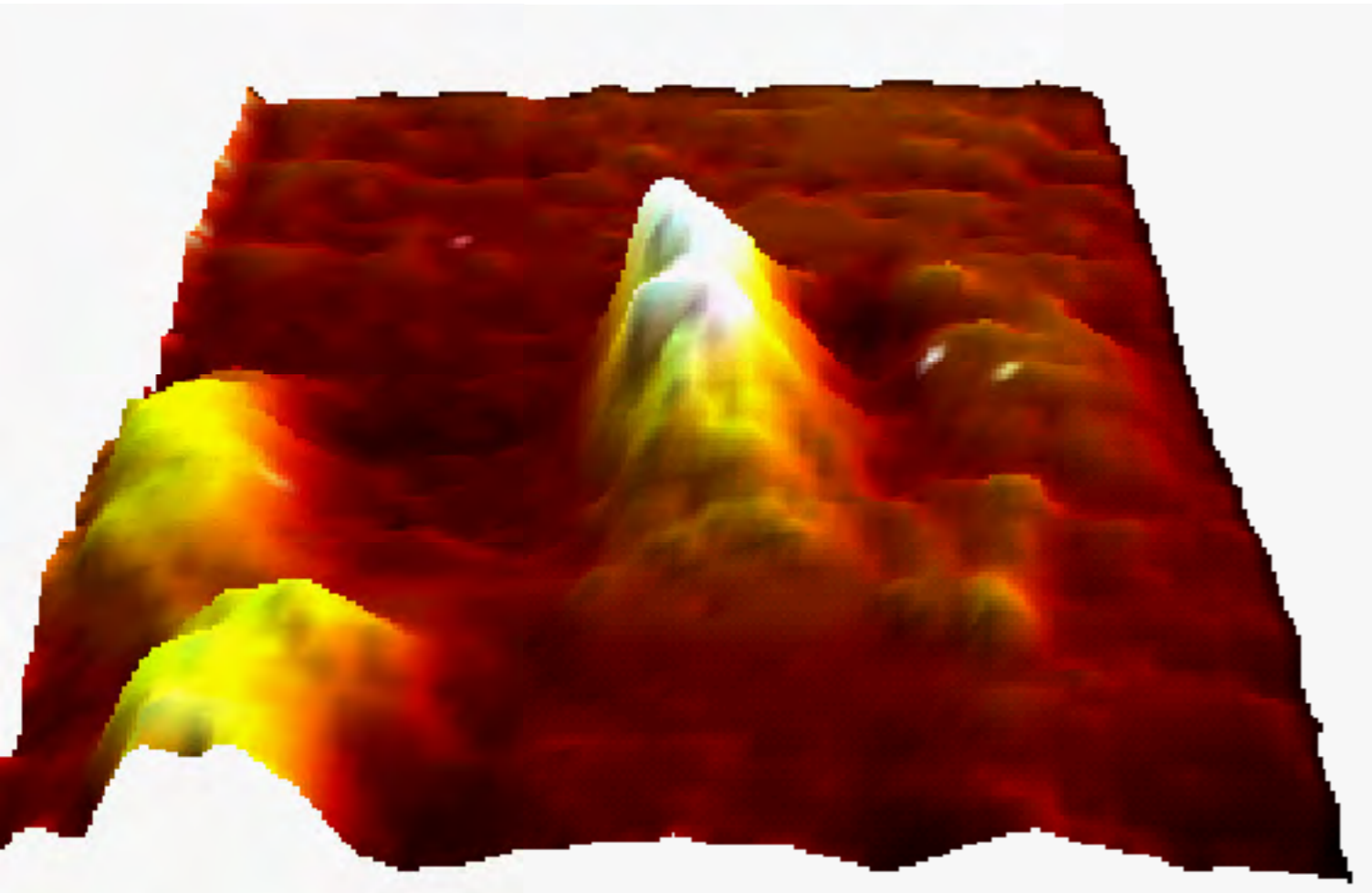
- Single Molecule Transistor

Detect modulation of tunnel current at Larmor frequency



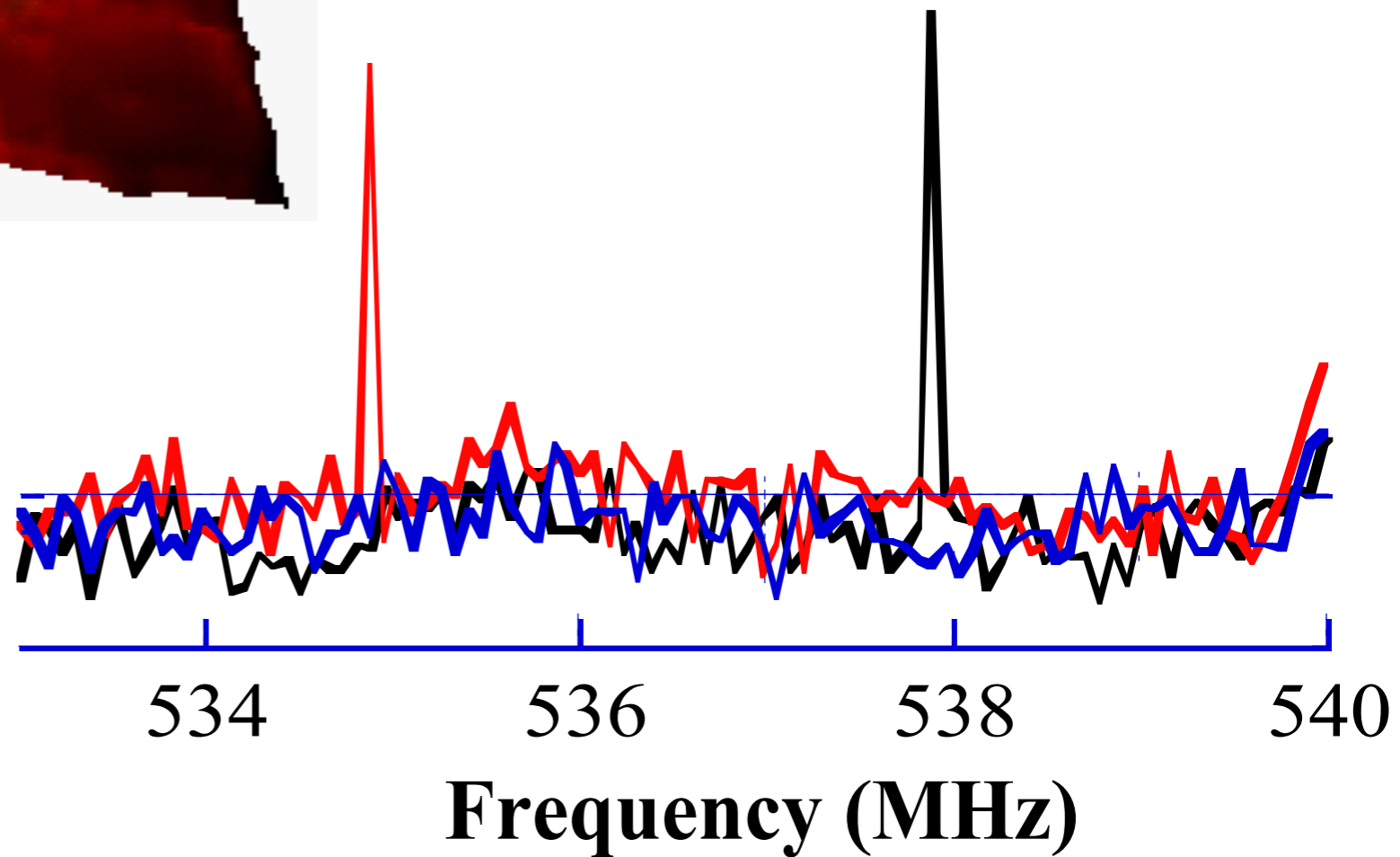
First demonstration: Manassen et al., PRL 62, 2531 (1989).

STM EPR



10 nm

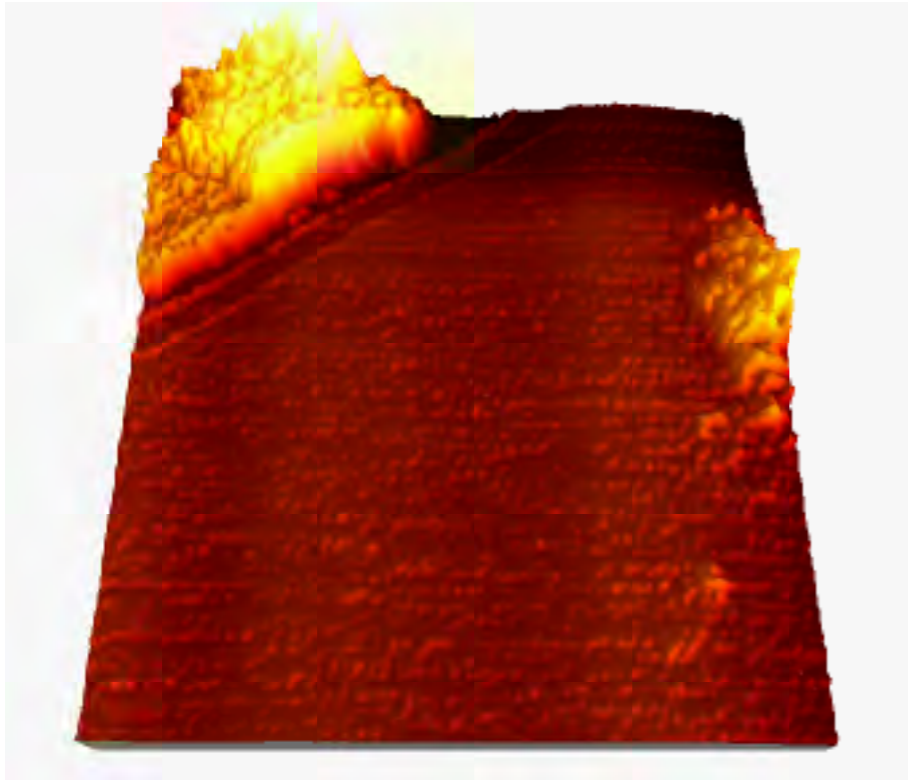
STM-ESR spectra of BDPA on HOPG (red and black) and bare HOPG (blue).



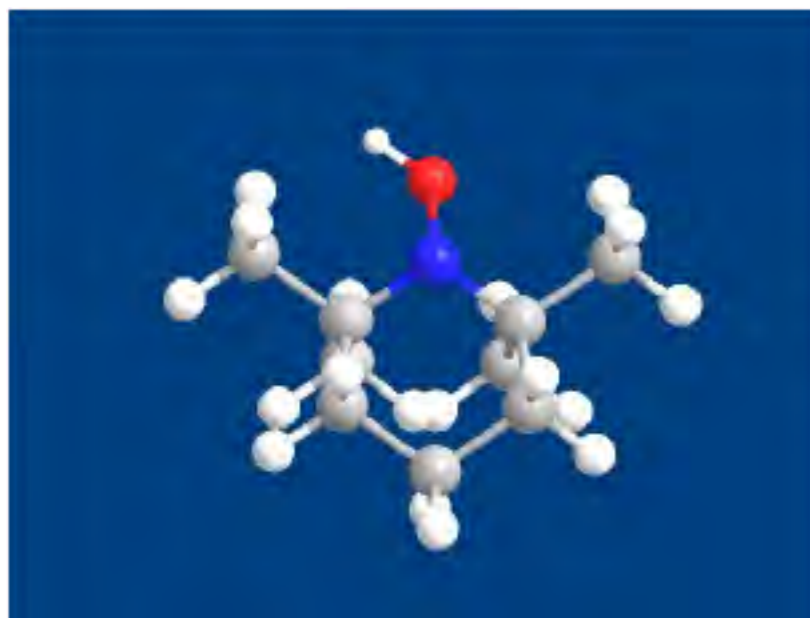
C. Durkan and M. E. Welland, Electronic spin detection in molecules using scanning-tunneling microscopy-assisted electron-spin resonance. *Appl. Phys. Lett.*, 80, 458 (2002).

STM EPR of TEMPO

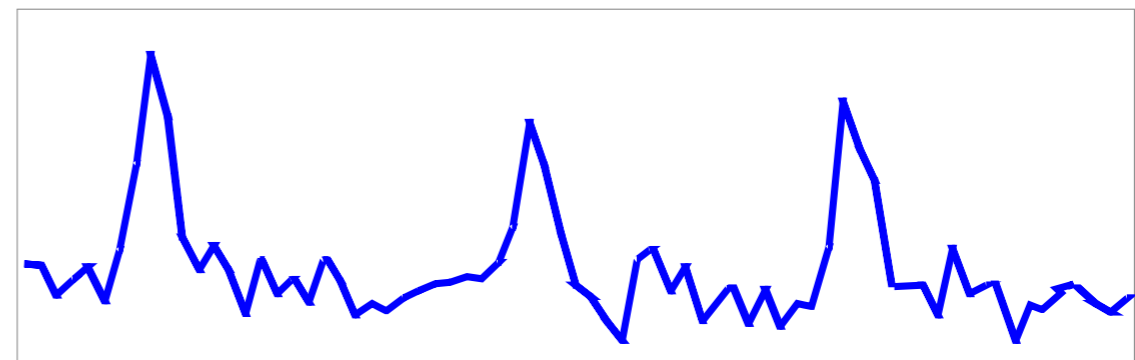
TEMPO on graphite : $S=1/2$, $I=1$: hyperfine splitting



200 nm x 200 nm area



TEMPO

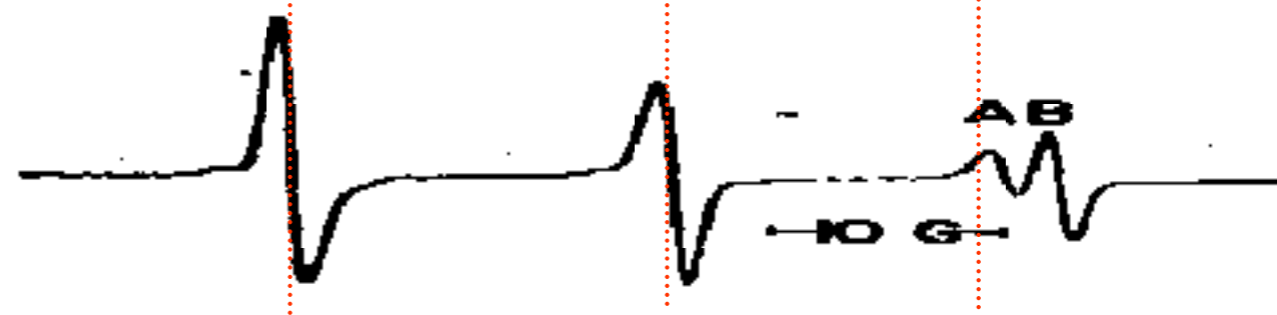


485

525

575

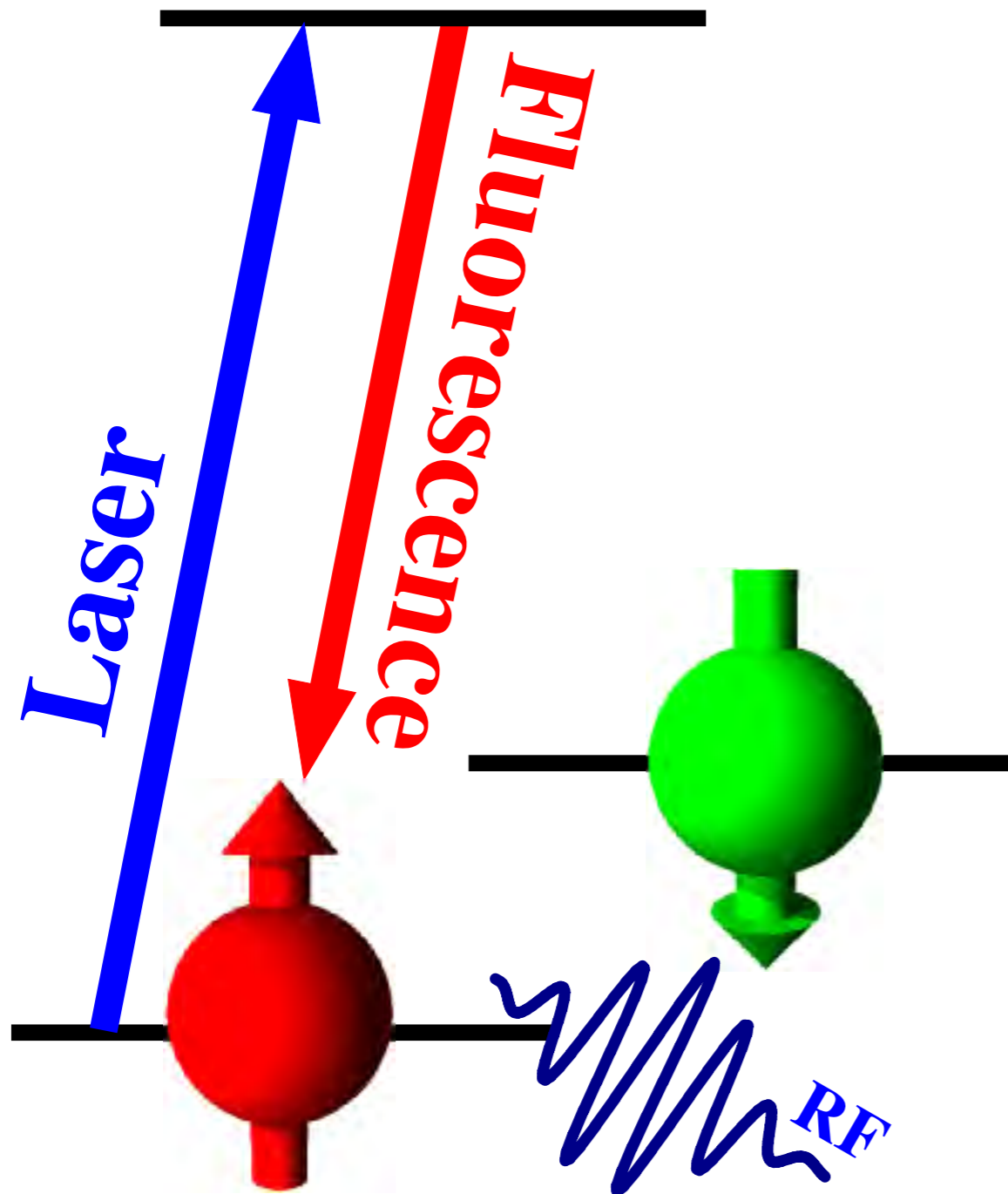
Frequency / MHz



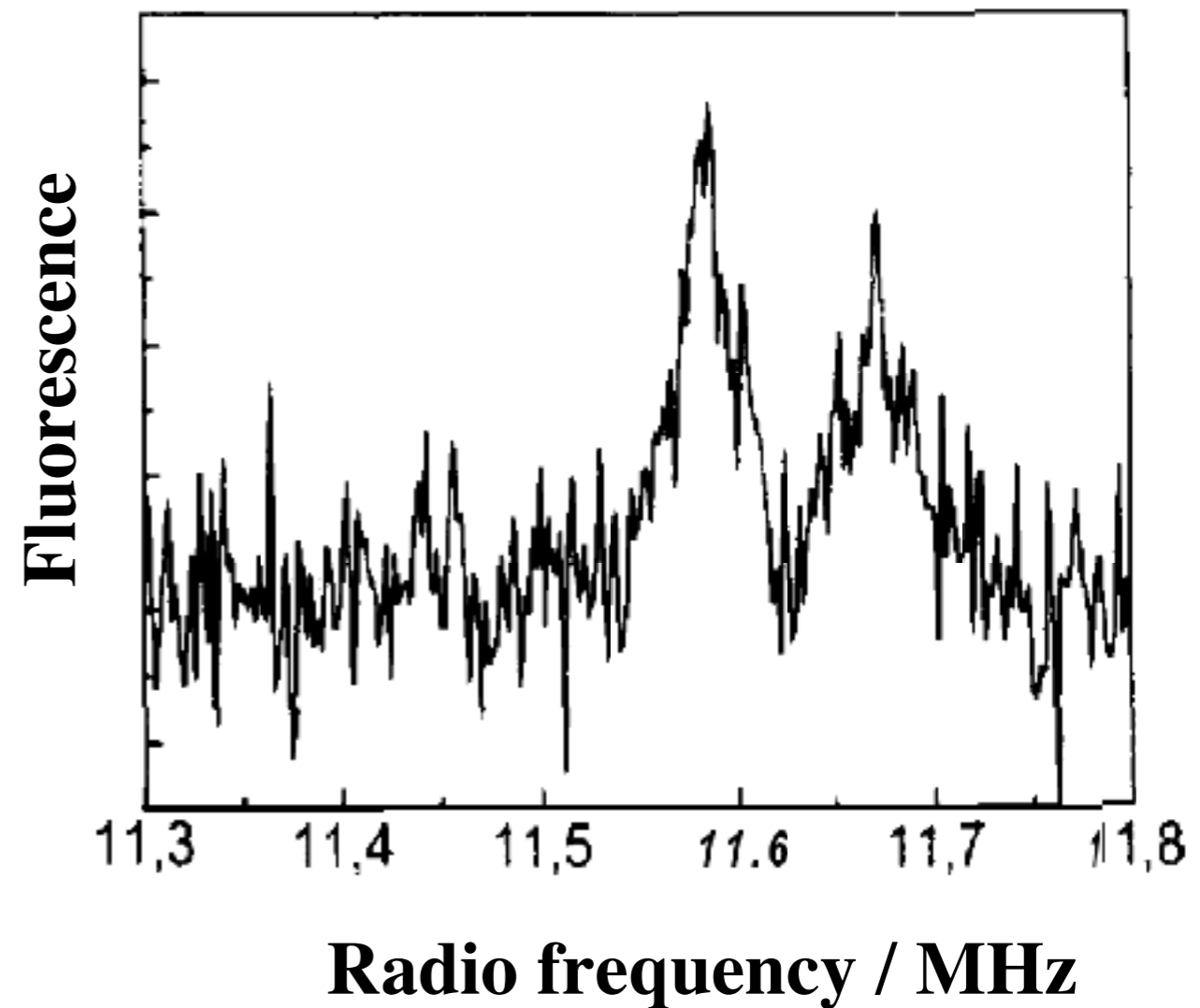
Conventional EPR

Single-Spin Detection

by optically detected magnetic resonance



single ^1H in pentacene

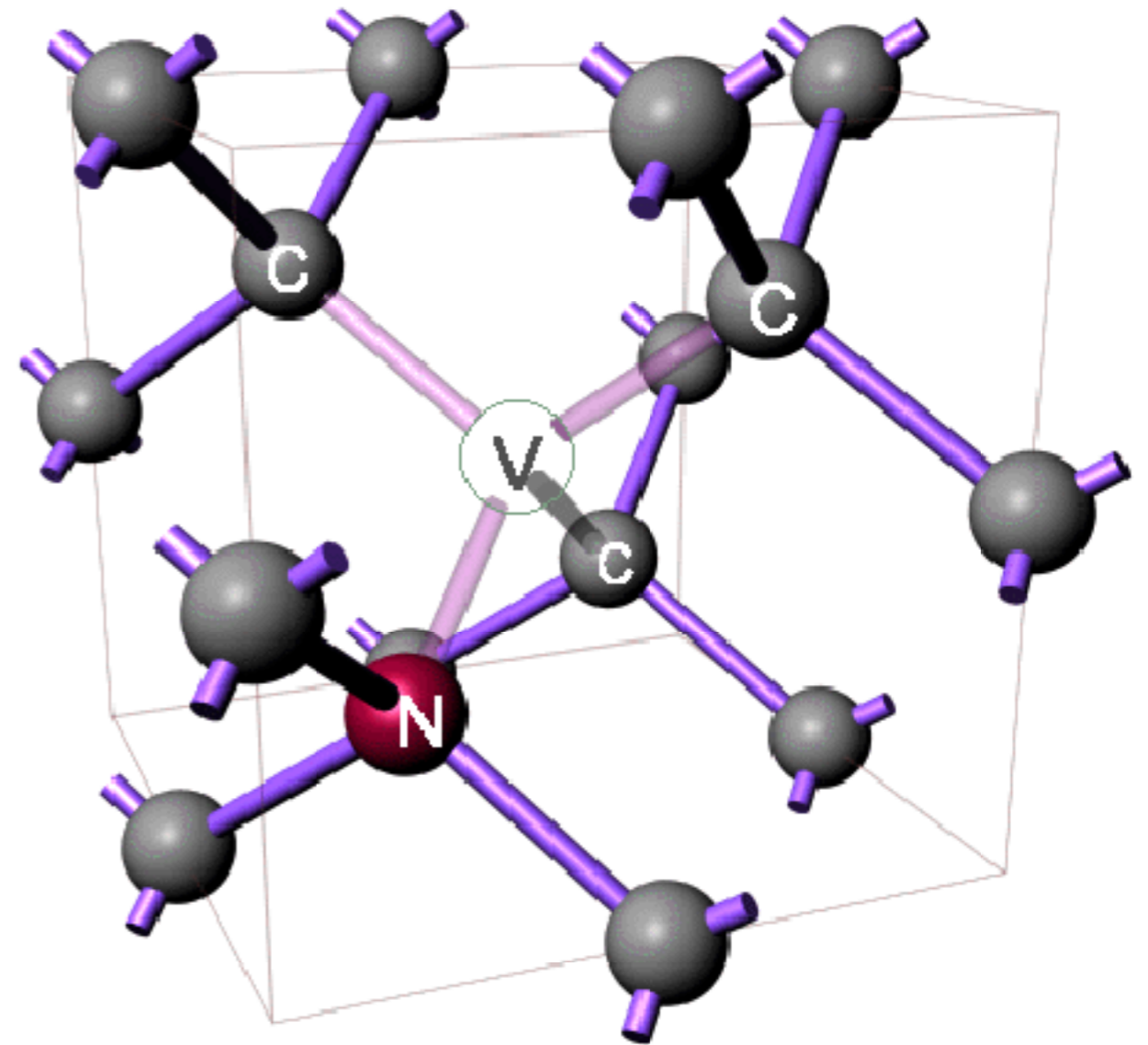
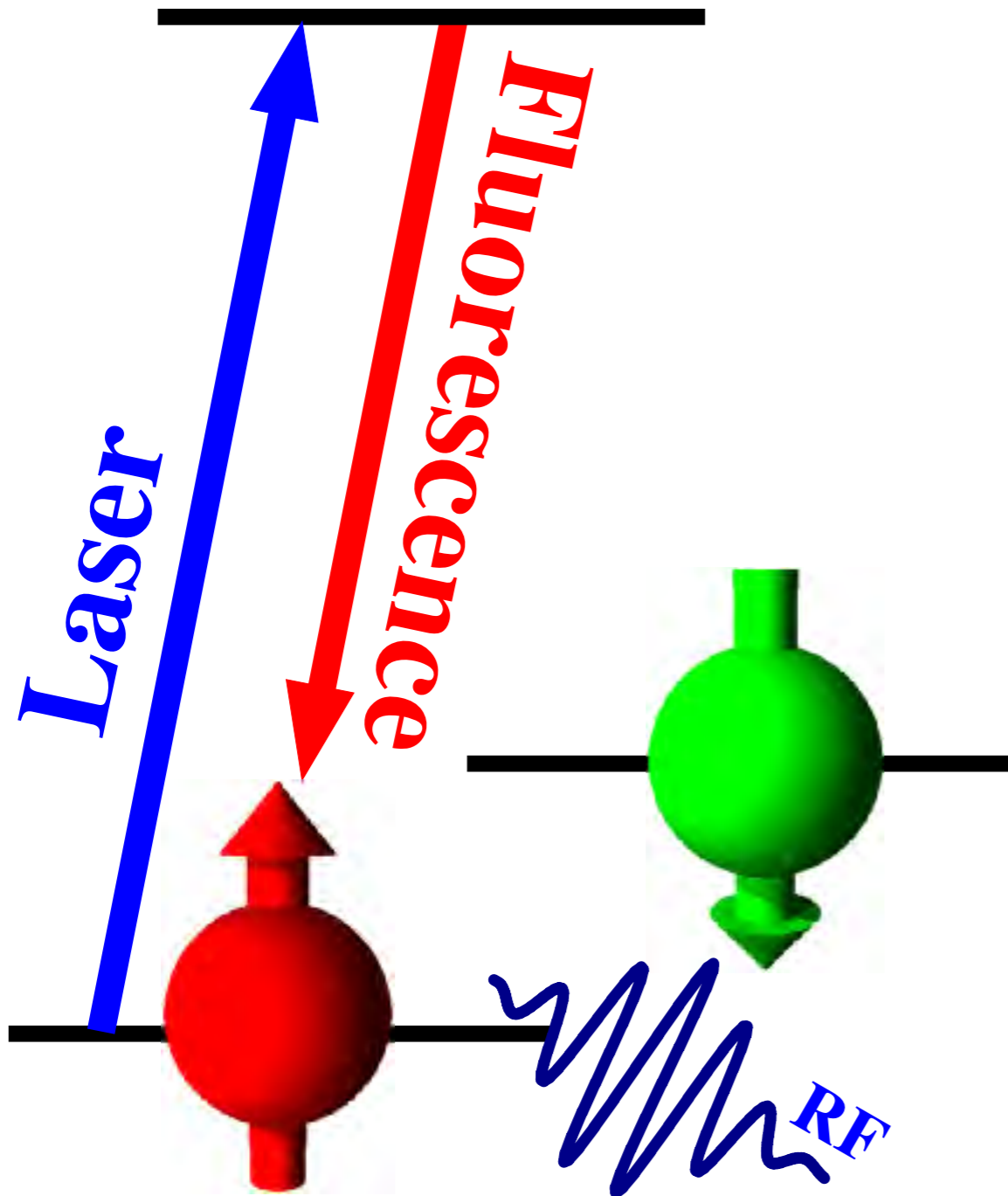


J. Wrachtrup, A. Gruber, L. Fleury, and C.v. Borczyskowski, *Chem. Phys. Lett.* **267**, 179 (1997).

Single-Spin Detection

by optically detected magnetic resonance

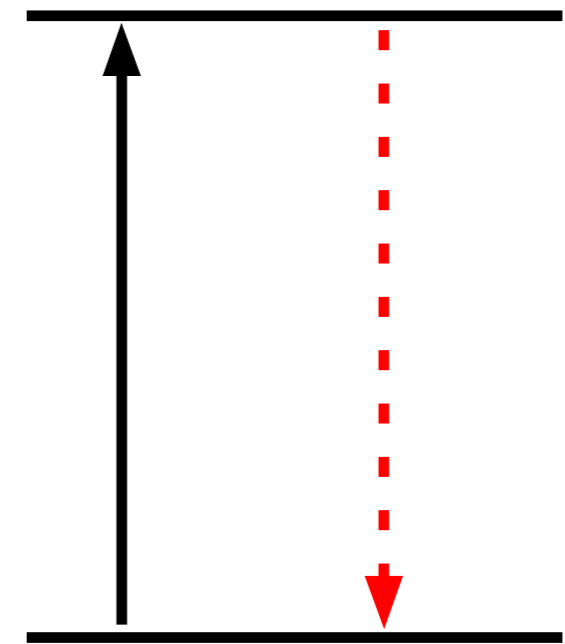
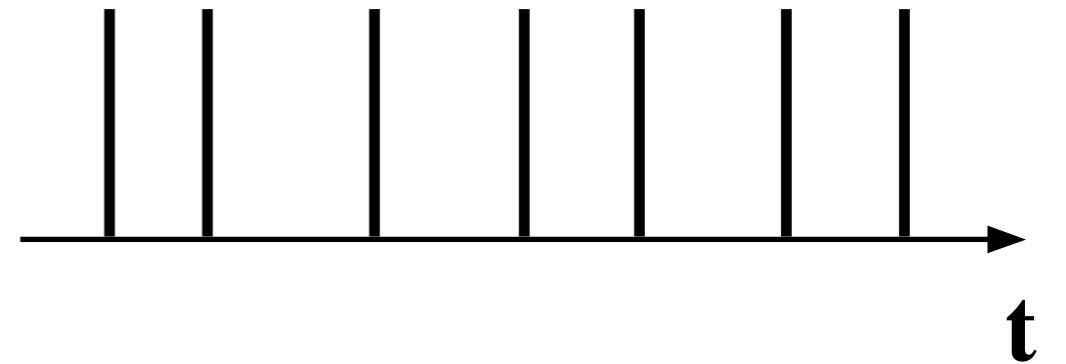
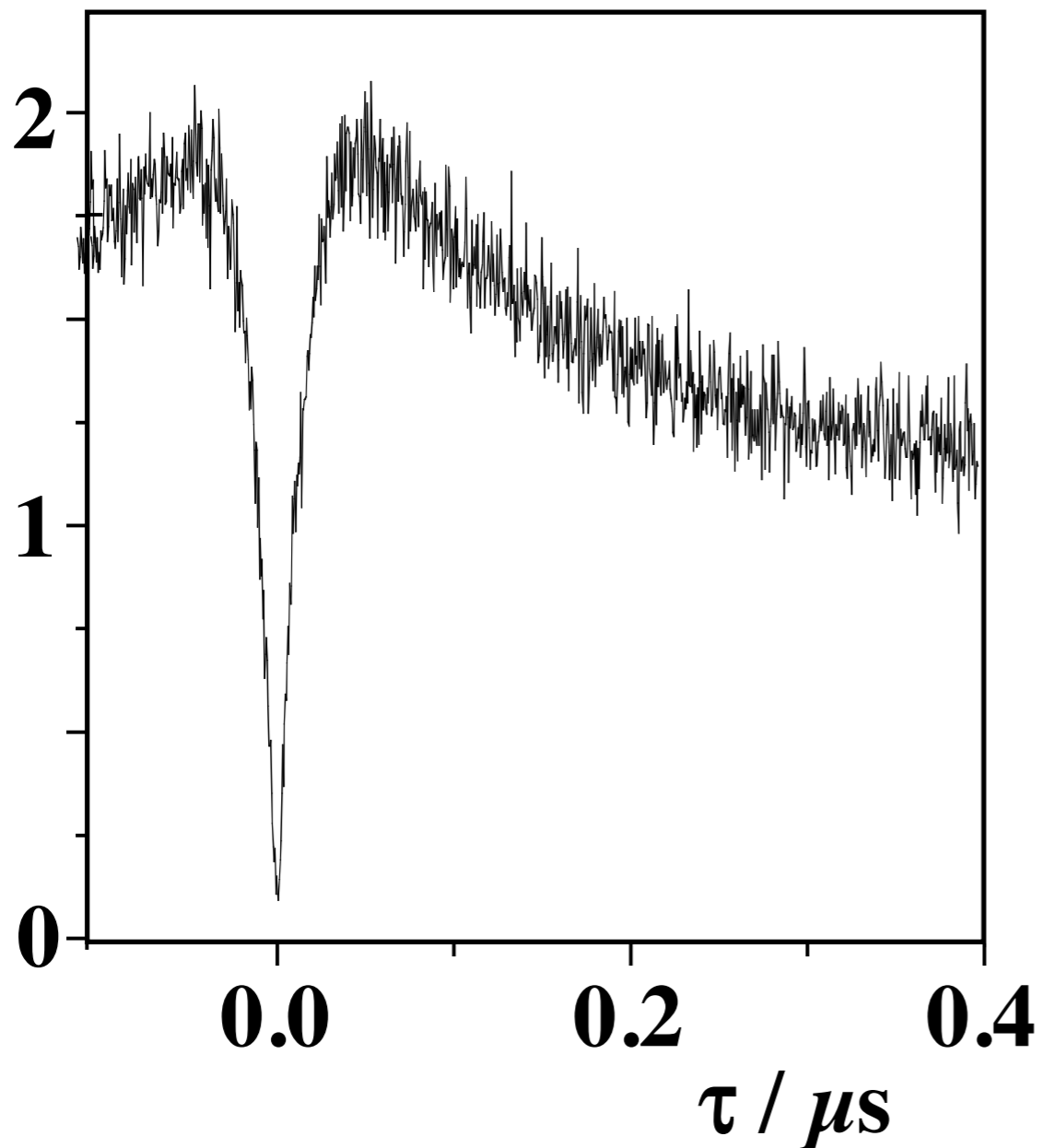
Diamond N/V center



F. Jelezko, C. Tietz, A. Gruber, I. Popa, A. Nizovtsev, S. Kilin, and J. Wrachtrup, *Single Mol.* 2, 255 (2001).

Single Center : Photon Antibunching

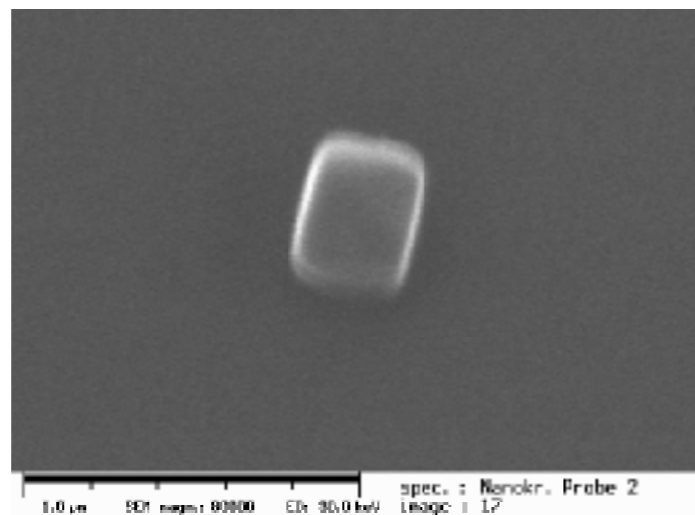
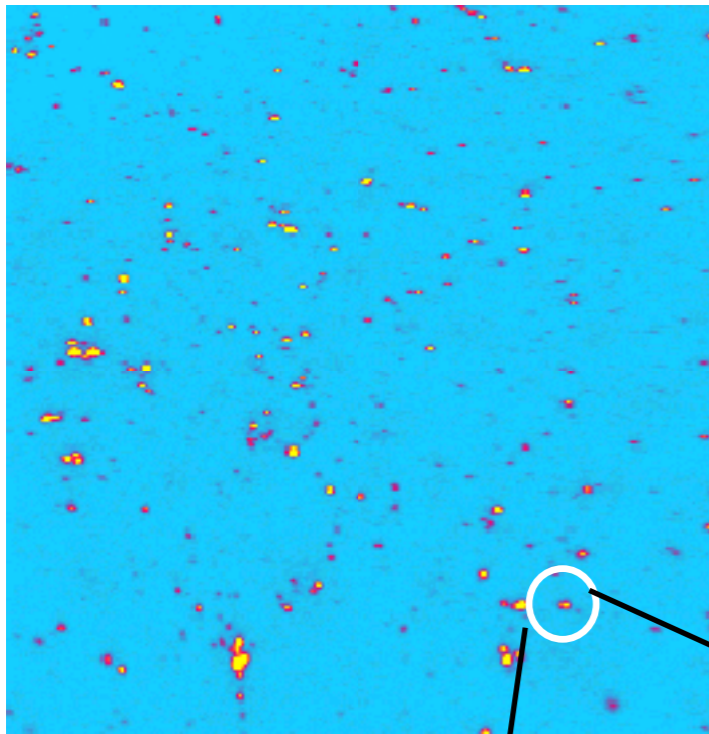
$$g^{(2)}(\tau) = \frac{\langle I(t) I(t+\tau) \rangle}{\langle I(t) \rangle^2}$$



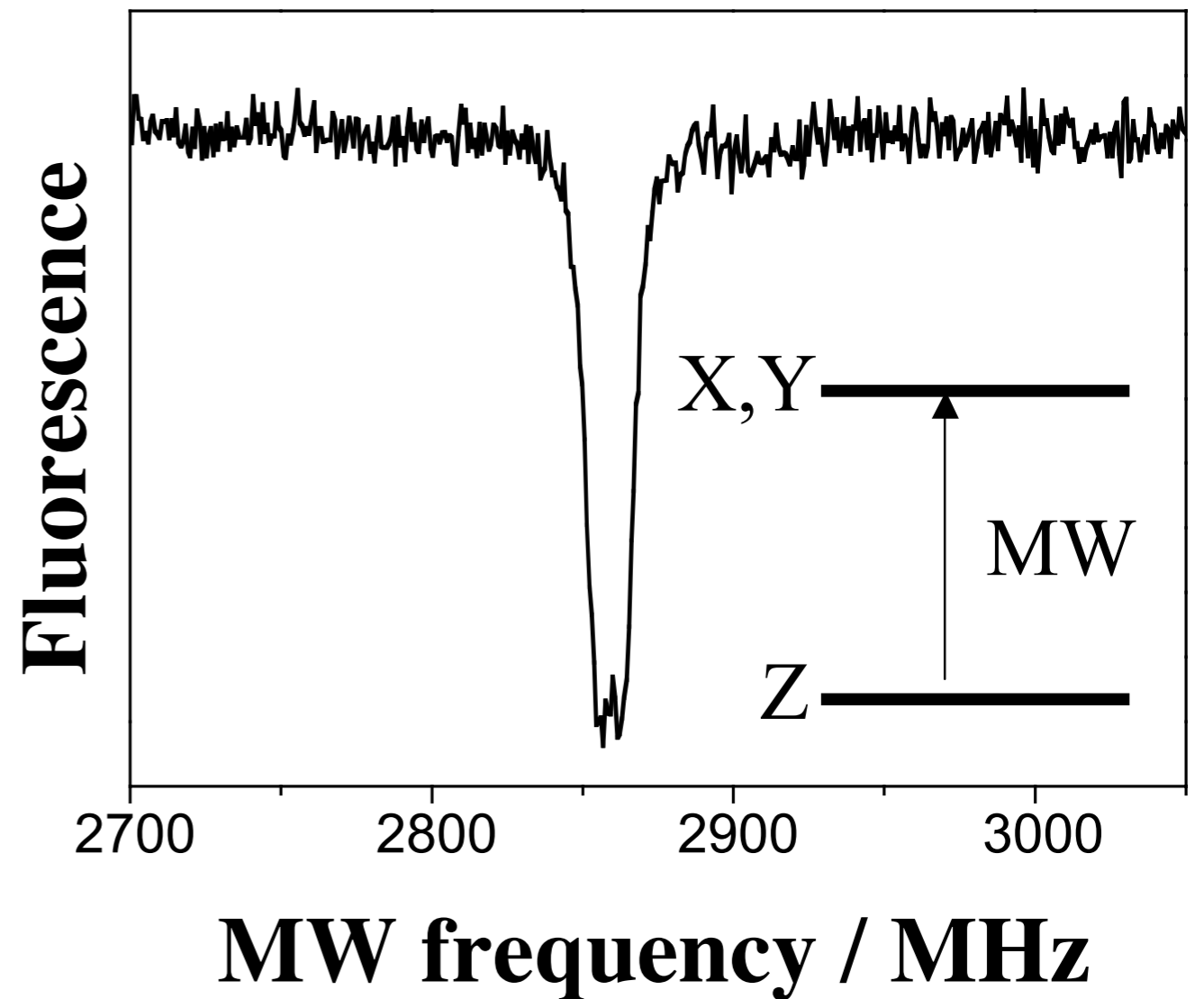
Single Center : Spectroscopy

NV - containing nanocrystals

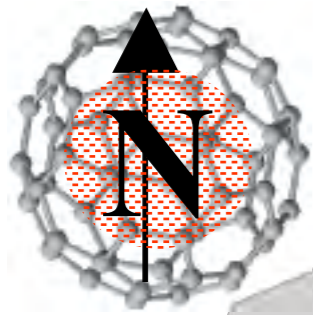
Fluorescence



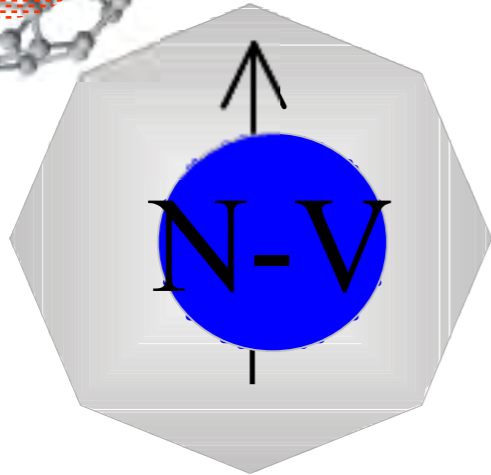
EM image



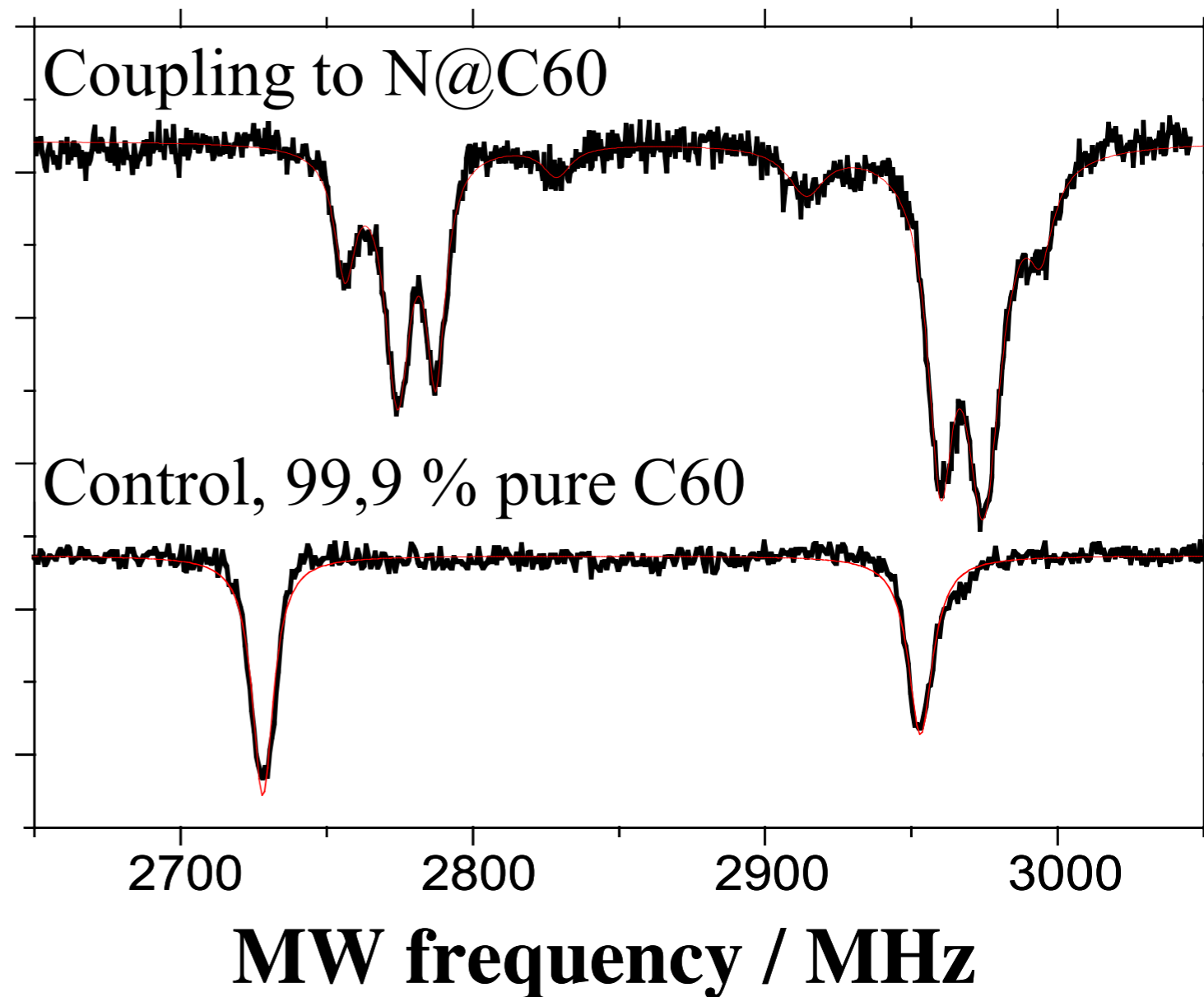
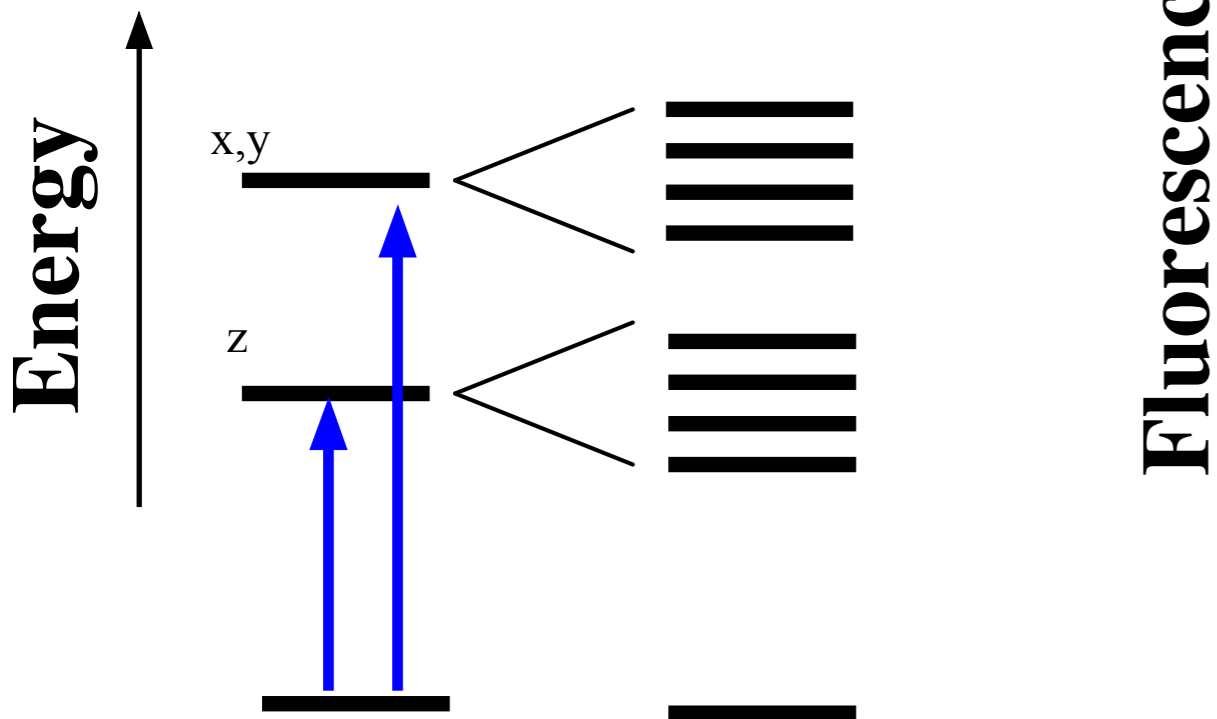
Detecting N@C60 Spins



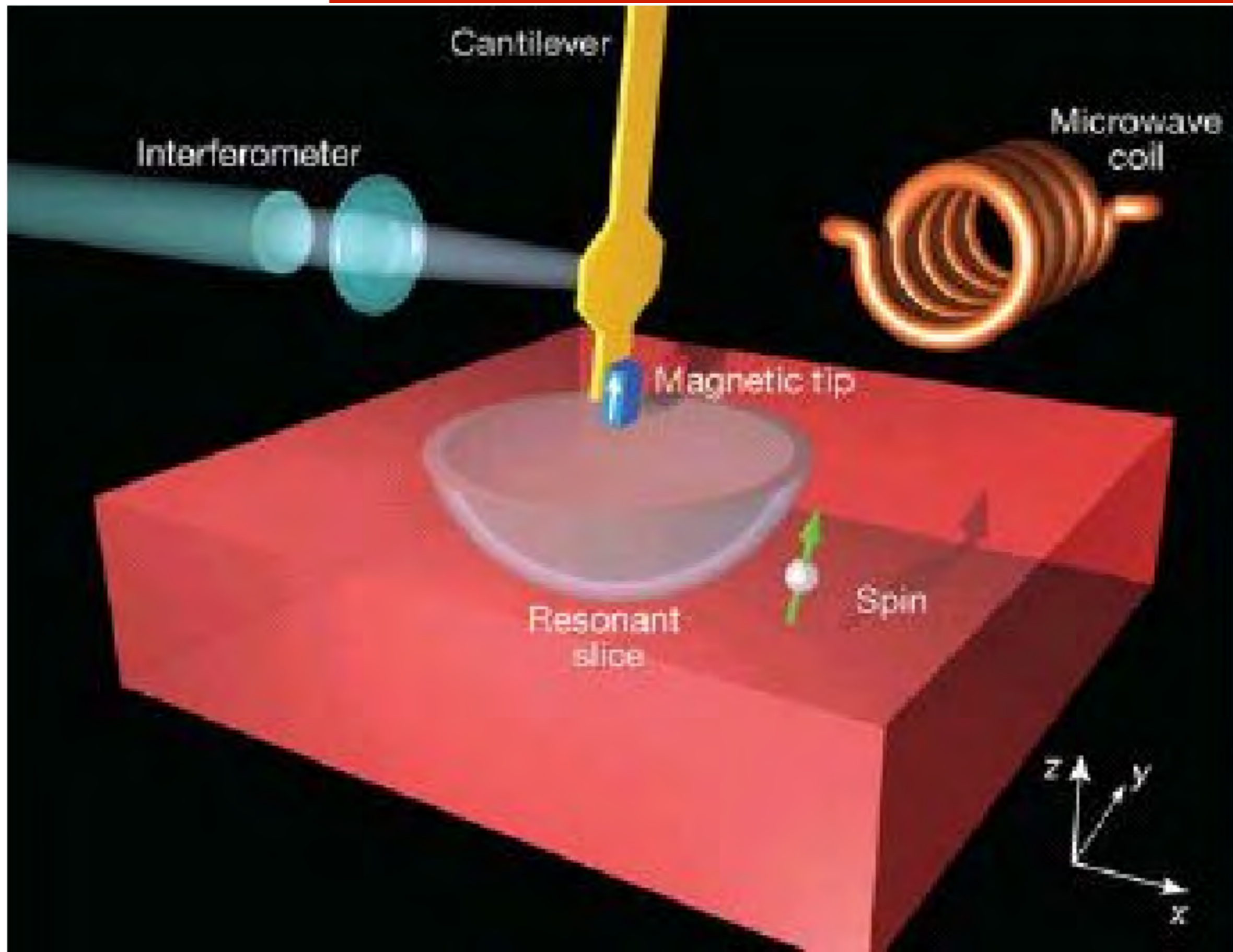
use N/V center as field probe



N/V N/V + N@C60

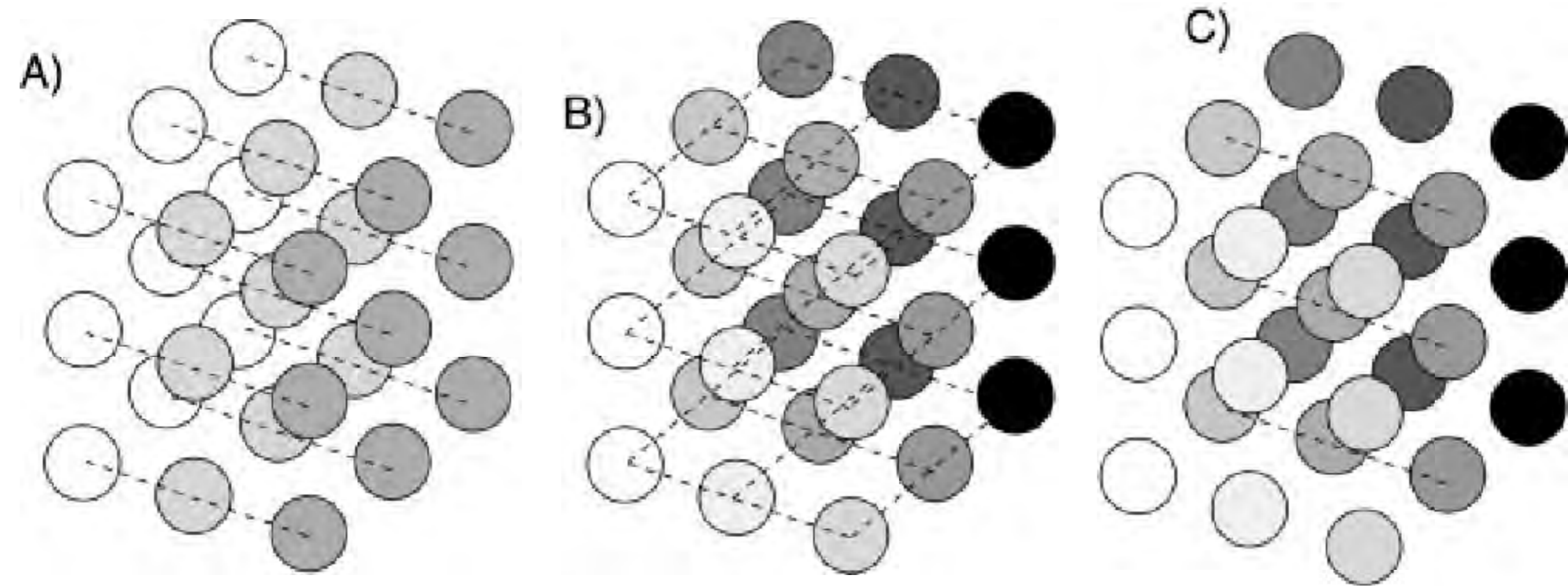


Single Spin Force Detection



Crystal Lattice Quantum Computer

F. Yamaguchi, and Y. Yamamoto, 'Crystal lattice quantum computer', Appl. Phys. A 68, 1 (1999).



Detection e.g. by vibrating cantilever

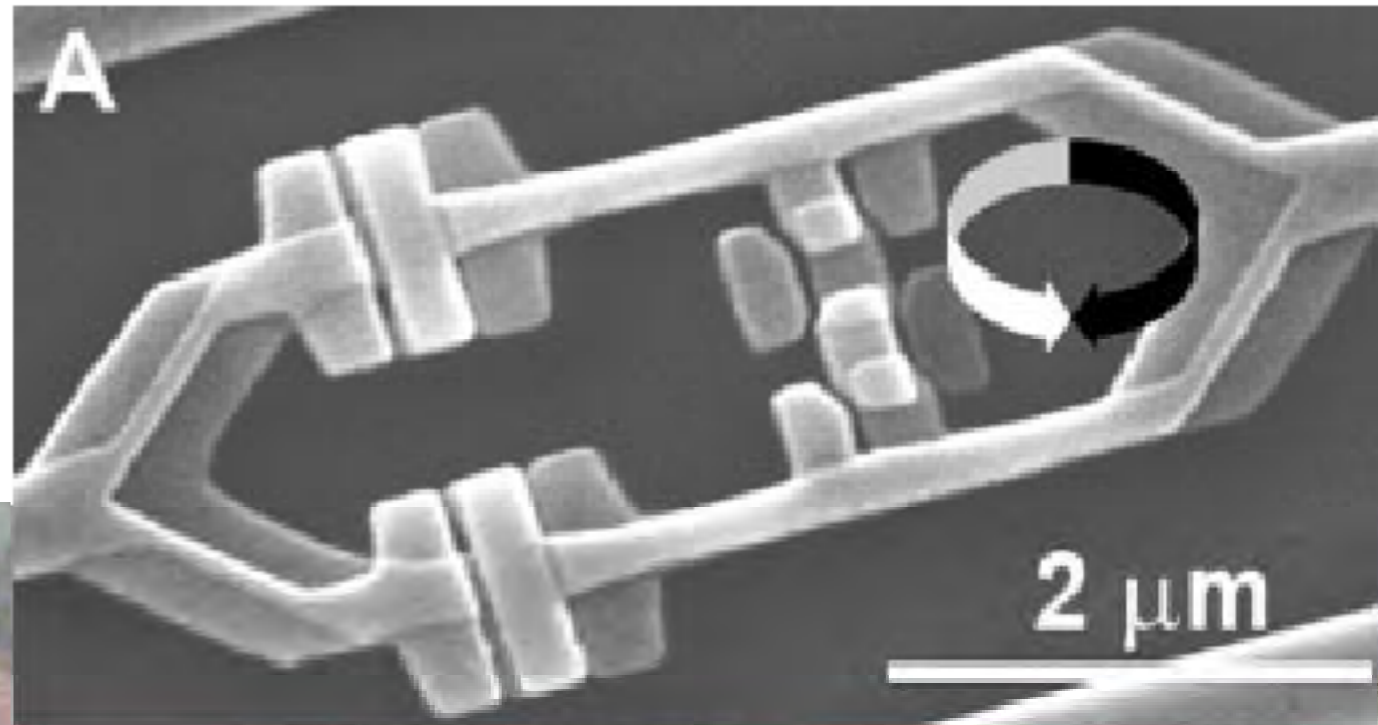
12.2 *Superconducting Systems*

12.2.1 Charge Qubits

12.2.2 Flux Qubits

12.2.3 Gate Operations

12.2.4 Readout



Superconducting Qubits

Macroscopic quantum state

Easily coupled to each other

Can be integrated

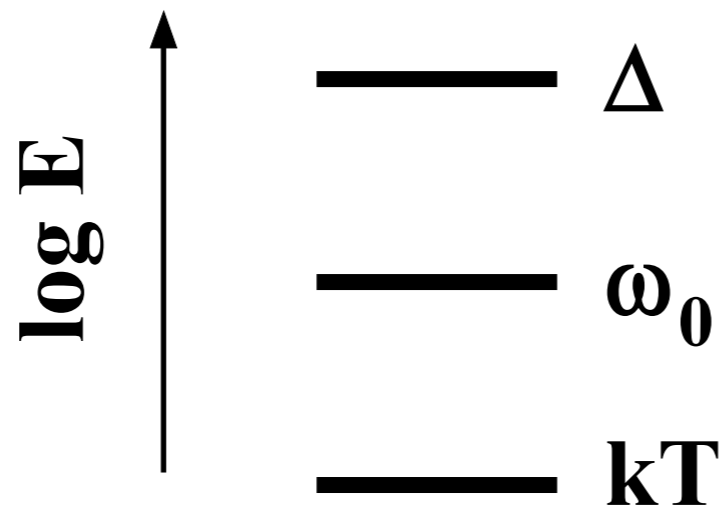
Non-dissipative:

Must operate at < 50 mK

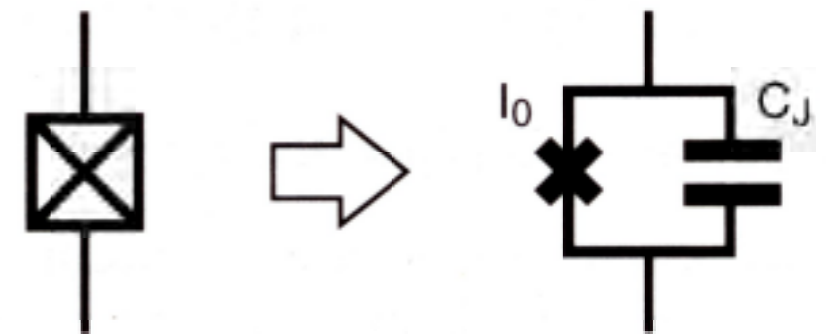
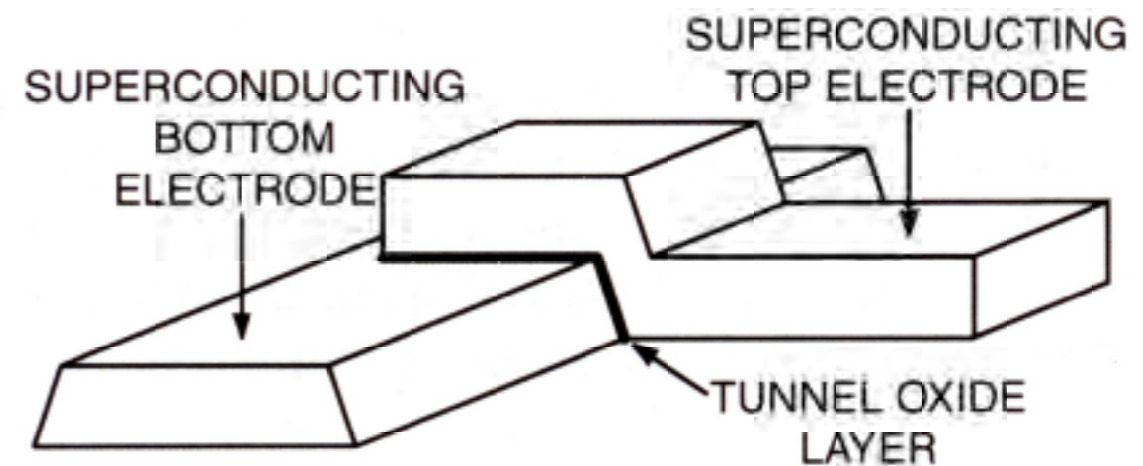
Only superconducting elements

Electron temperature < 50 mK

Energy scales:



Josephson junction

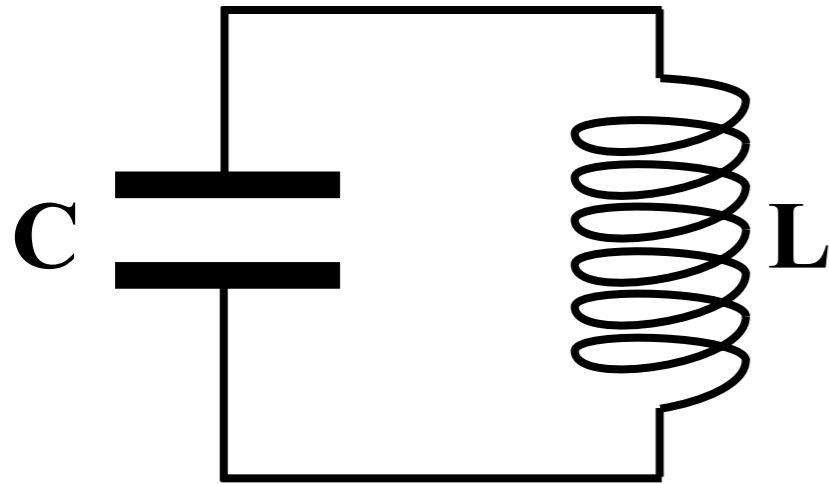


Relevant Observables

Flux Φ = phase difference

Charge Q

Harmonic Oscillator



Classical $\frac{d^2Q}{dt^2} + \frac{Q}{LC} = 0$

Quantum $H = \frac{\Phi^2}{2L} + \frac{Q^2}{2C}$
 $= \hbar\omega_0(n + \frac{1}{2})$

Typical values:

Dimension $\sim 10 \mu\text{m}$

L $\sim 0.1 \text{ nH}$

C $\sim 1 \text{ pF}$

$\omega_0/2$ $\sim 16 \text{ GHz}$

$$[\Phi, Q] = i \hbar$$

\nearrow **~Position** \nwarrow **~Momentum**

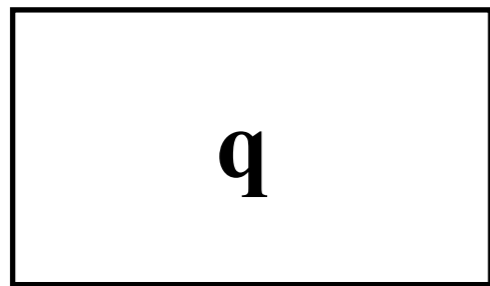
Main challenges:

Coupling to environment

Variability of engineered circuits

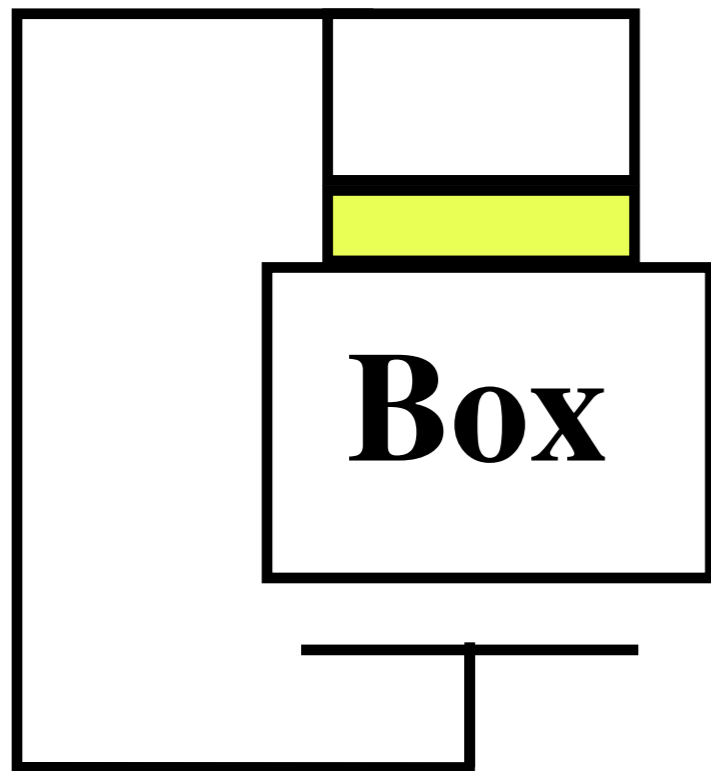
Cooper Pair Box

Coulomb energy of a box:



$$E_C = \frac{q^2}{2C} = \frac{(2ne)^2}{2C} = \frac{2n^2e^2}{C}$$

Hamiltonian including tunnel junction



tunable by
offset voltage

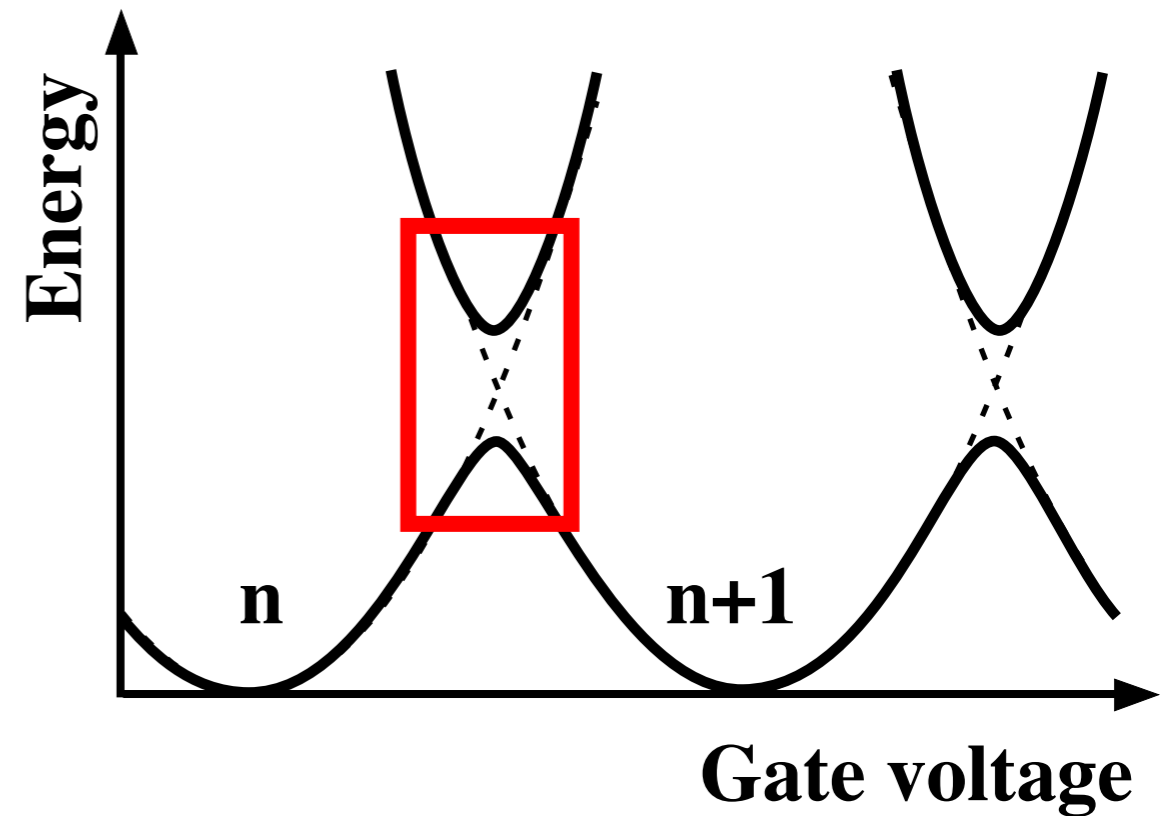
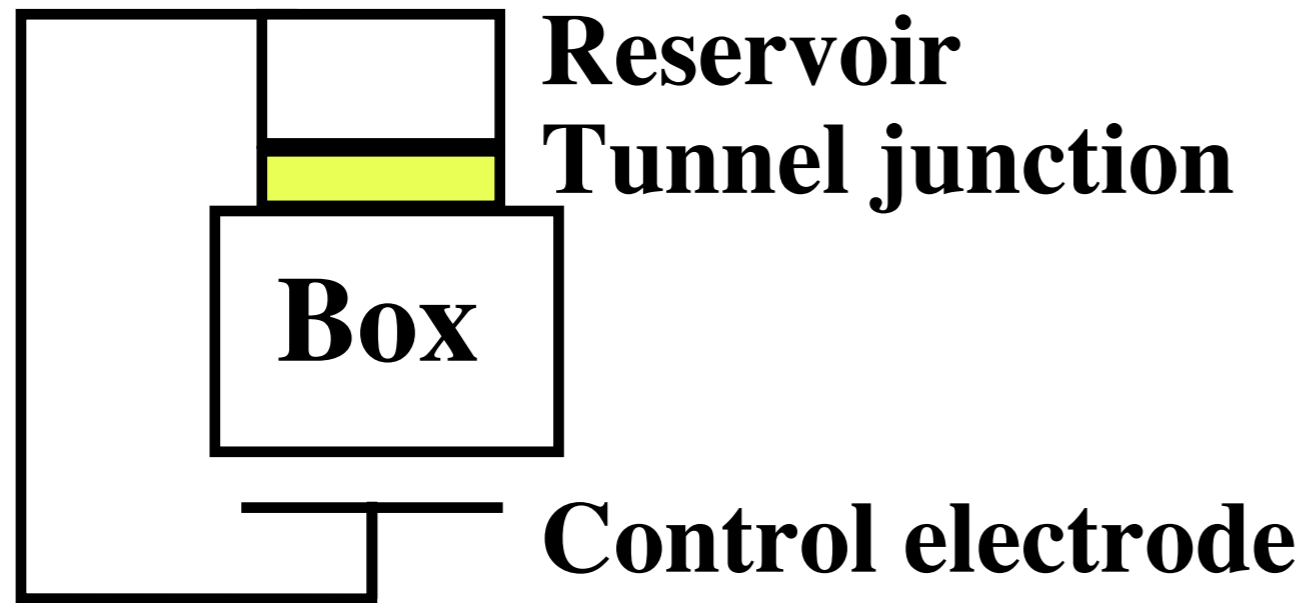
tunable by flux
through split junction

$$H = E_C(N - N_g)^2 - E_J \cos\theta$$

Cooper pairs
on island

Phase difference
across junction

Charge Qubit



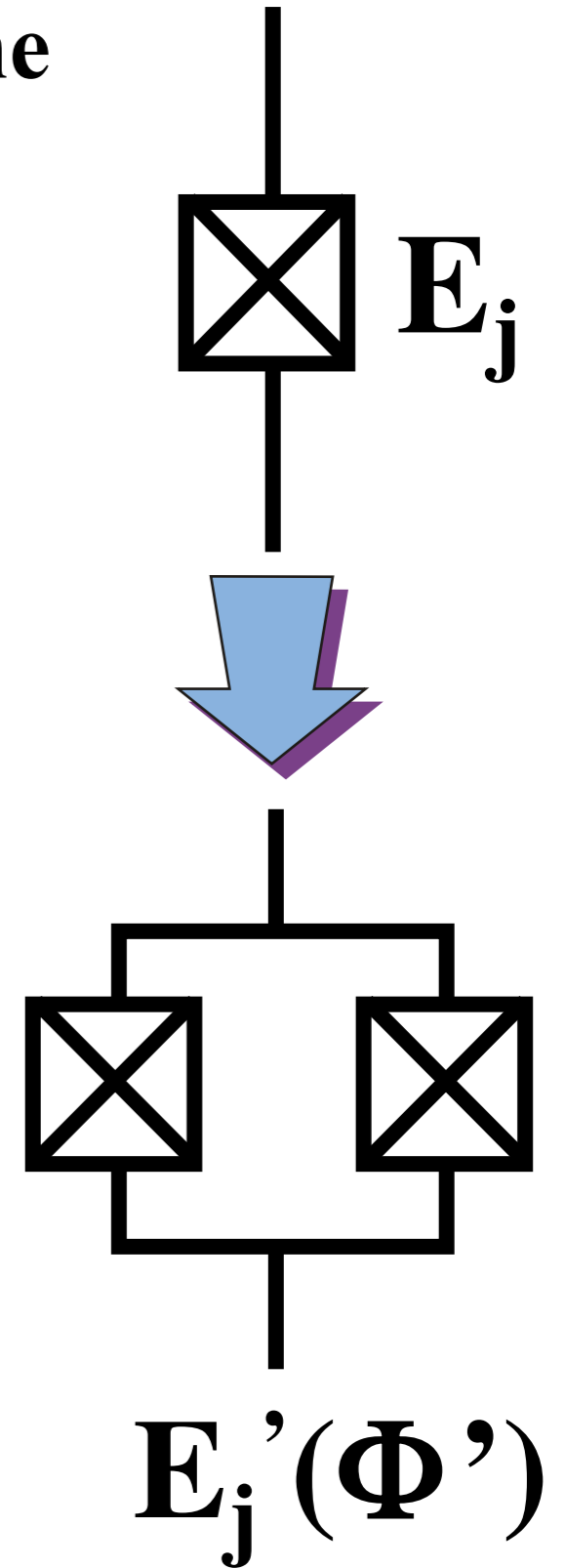
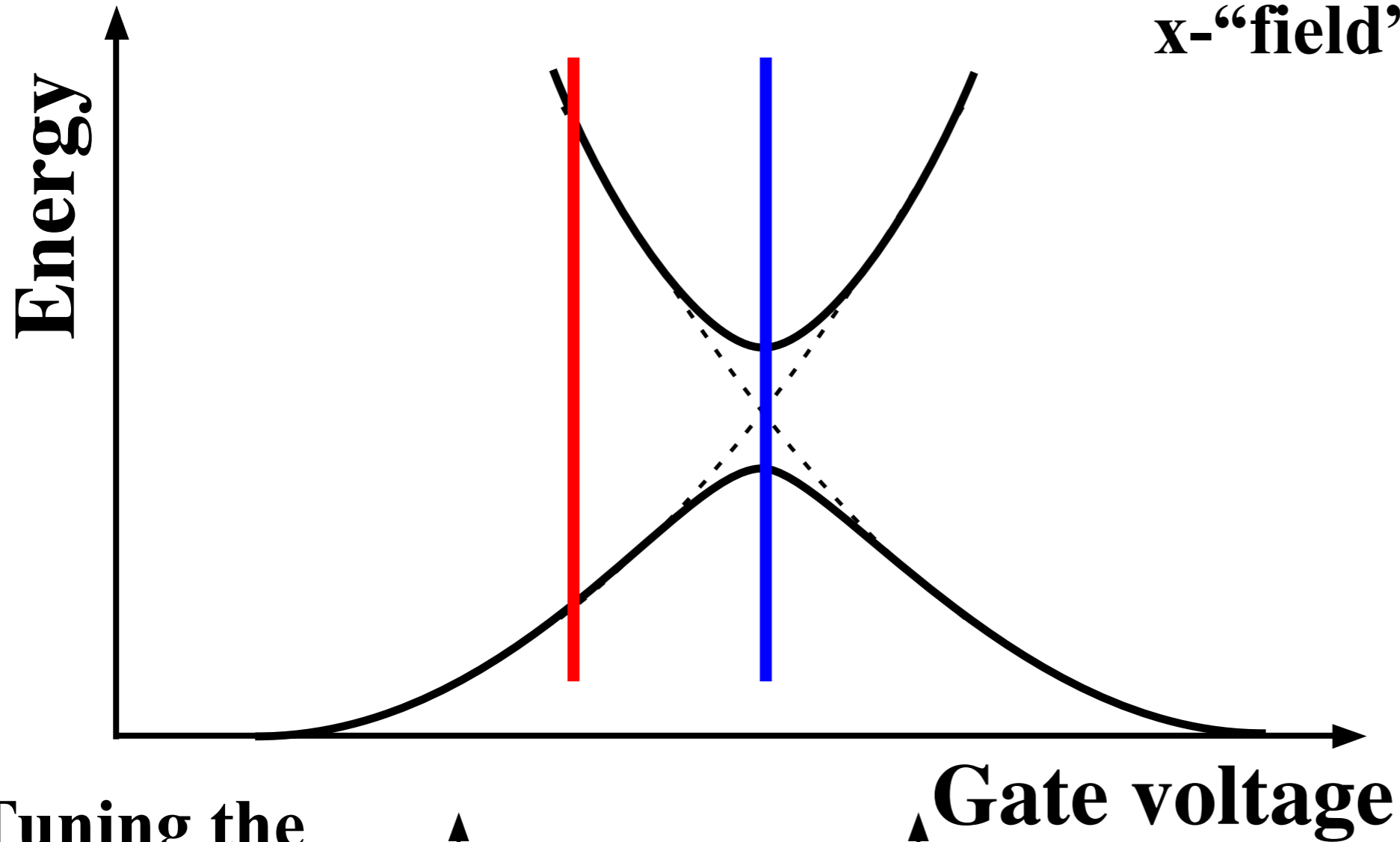
Qubit states: $|n\rangle, |n+1\rangle$

Qubit Hamiltonian:

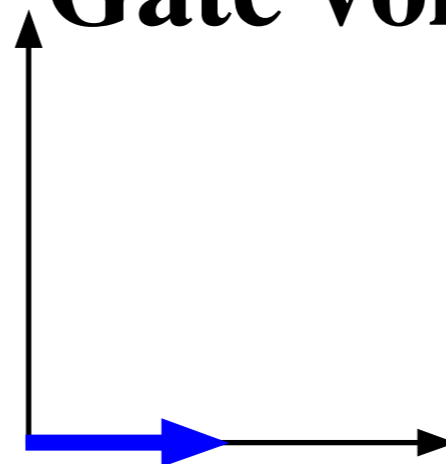
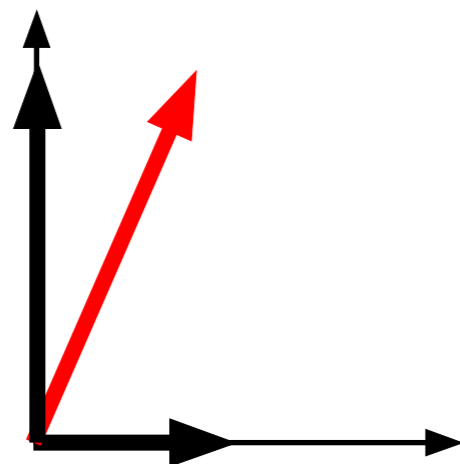
$$\mathcal{H} = 4 \frac{E_C}{\hbar} (1 - 2n_g) \mathbf{S}_z - \frac{E_J}{\hbar} \mathbf{S}_x$$

Gate Operations

Tuning the
x-“field”

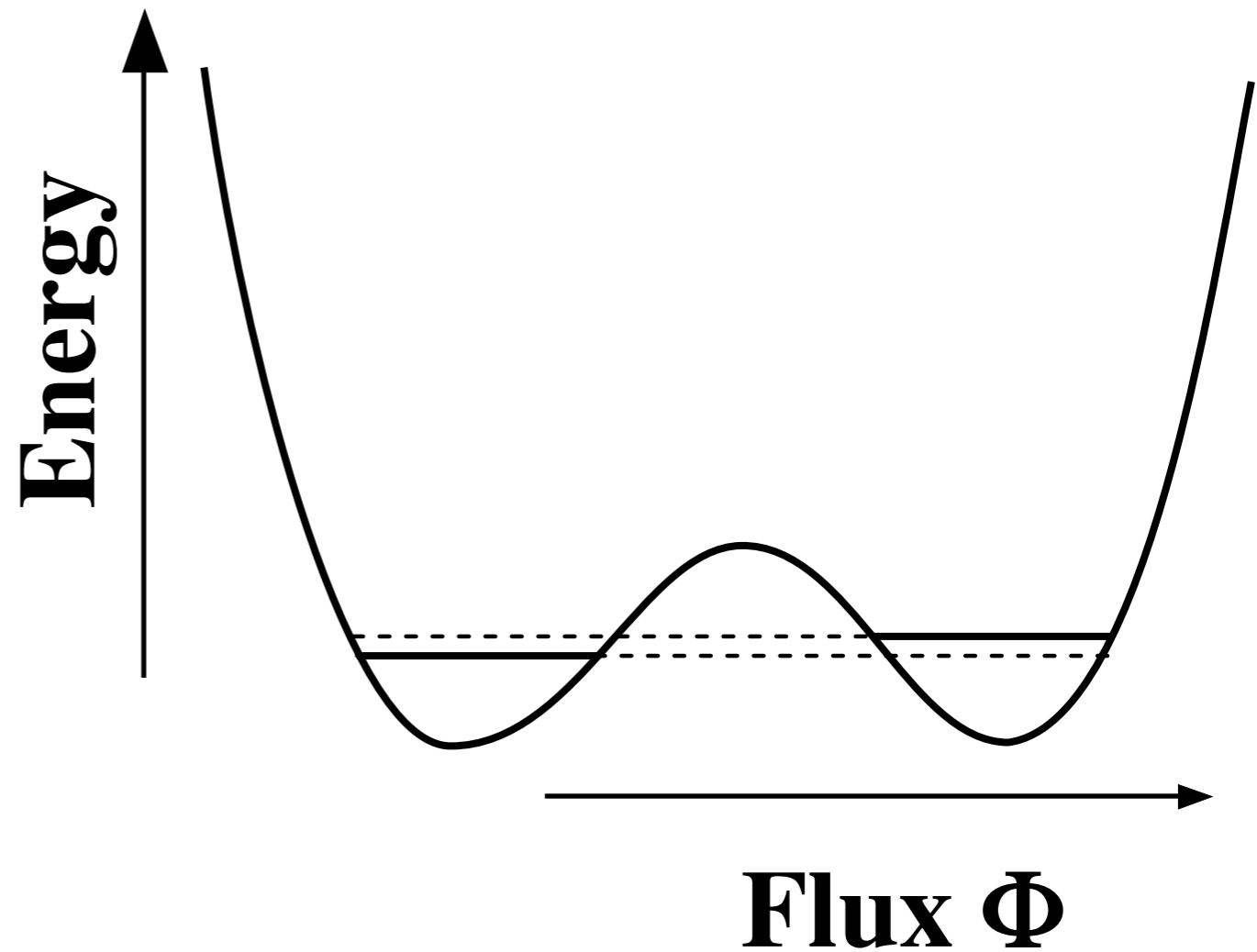
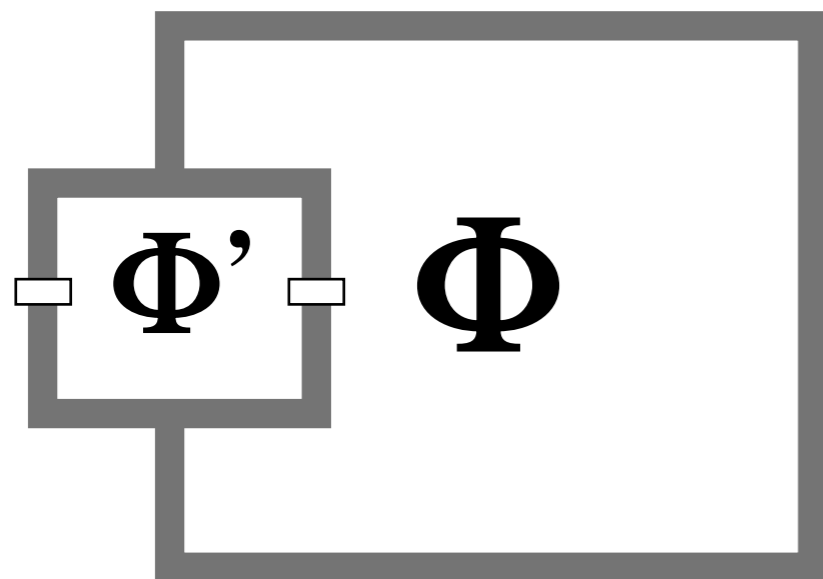
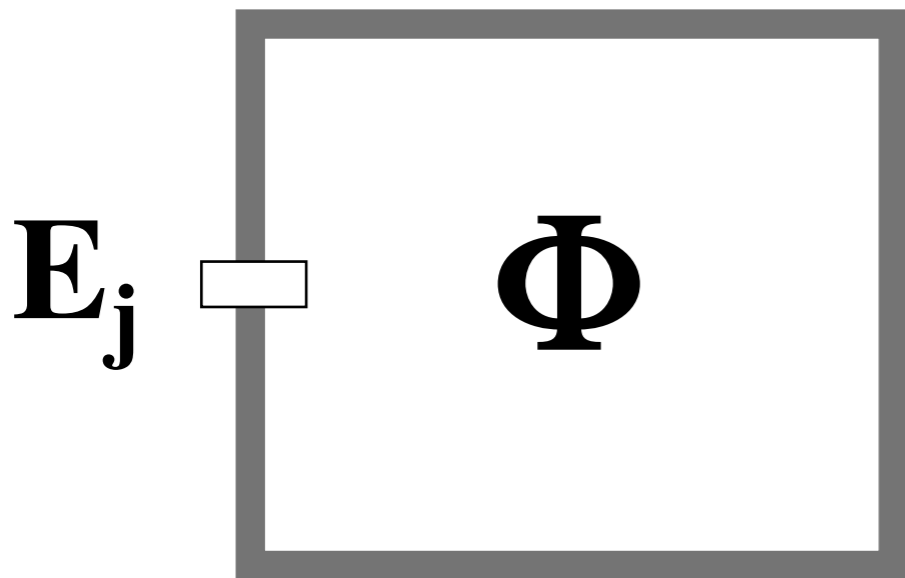


Tuning the
z-“field”

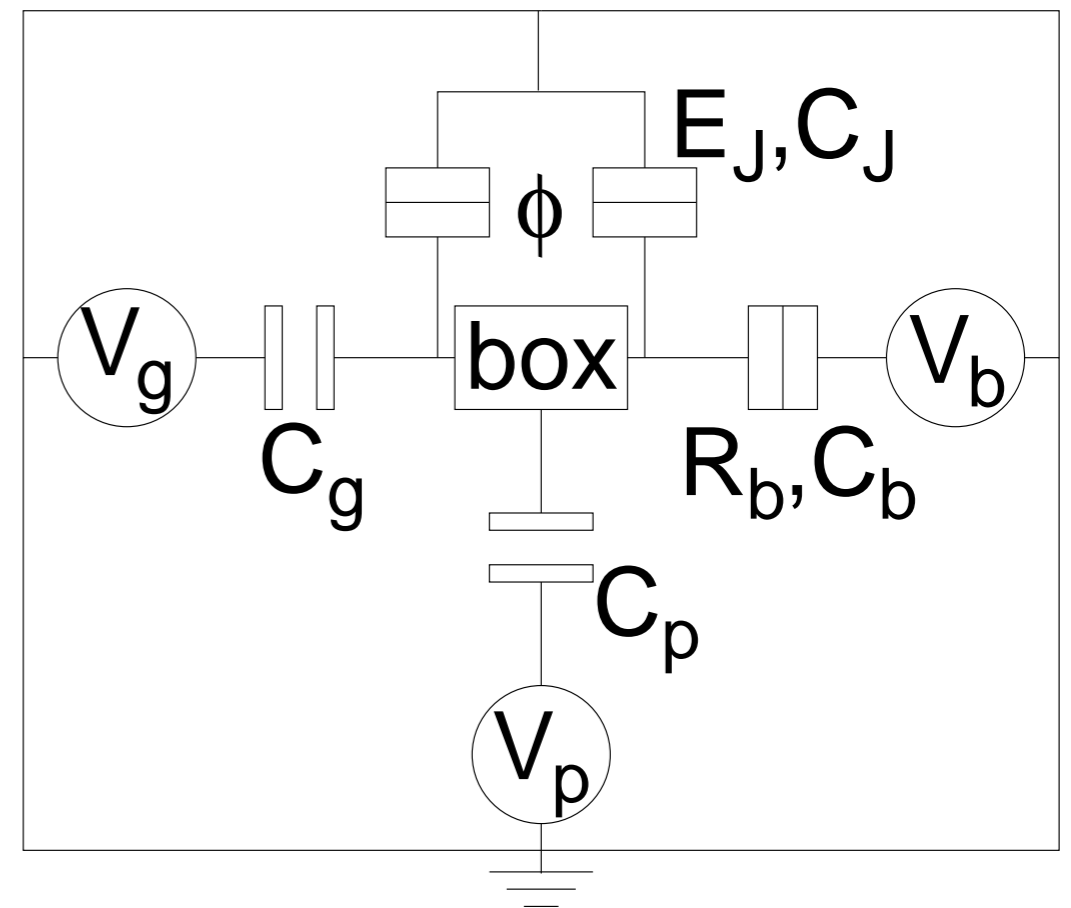
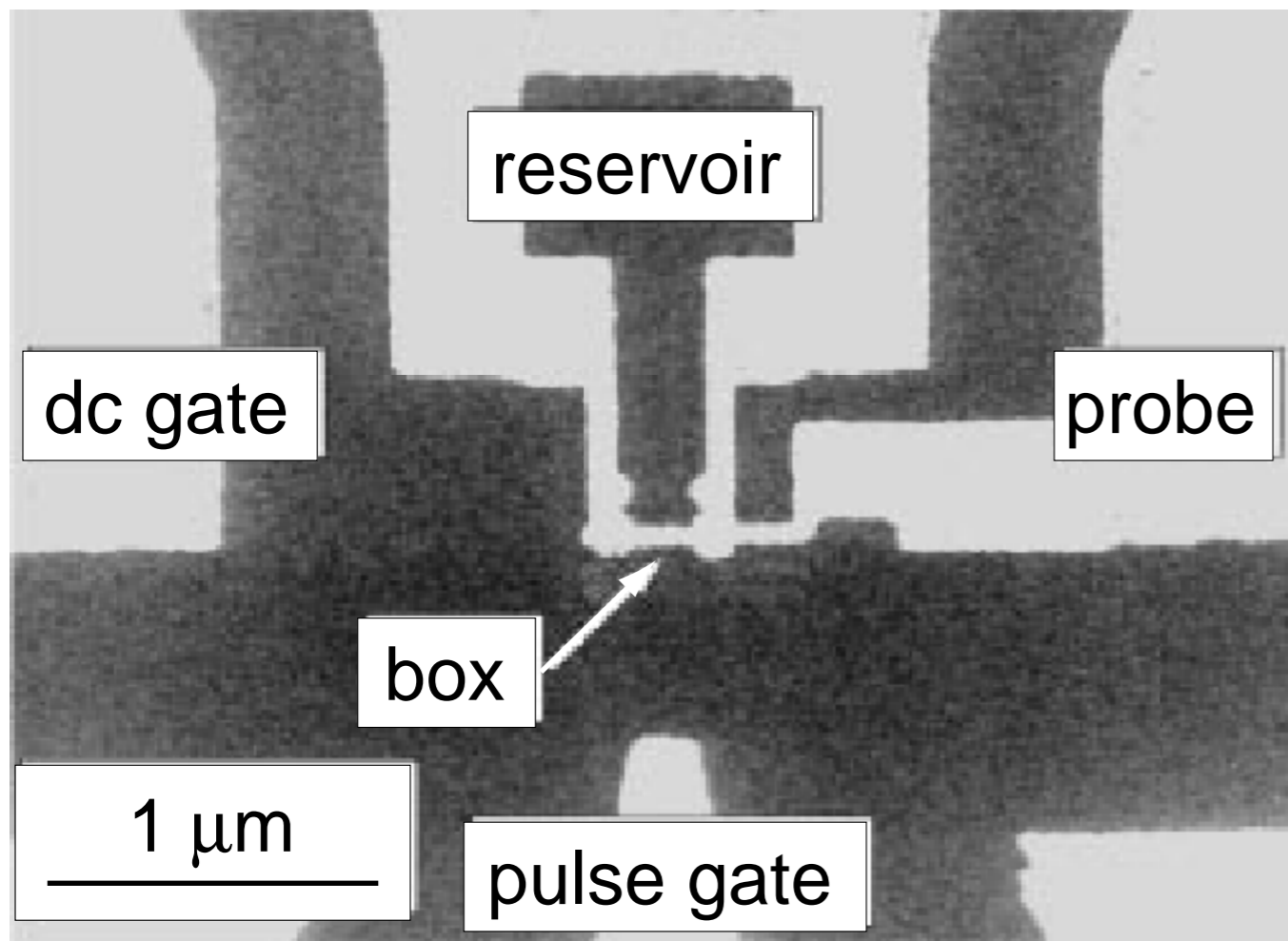


Flux Qubit

$$\mathcal{H}_{\text{fl}} = -E_J \cos\left(2\pi \frac{\Phi}{\Phi_0}\right) + \frac{(\Phi - \Phi_x)^2}{2L} + \frac{Q^2}{2C_J}$$

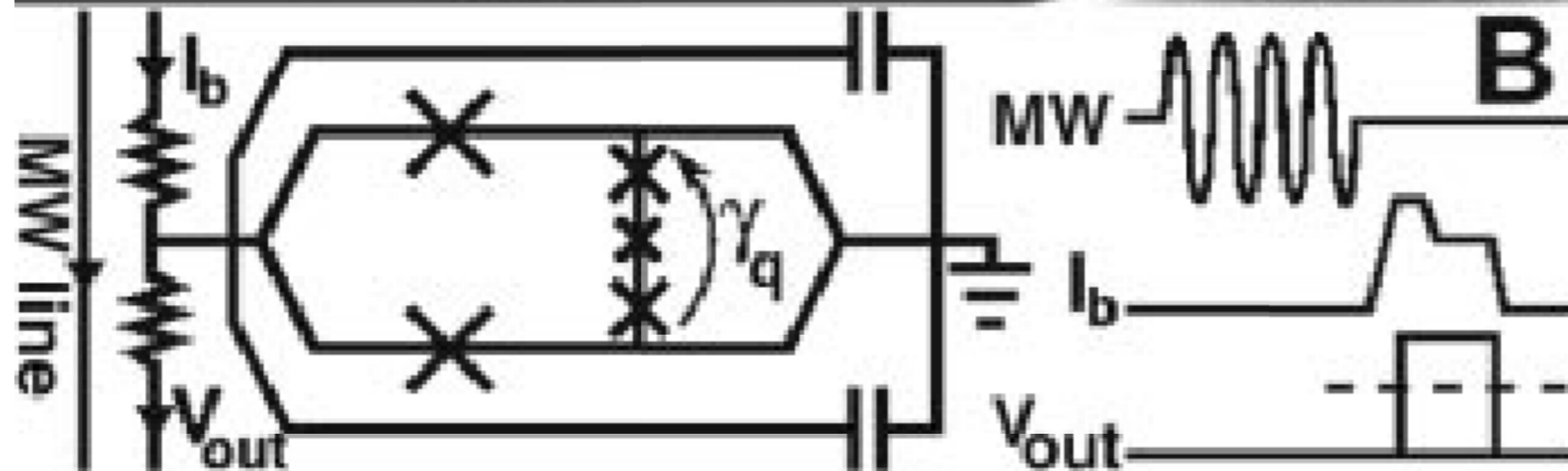
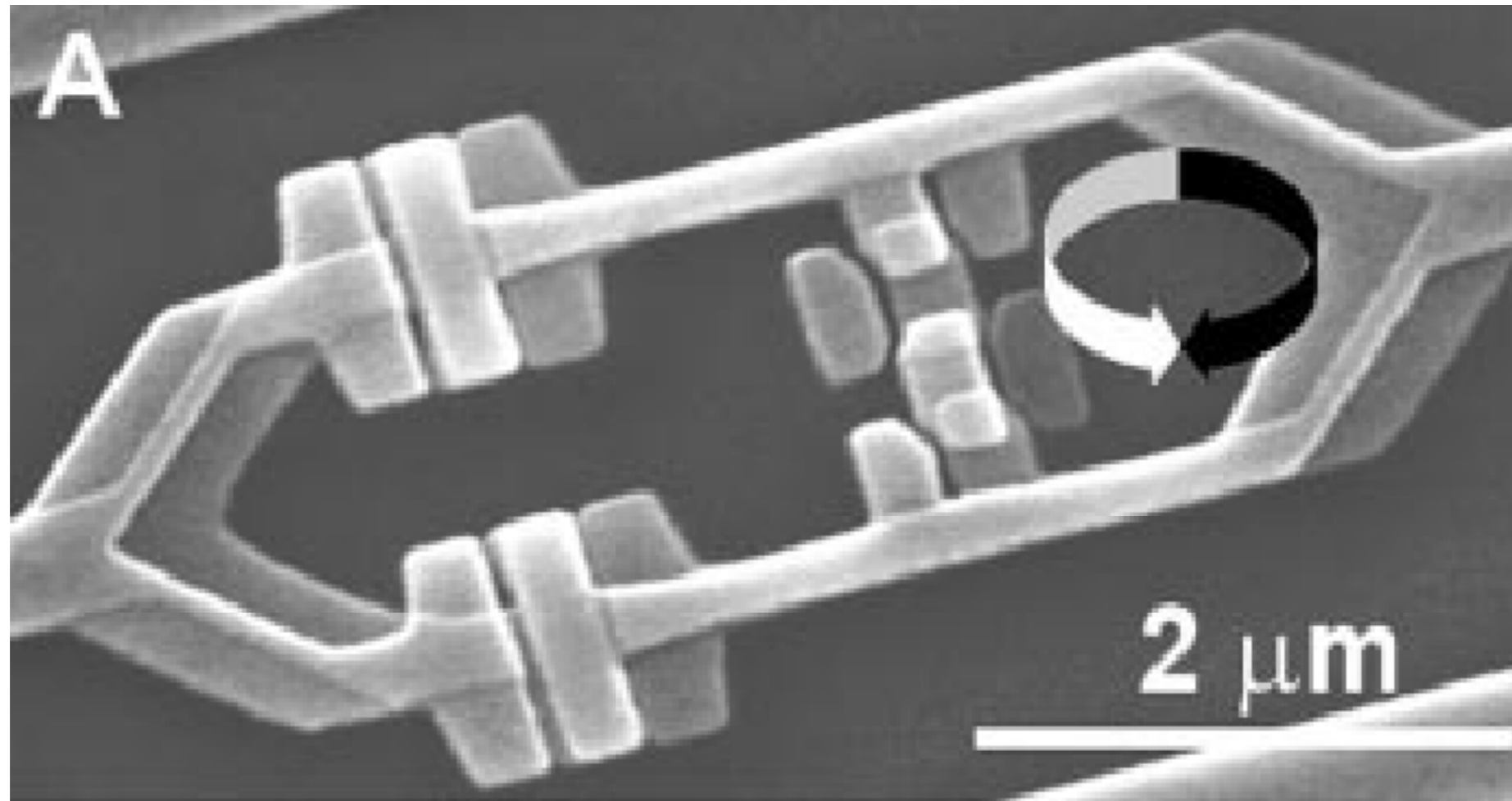


Josephson Qubit

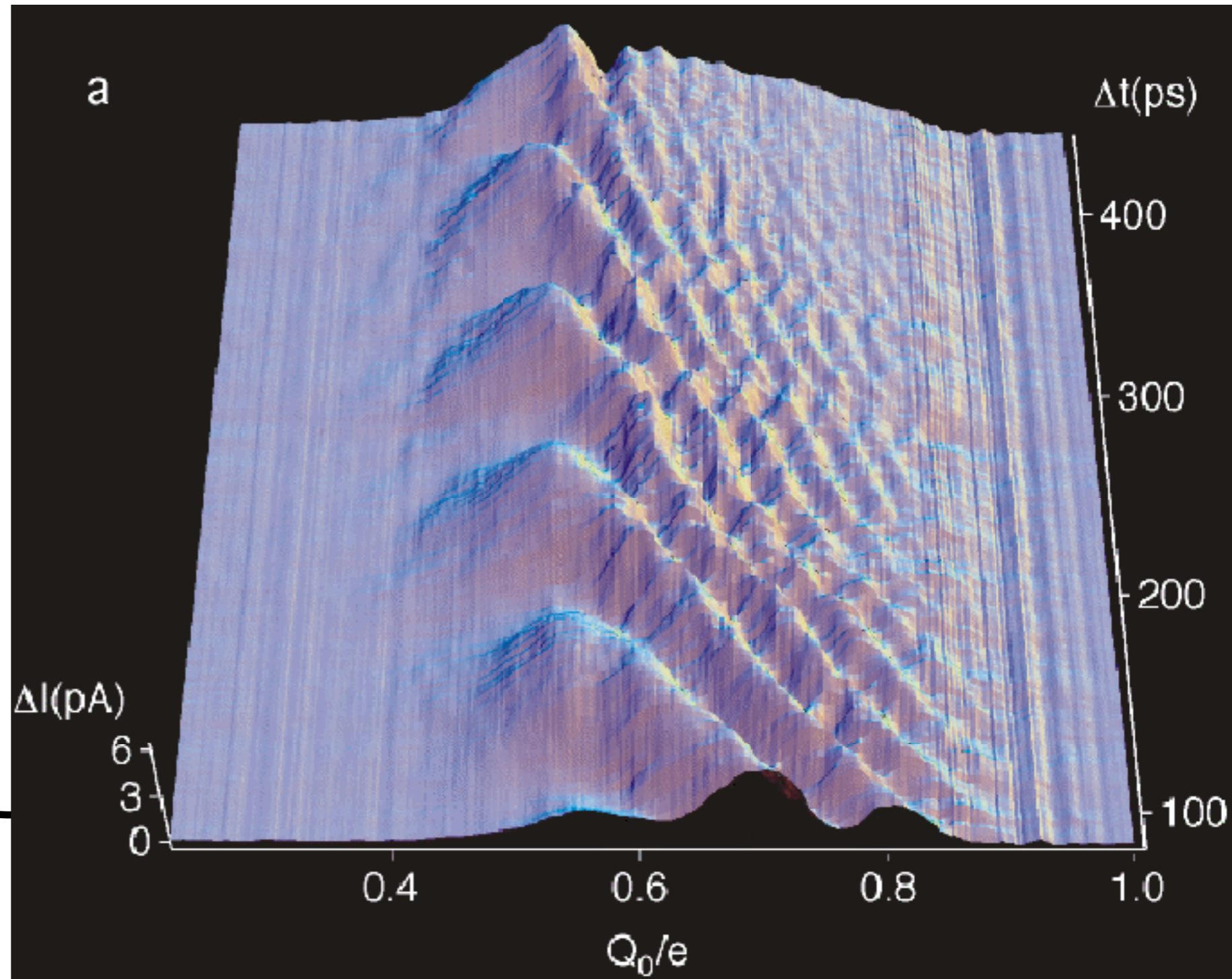
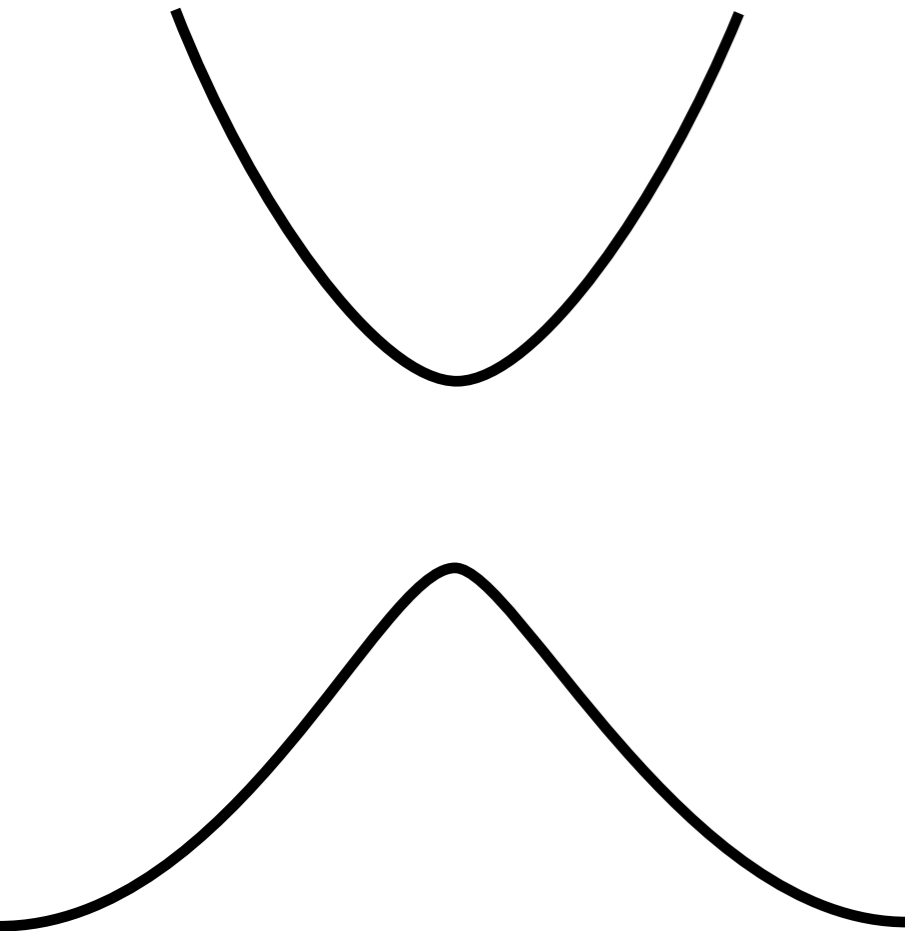


 : tunnel junction
 : capacitor

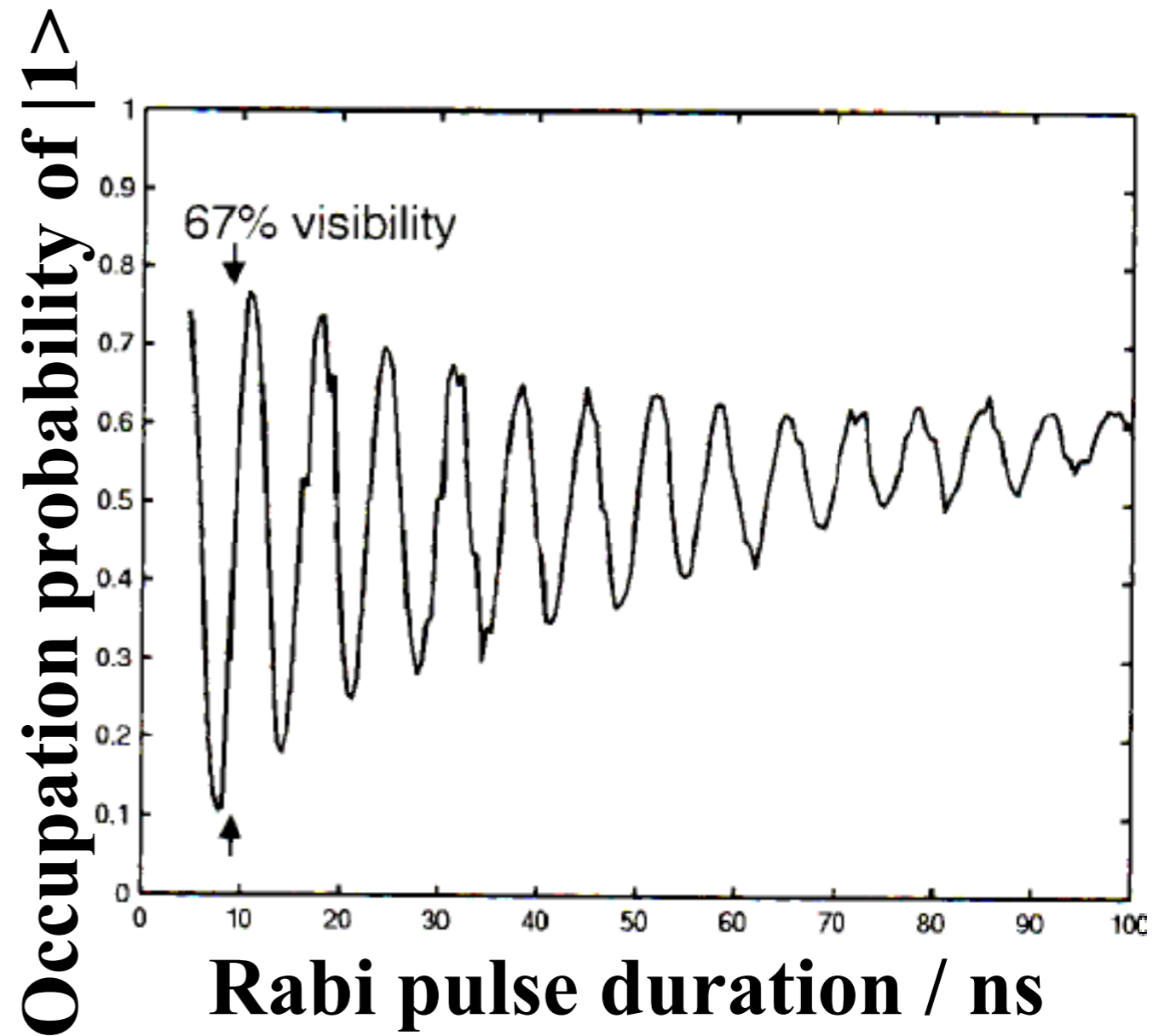
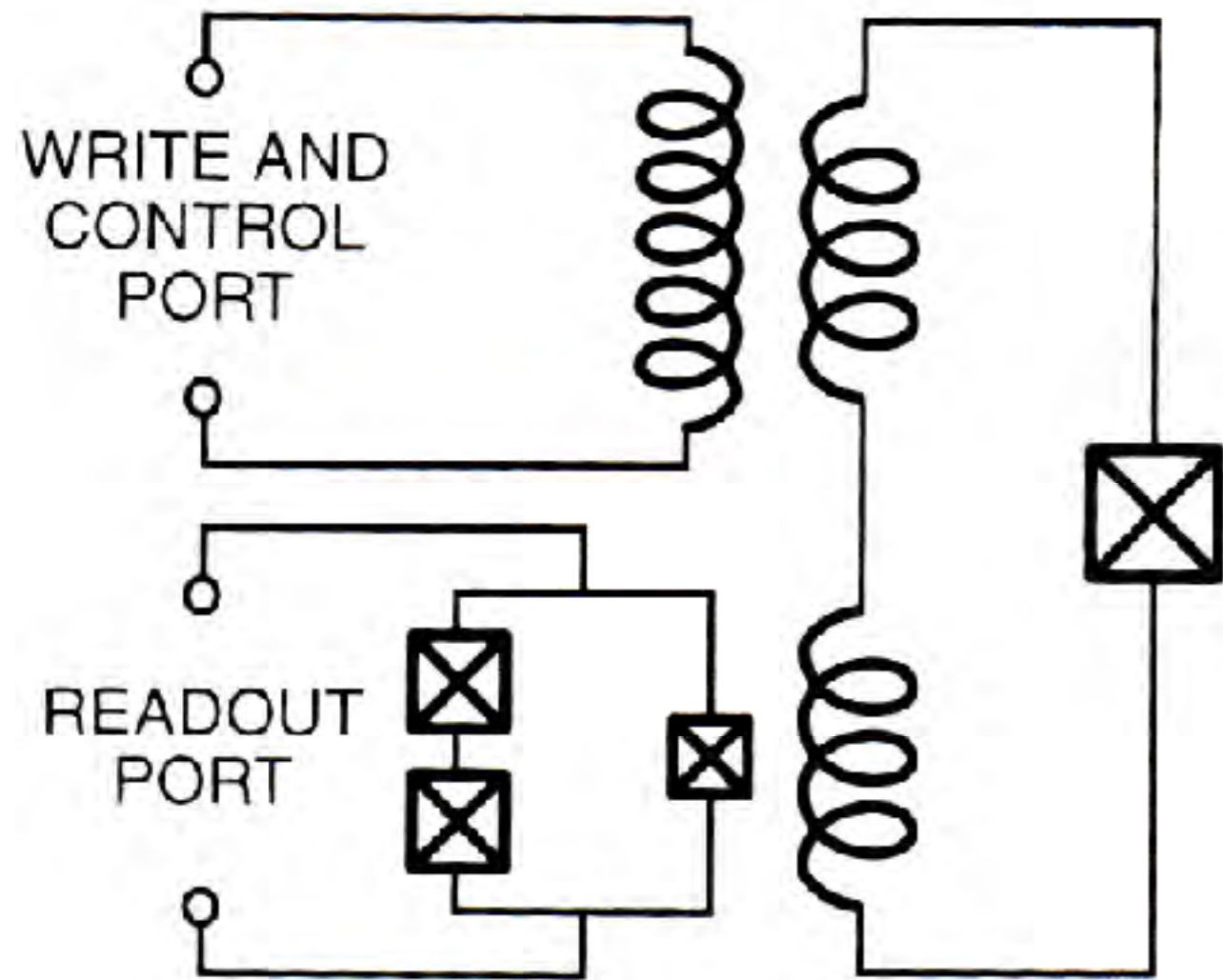
Flux Qubit



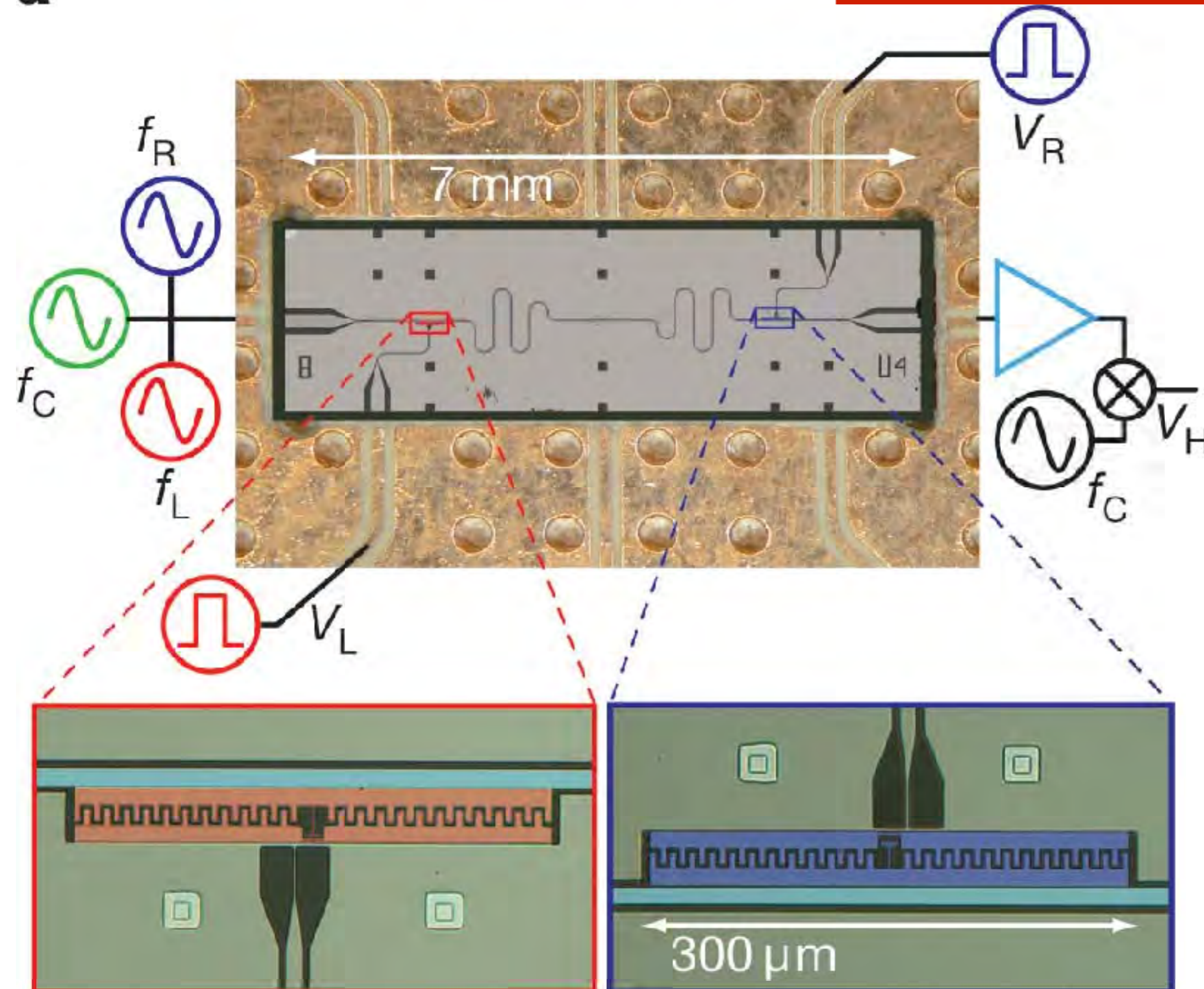
Rabi Oscillations



Resonant Excitation

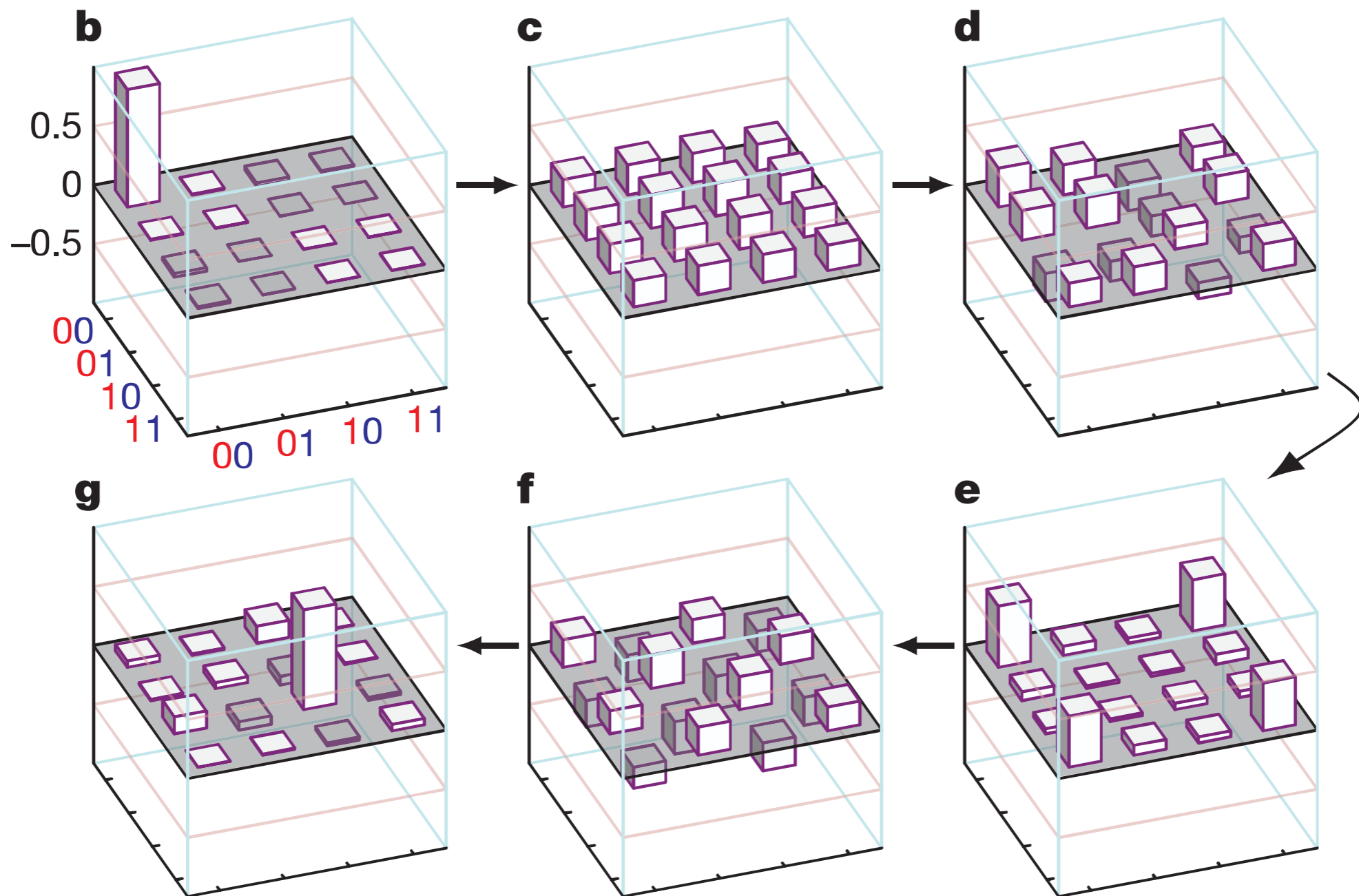
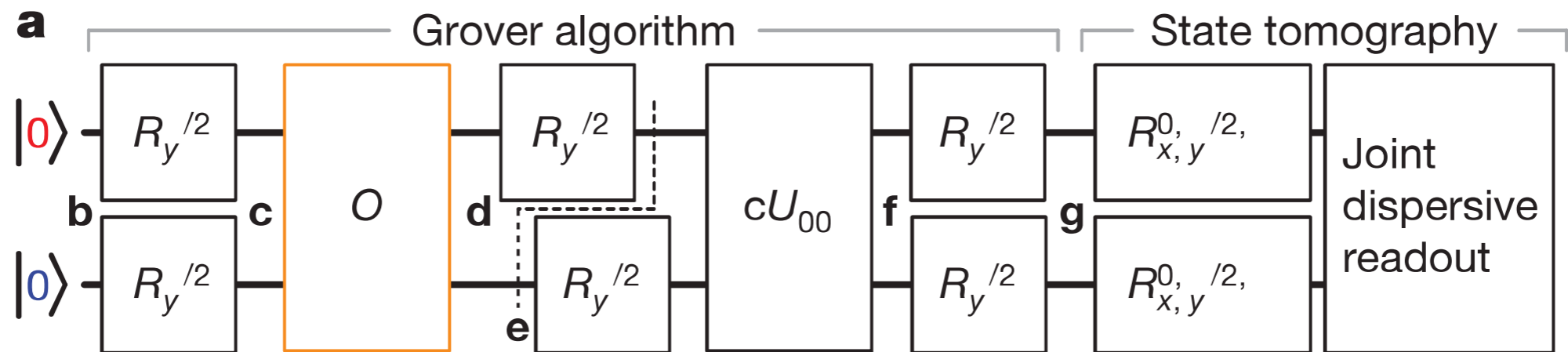


Current Device



DiCarlo et al., *Nature*, 460, 240 (2009).

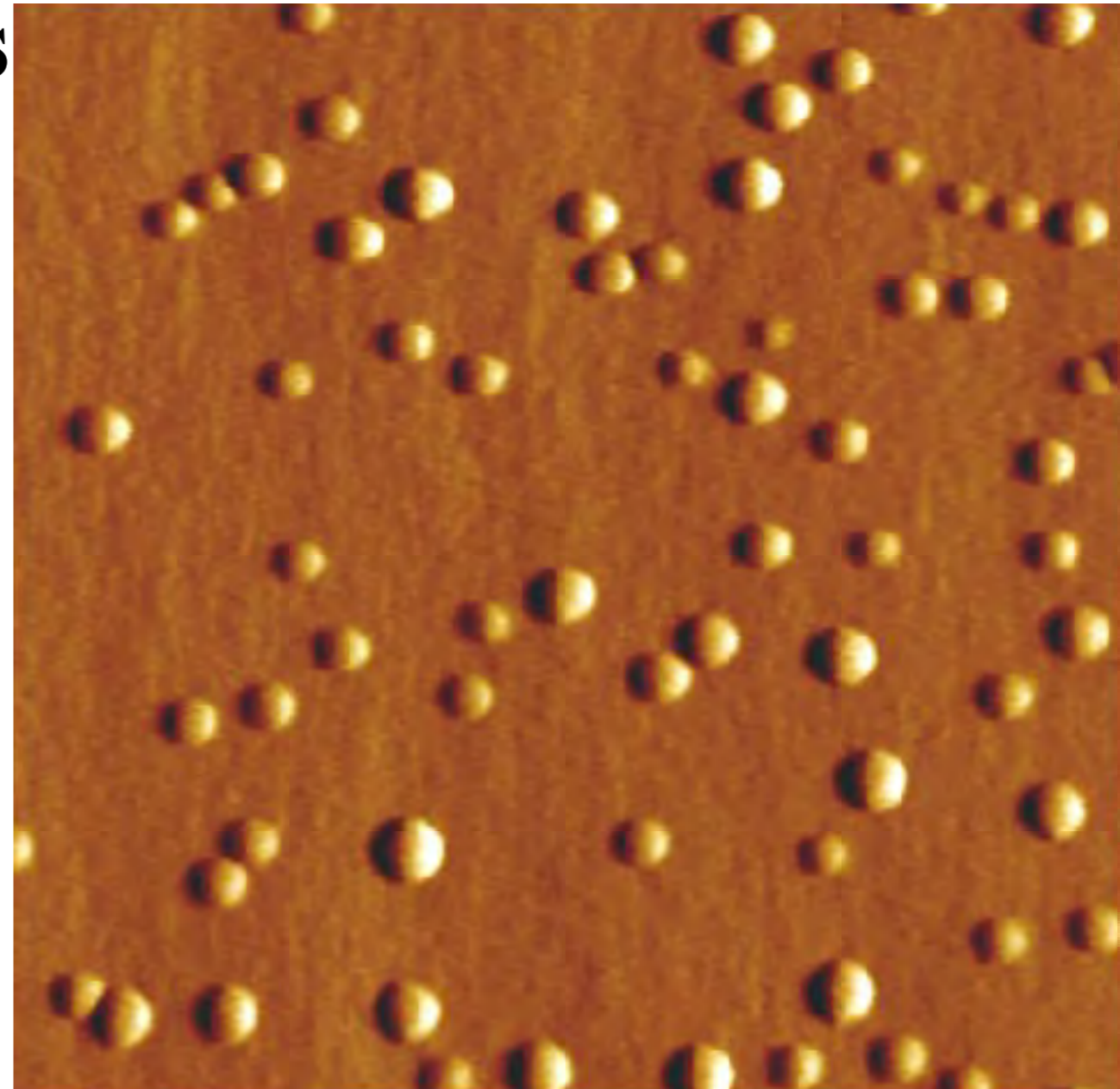
Grover Search



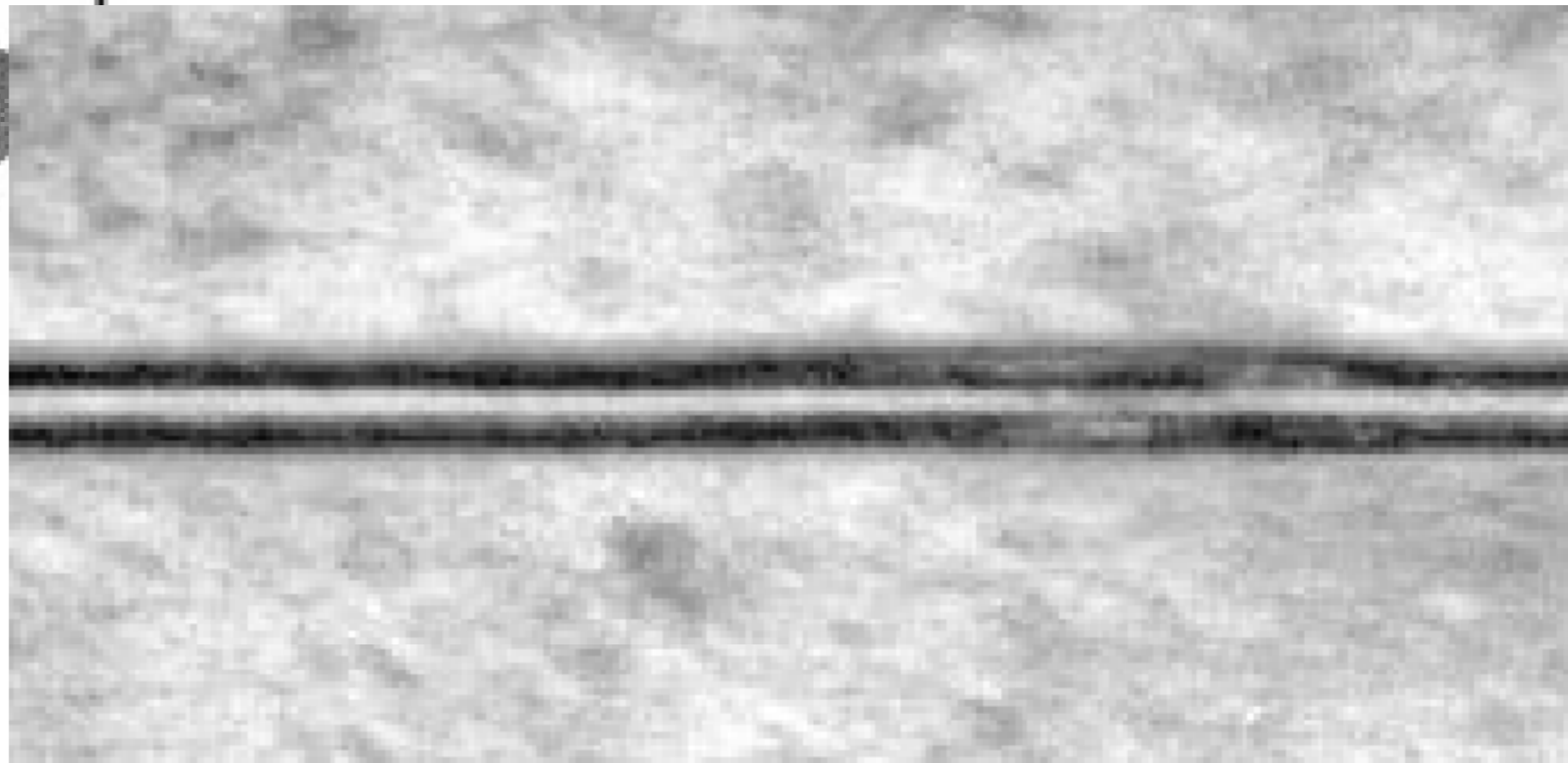
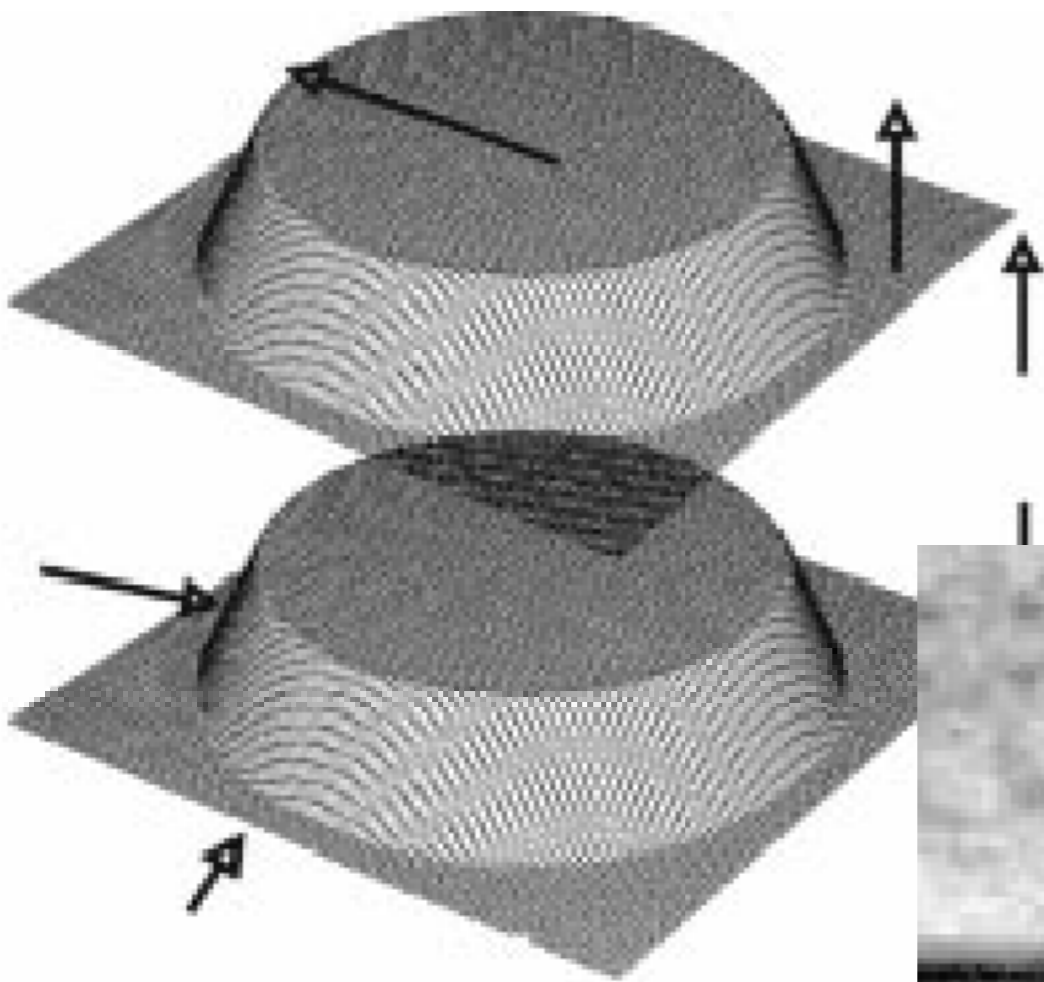
12.3.1 Materials

12.3.2 Excitons in quantum dots

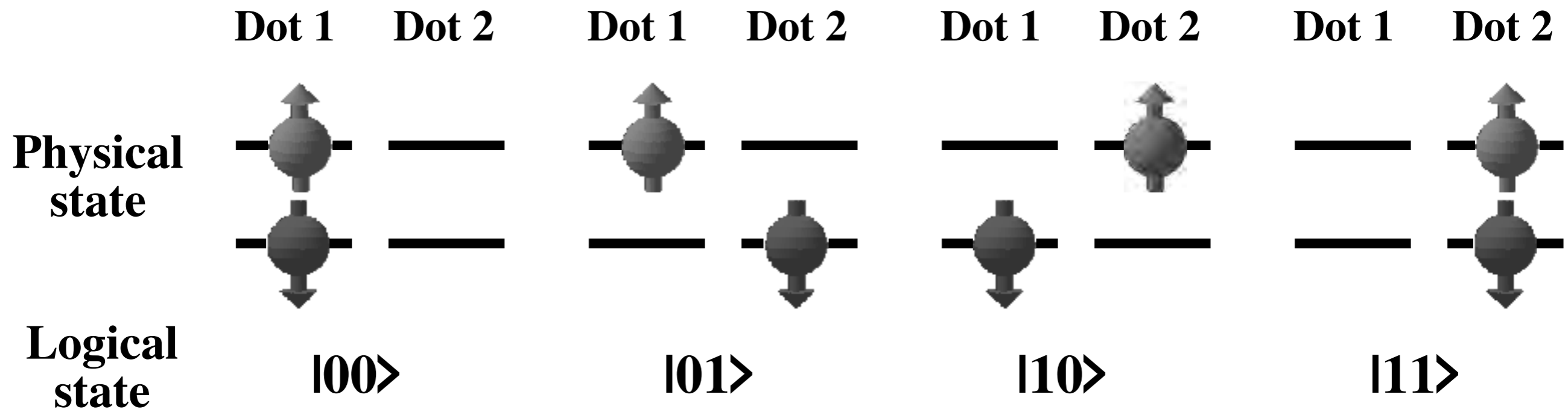
12.3.3 Electron spin qubits



Coupled Quantum Dots



Qubits

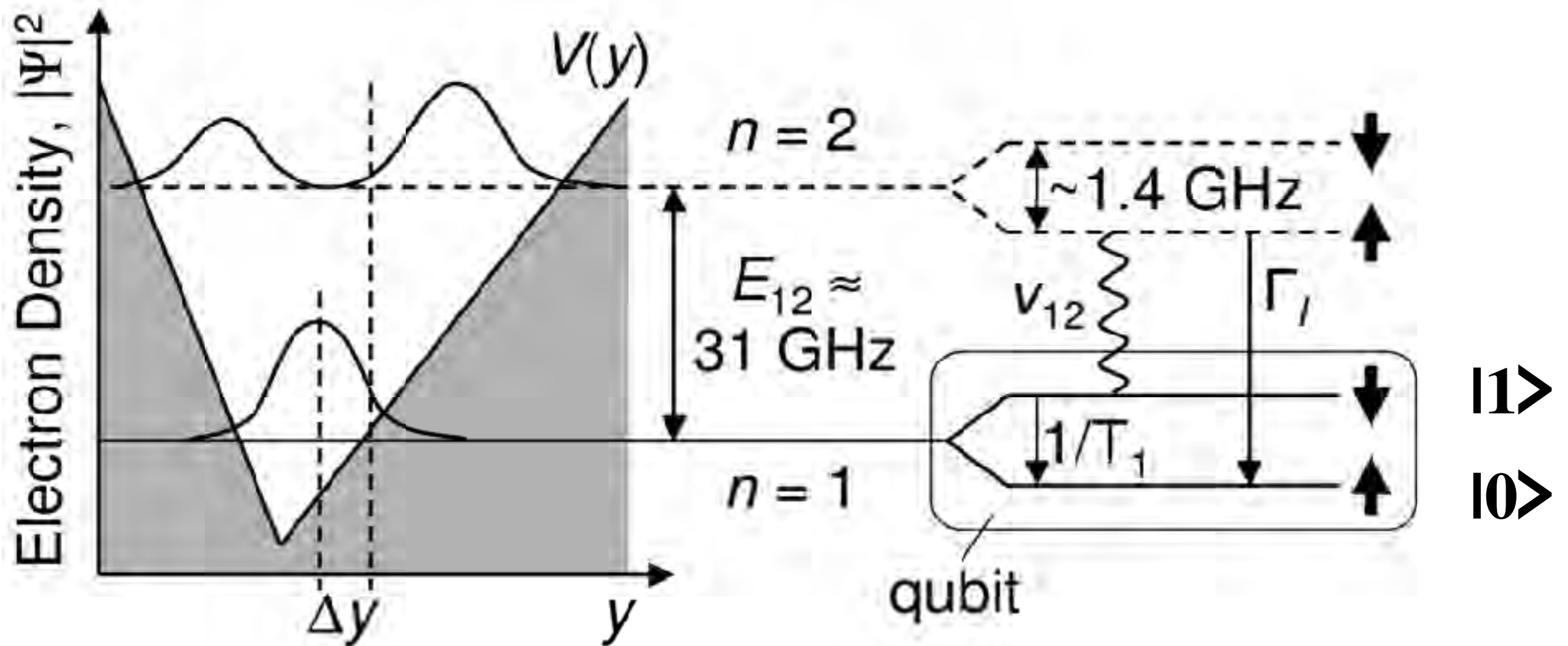


Single-step readout by microwave excitation

QDot Readout

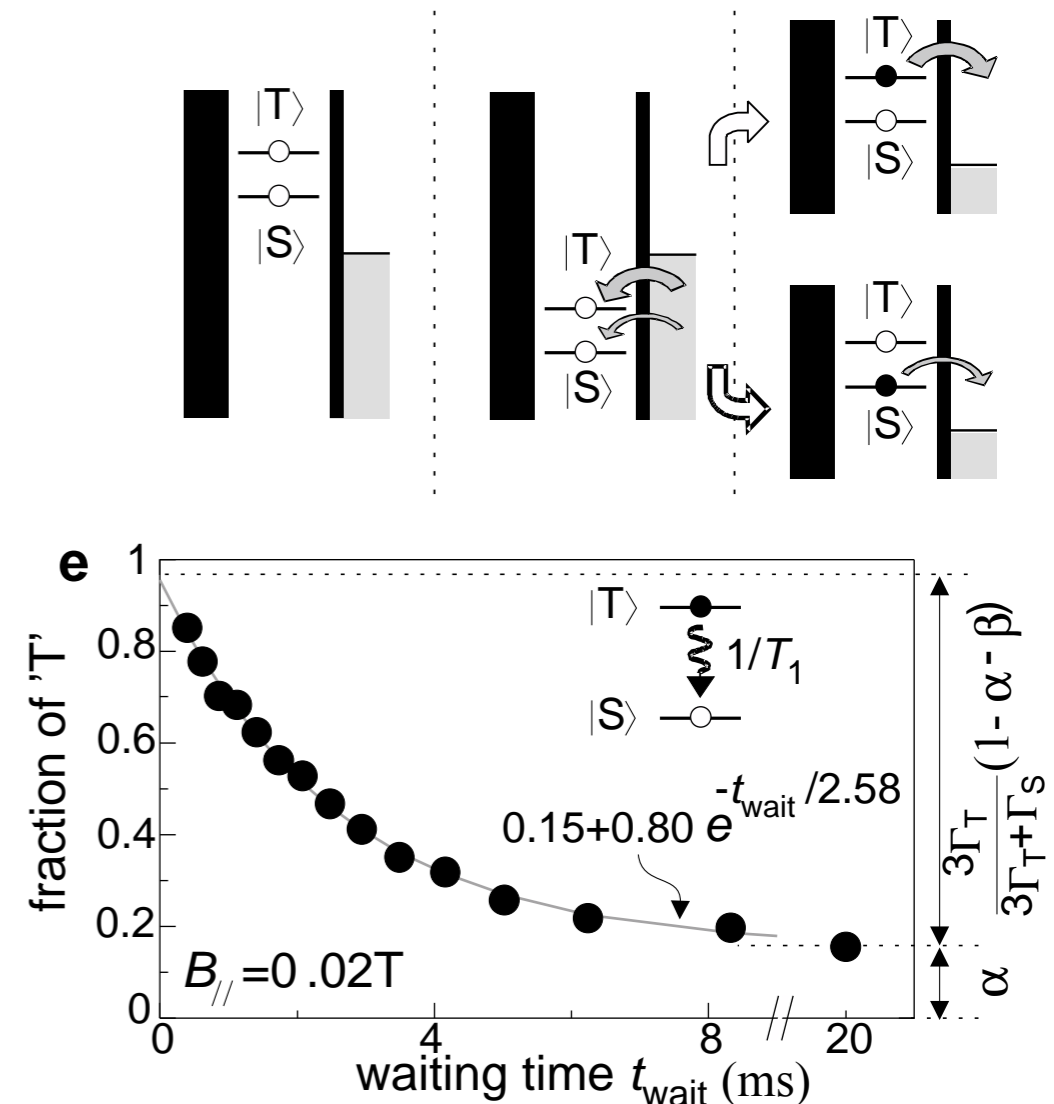
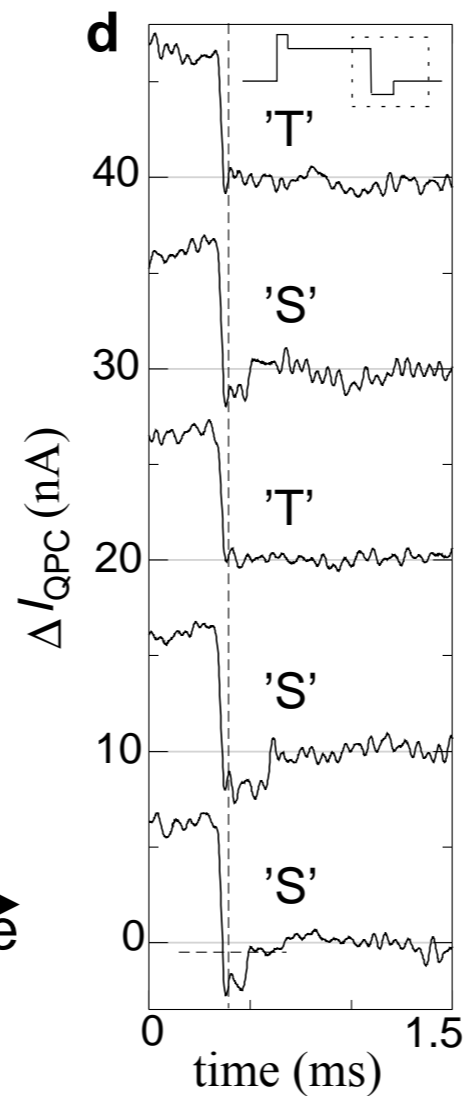
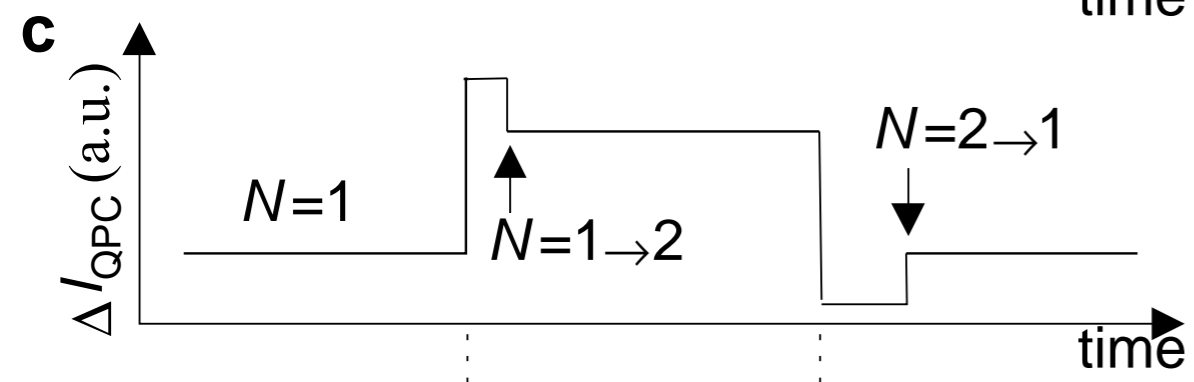
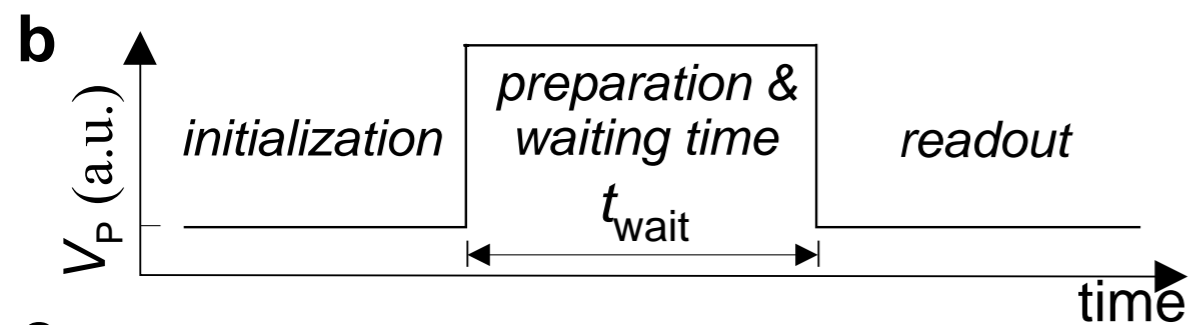
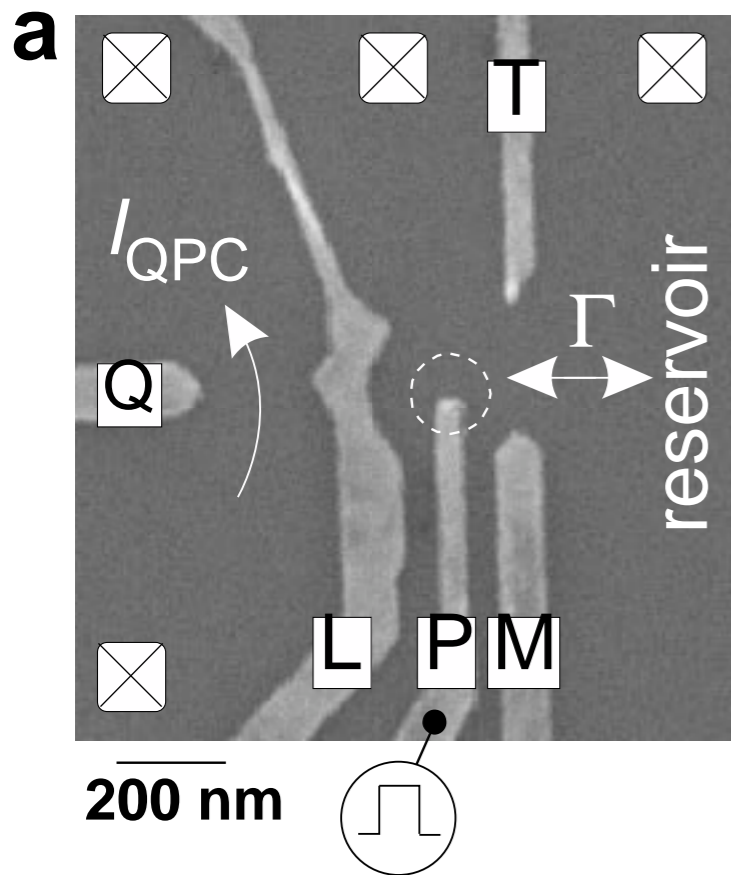
M. Friesen et al. , Phys. Rev. Lett. 92, 037901 (2004).

Asymmetric QW



- Irradiation at ν_{12} creates charge oscillation if qubit is in $|1\rangle$ state
- Can also be used for initialization

Spin-Filter Readout

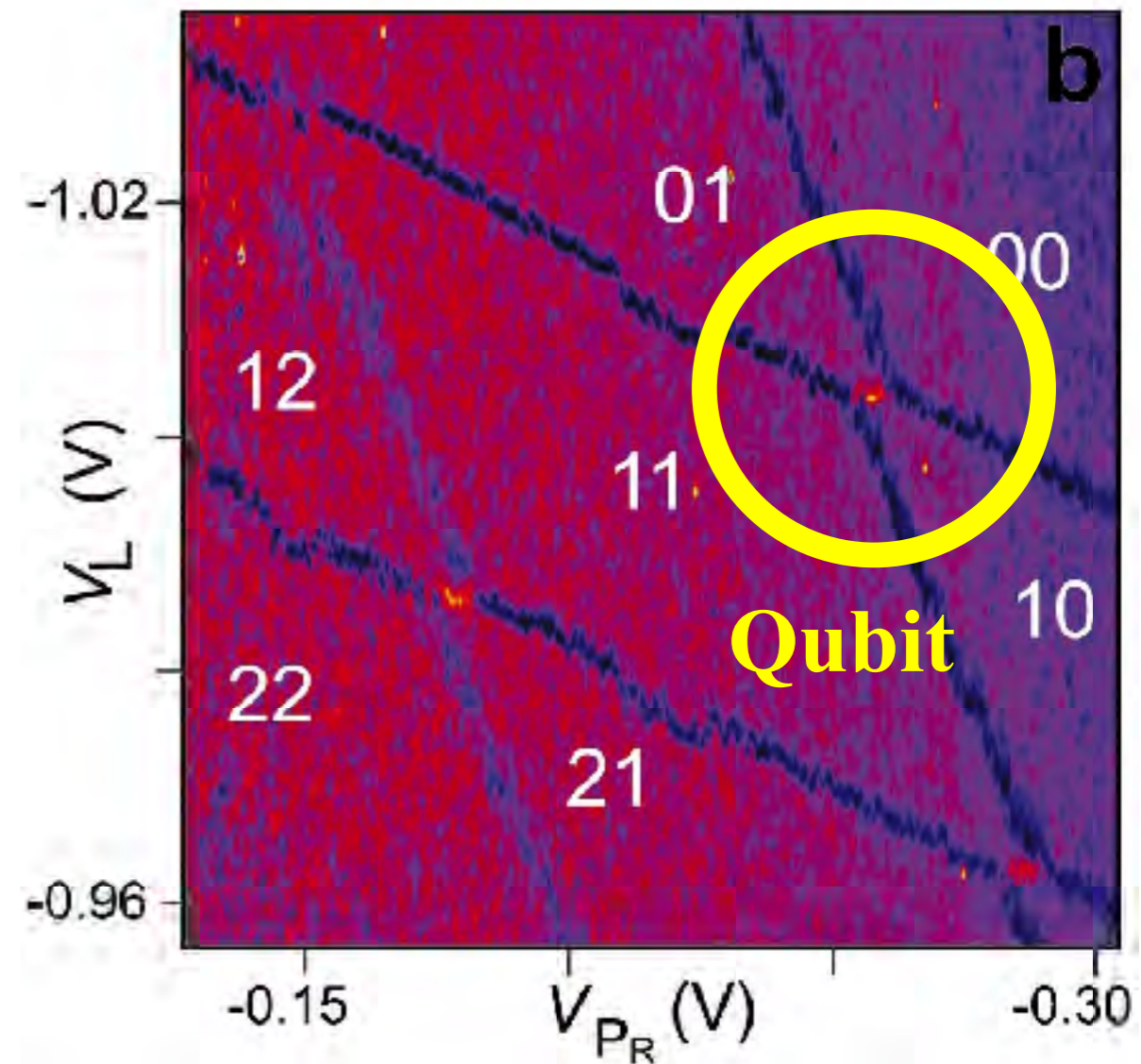
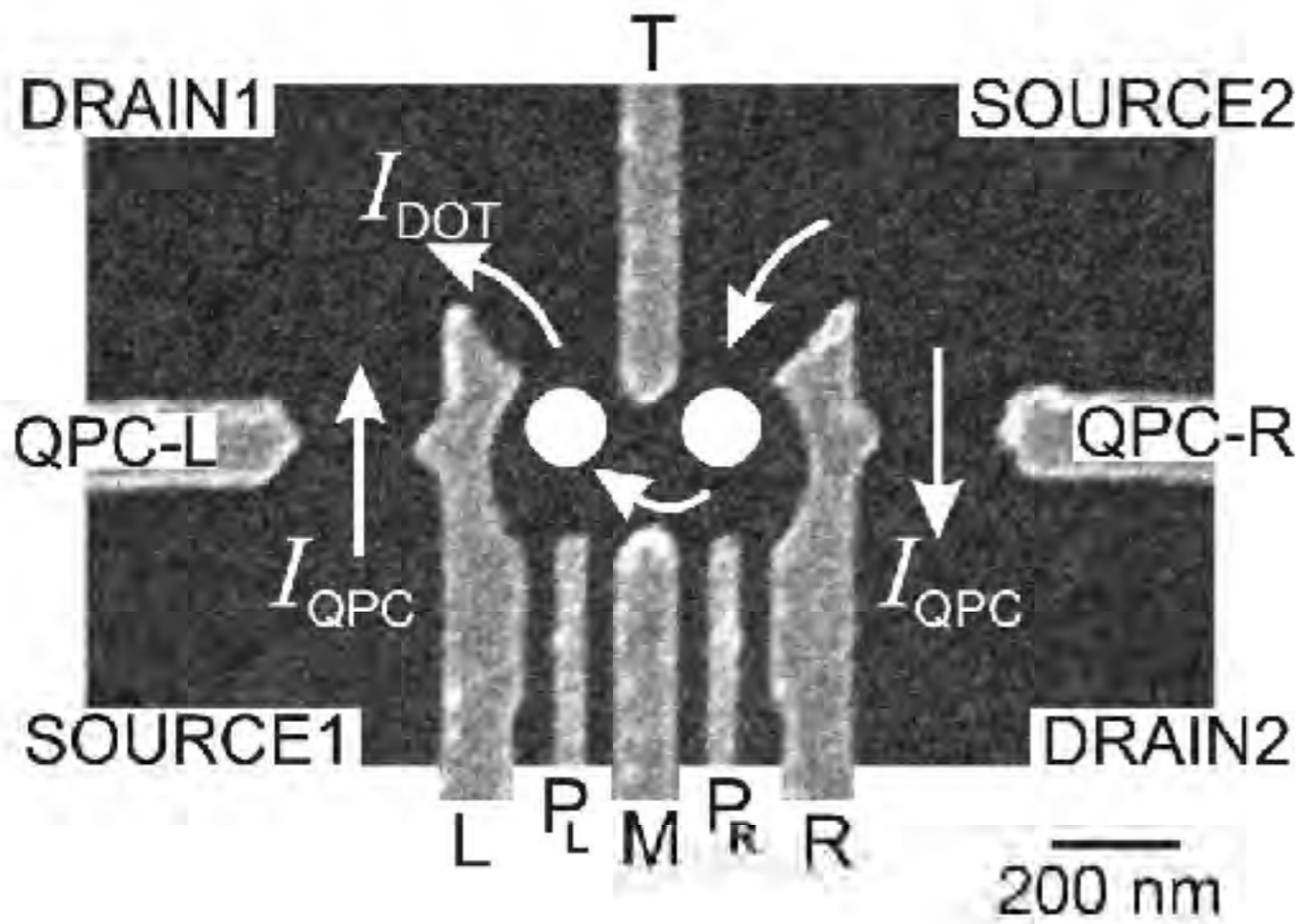


R. Hanson, L.H.W.v. Beveren, I.T. Vink, J.M. Elzerman, W.J.M. Naber, F.H.L. Koppens, L.P. Kouwenhoven, and L.M.K. Vandersypen, 'Single-Shot Readout of Electron Spin States in a Quantum Dot Using Spin-Dependent Tunnel Rates', Phys. Rev. Lett. **94**, 196802 (2005).

Qubits in Quantum Dots

Electrostatically controlled
pair of quantum dots

Occupation numbers



[1] J.M. Elzerman, R. Hanson, J.S. Greidanus, L.H.W.v. Beveren, S.D. Franceschi, L.M.K. Vandersypen, S. Tarucha, and L.P. Kouwenhoven, 'Few-electron quantum dot circuit with integrated charge read out', PRB 67, 161308 (2003).